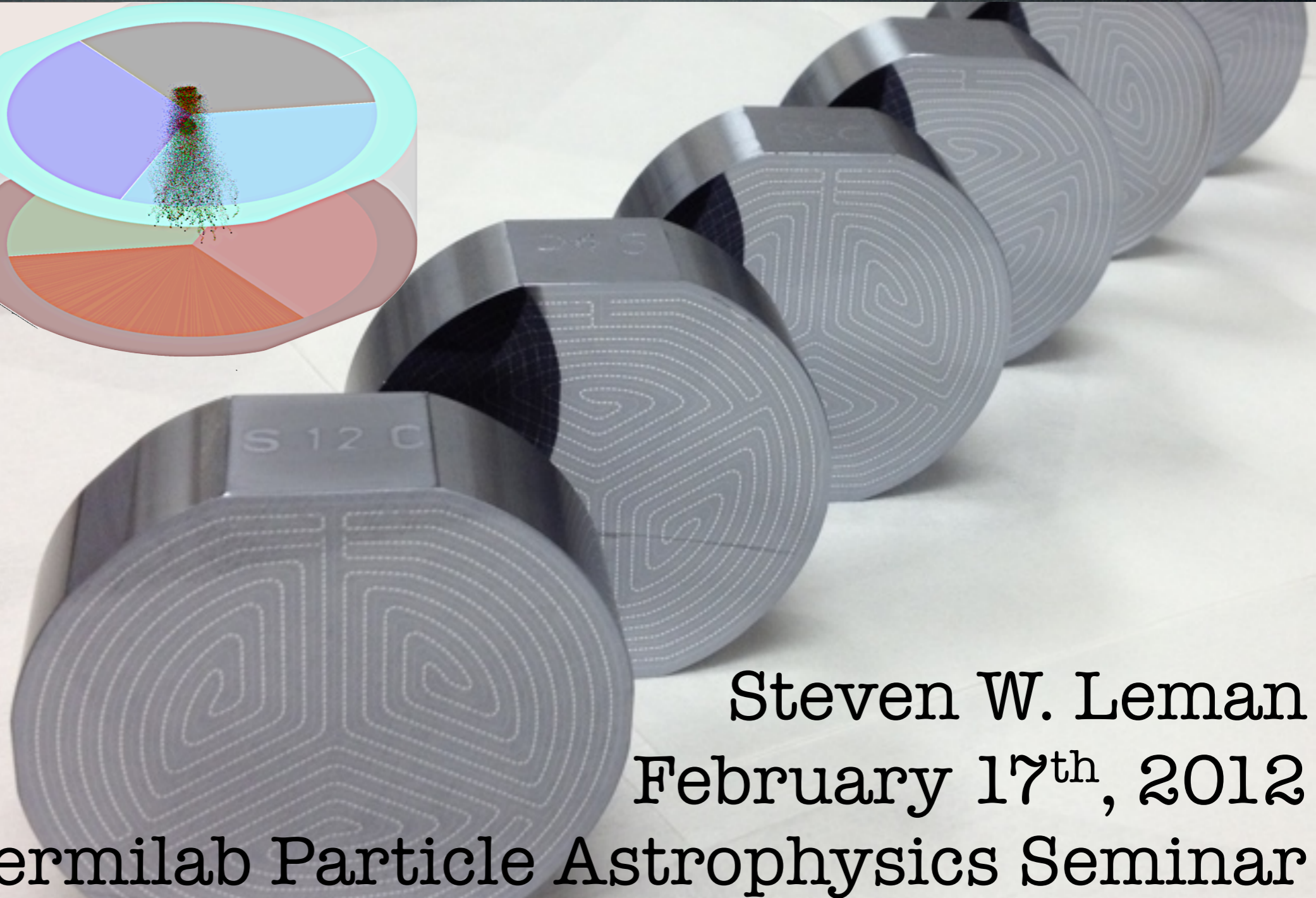
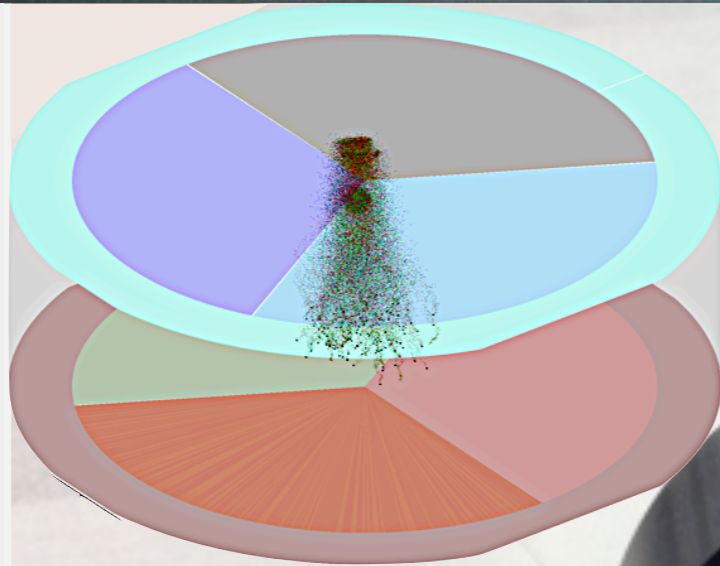
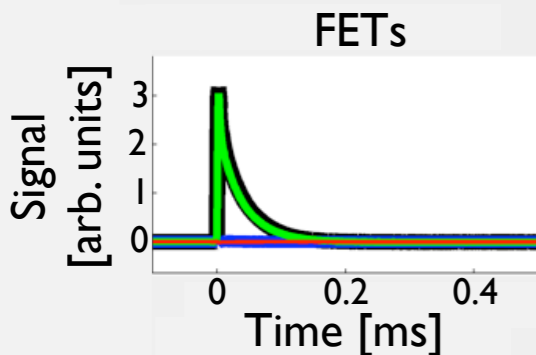
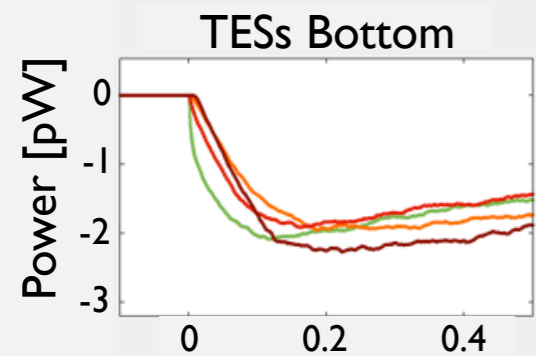
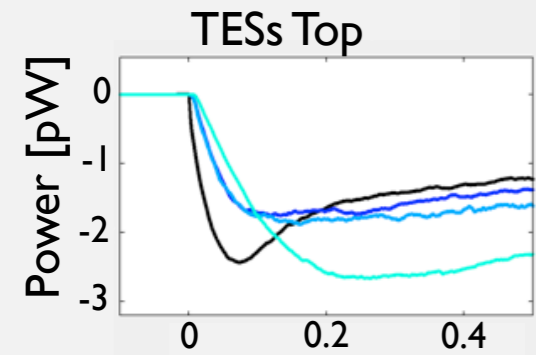


Bringing Light to a Dark Matter Search

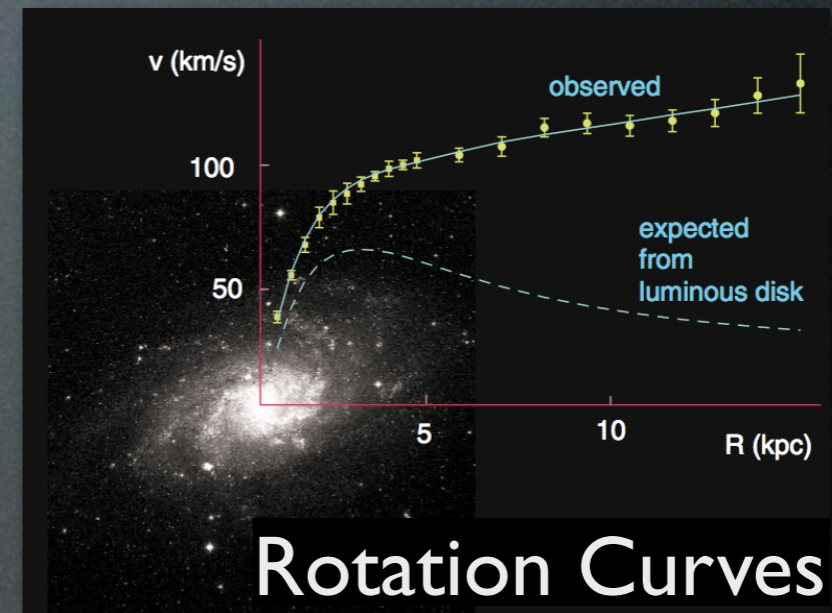


Steven W. Leman

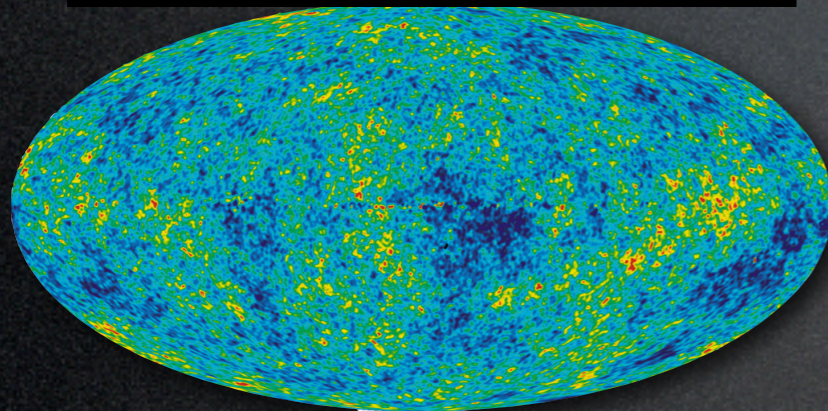
February 17th, 2012

Fermilab Particle Astrophysics Seminar

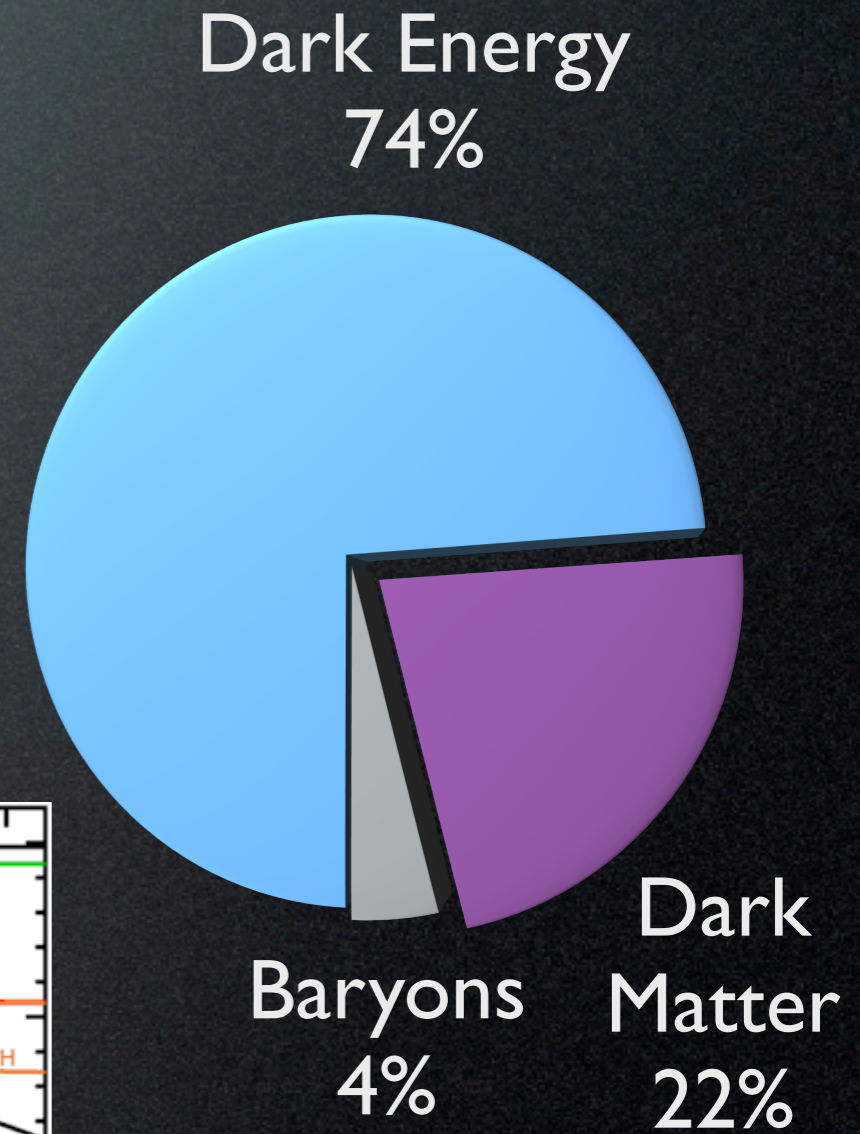
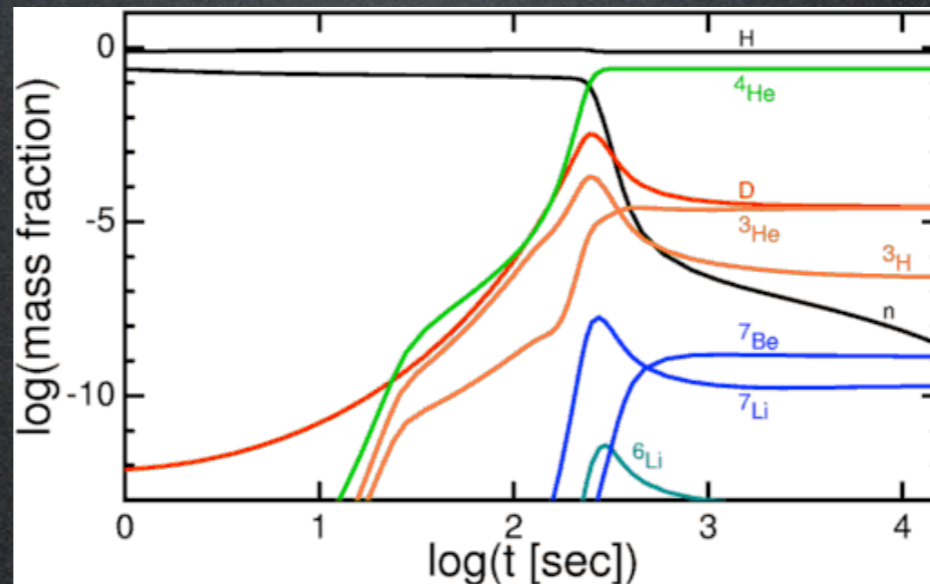
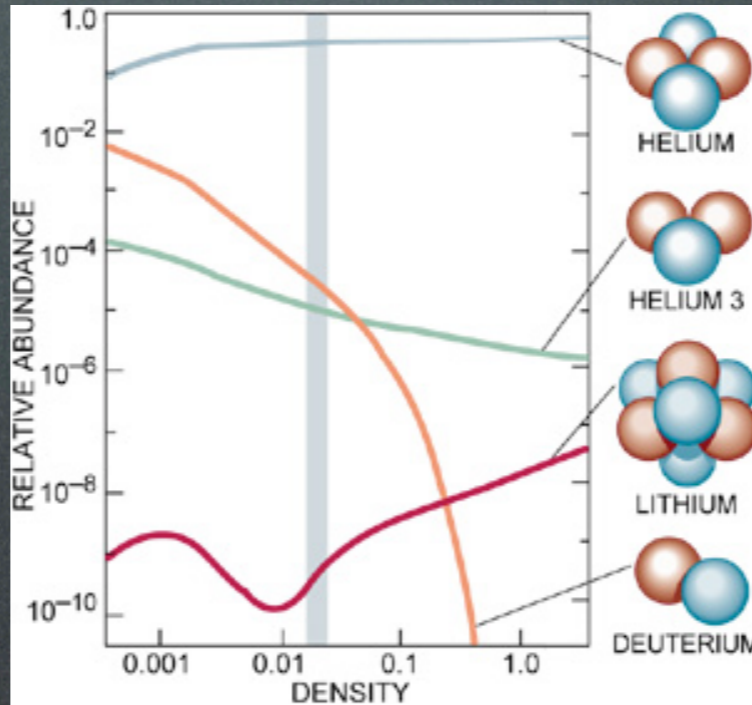
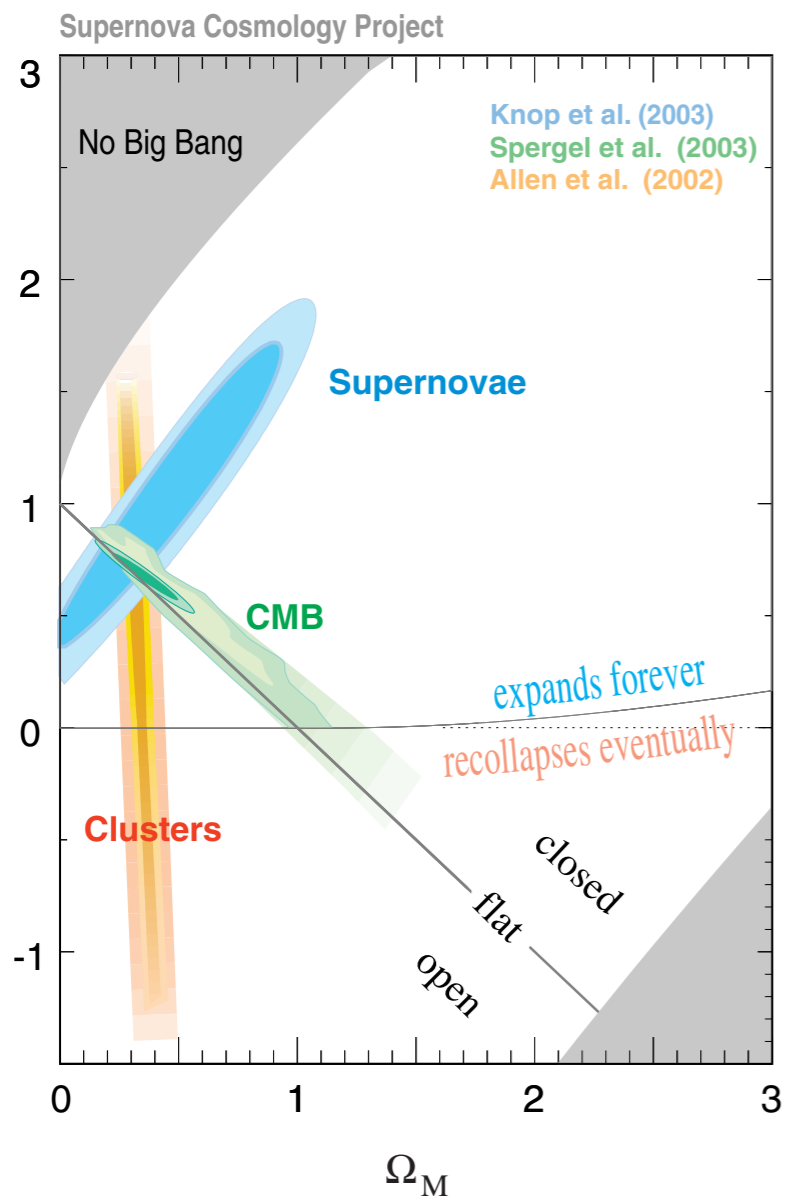
Dark Matter



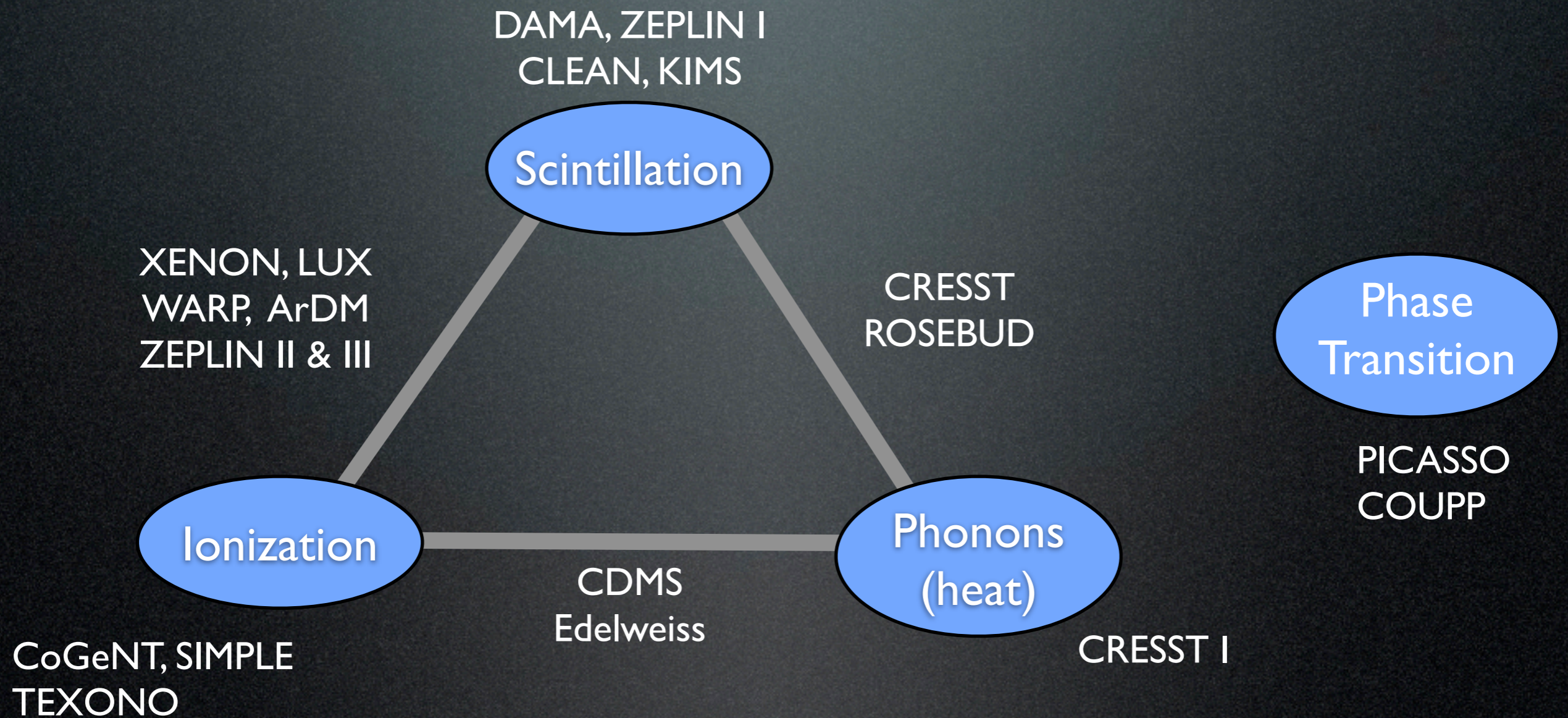
CMB Acoustic Peaks



Λ CDM Model



Readout Methods



Phonon Readout

2 Ionization Channels

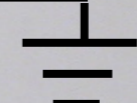
1 cm

7.5 cm

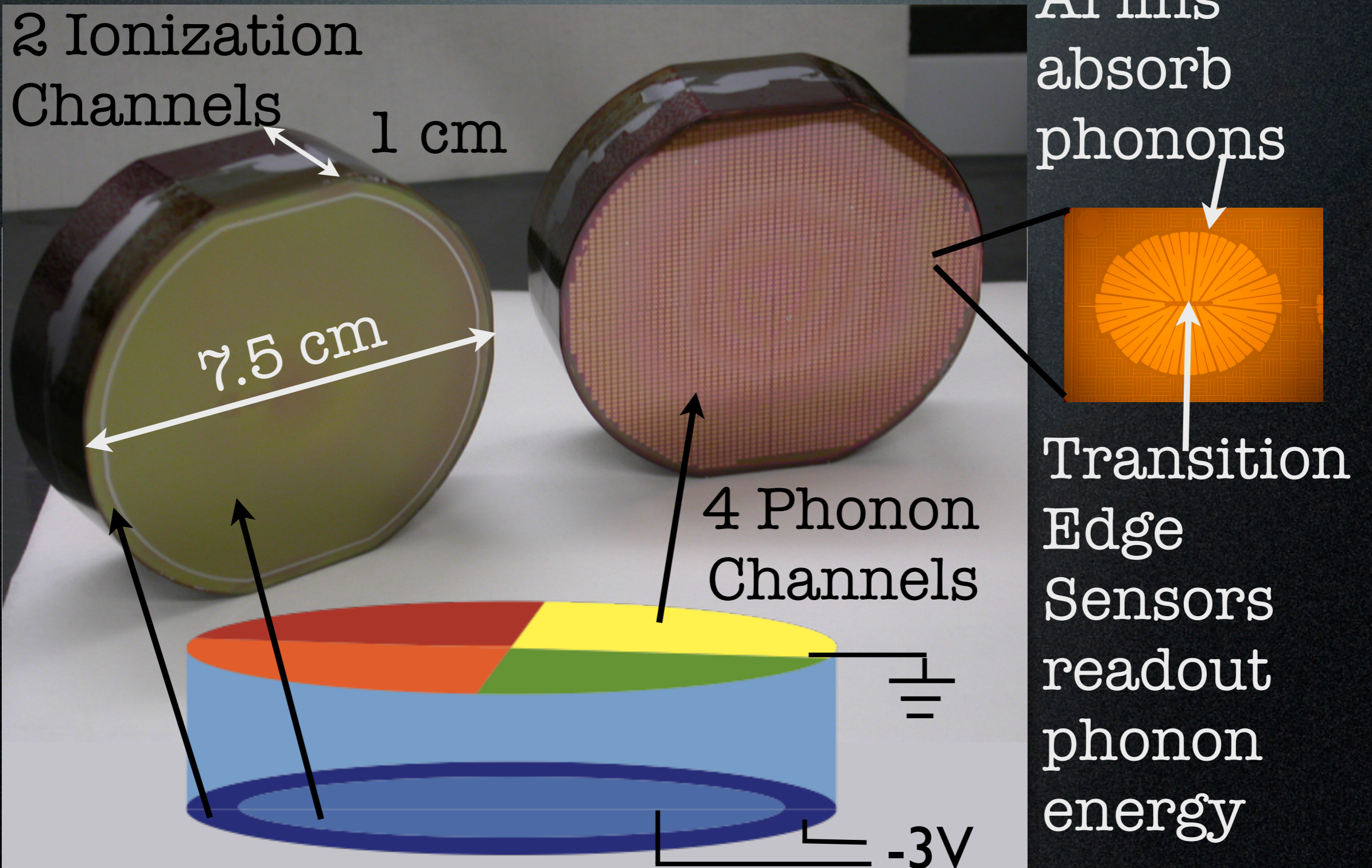
4 Phonon Channels

Al fins absorb phonons

Transition Edge Sensors readout phonon energy

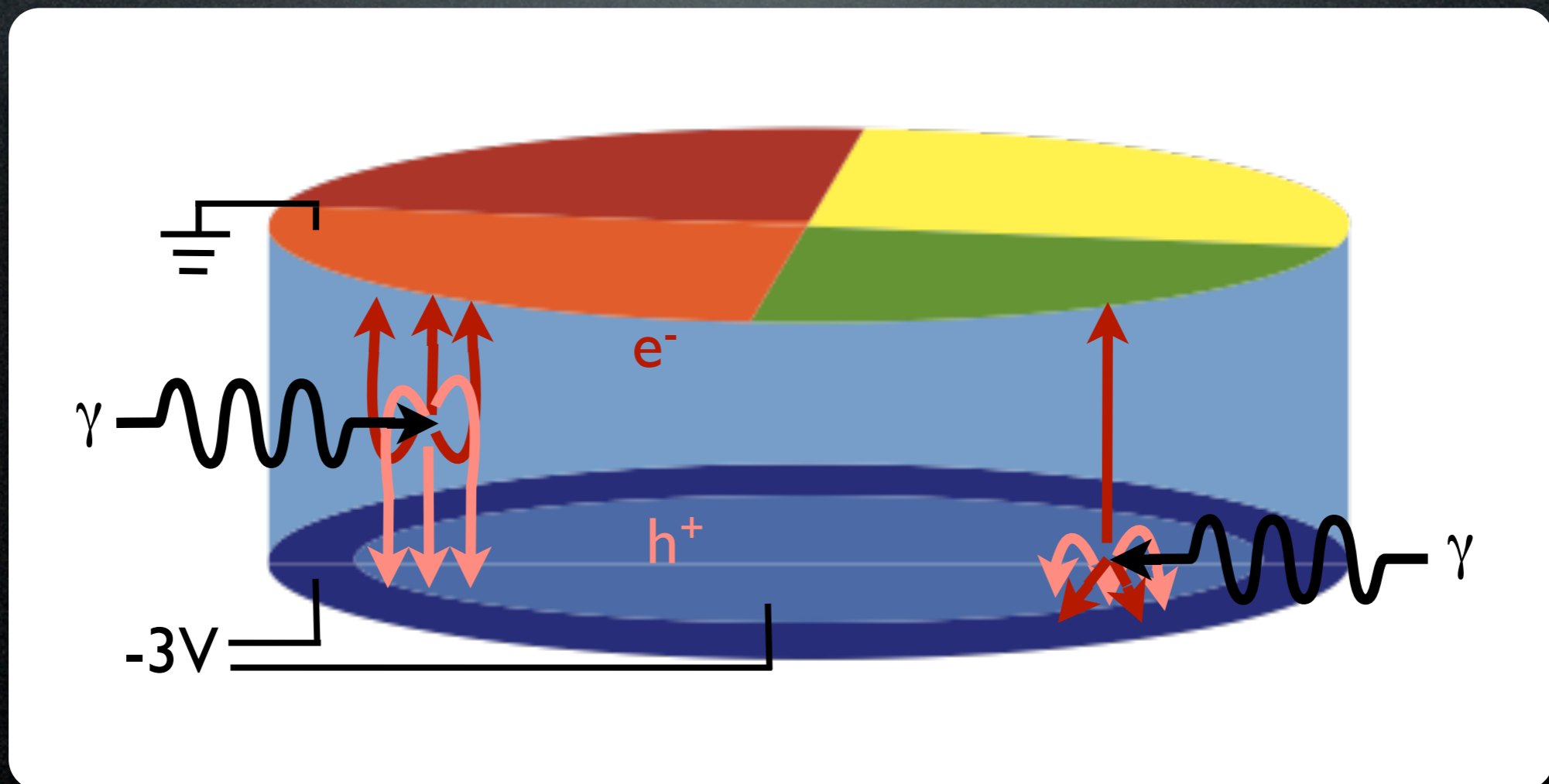


-3V



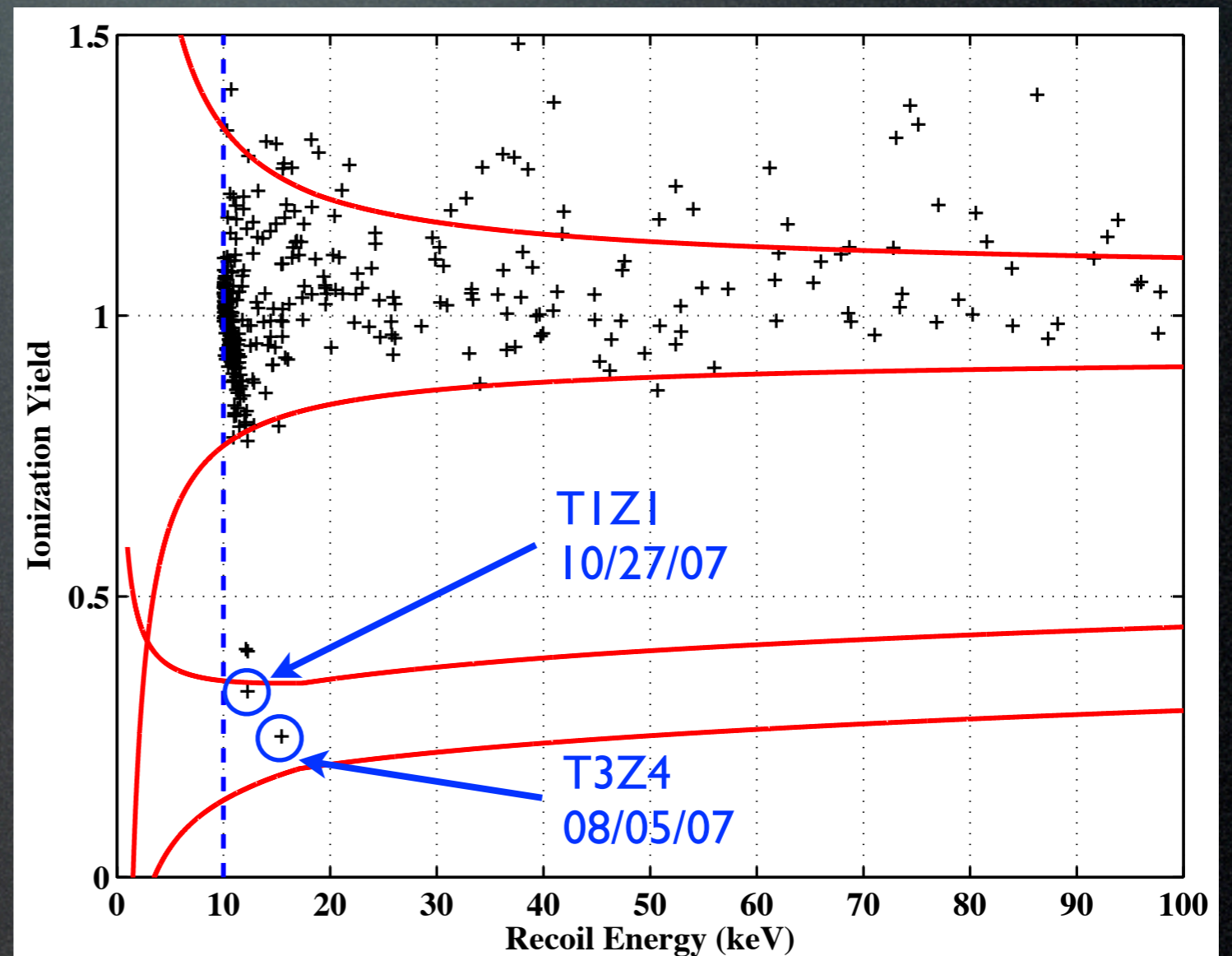
Carrier Transient

- Carriers initially high energy and can transport into the wrong electrode

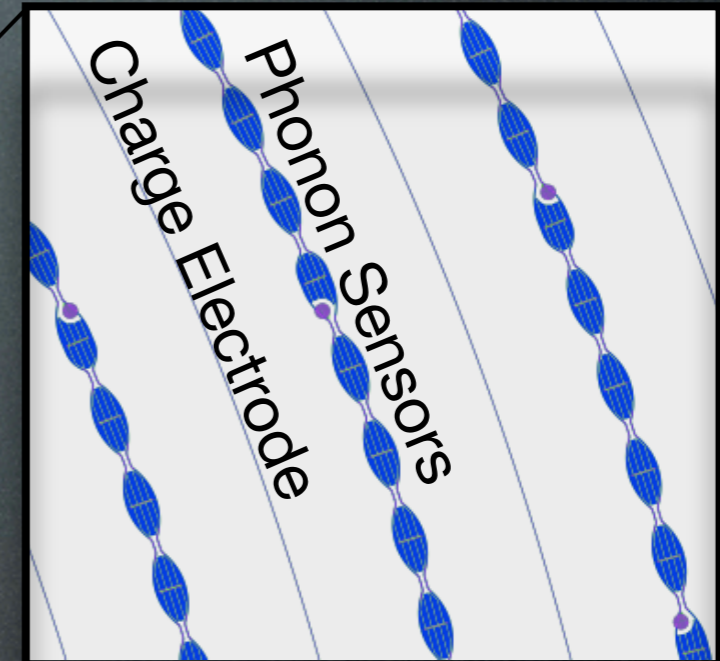
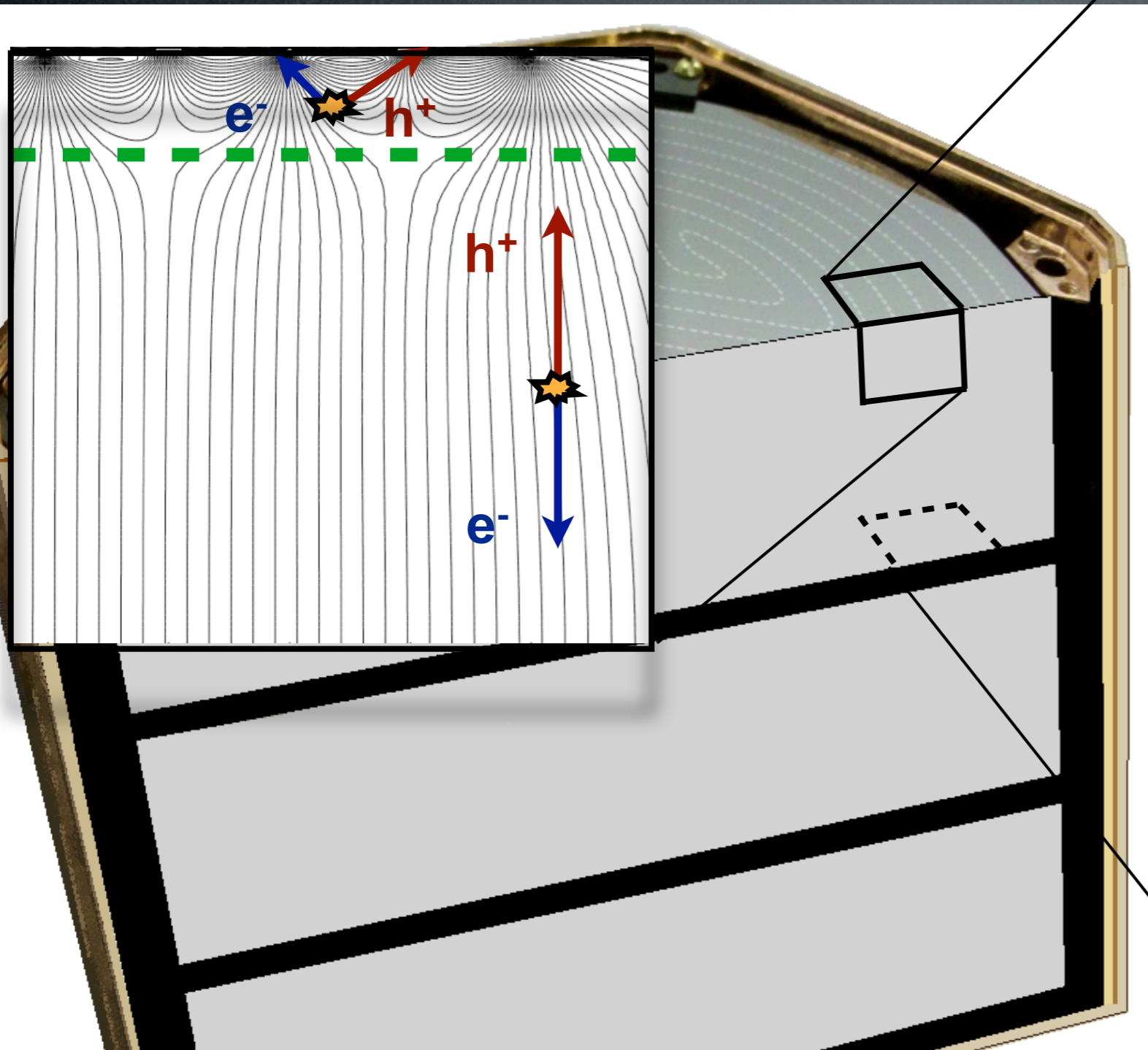


CDMS-II Data

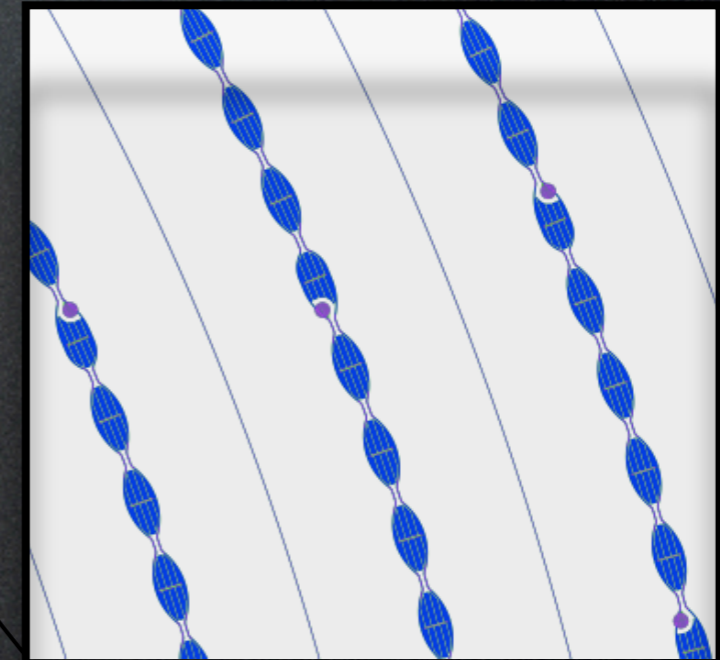
- 612 kg days Ge
- 2 events pass timing and NR cuts



SCDMS iZIP Detector



-2V 0V -2V 0V -2V 0V
2V 0V 2V 0V 2V 0V



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J. Beaty, H. Chagani, P. Cushman, S. Fallows, M. Fritts,
V. Mandic, X. Qiu, A. Reissetter, J. Zhang

University of Zurich

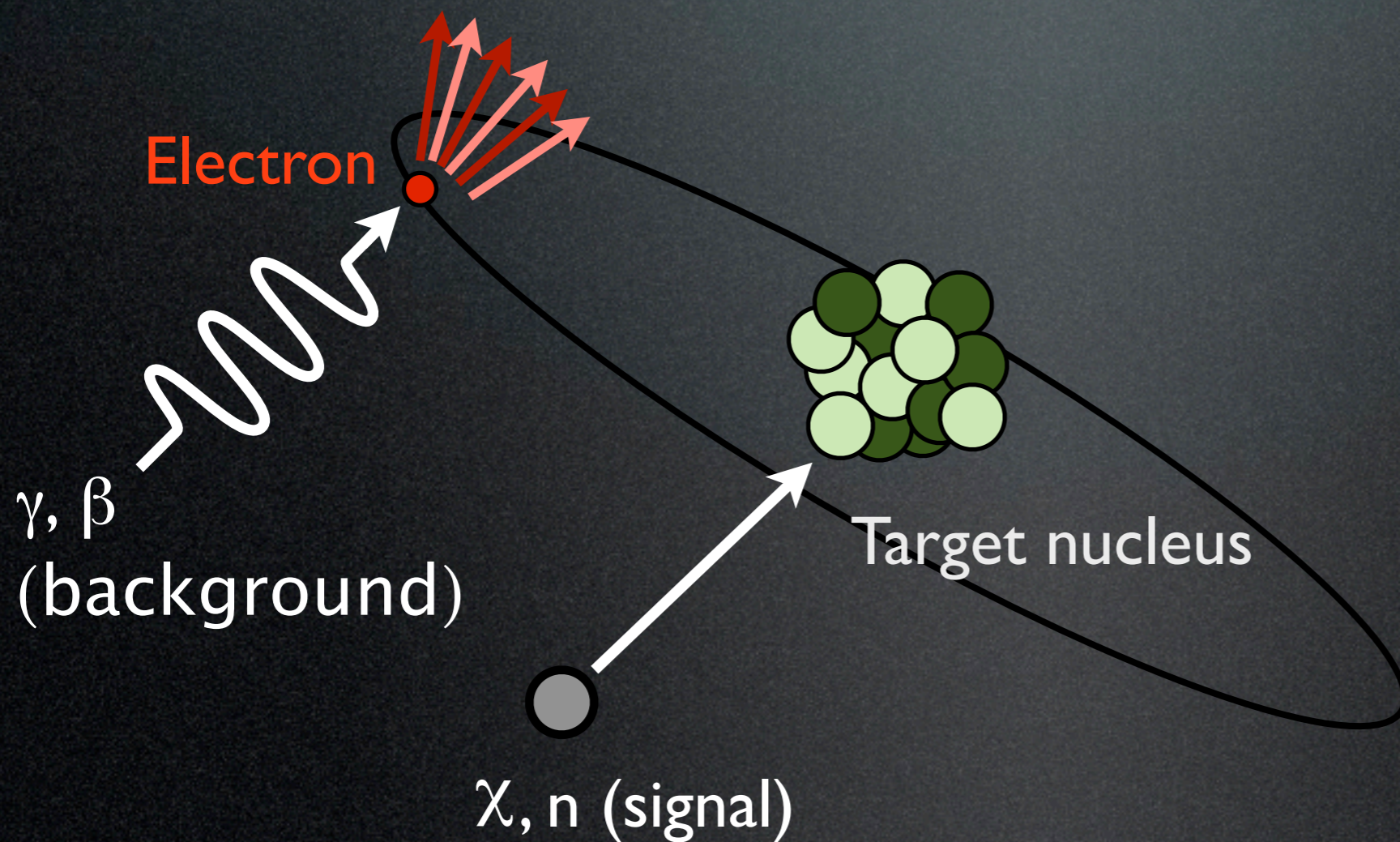
S. Arrenberg, T. Bruch, L. Baudis, M. Tarka

References

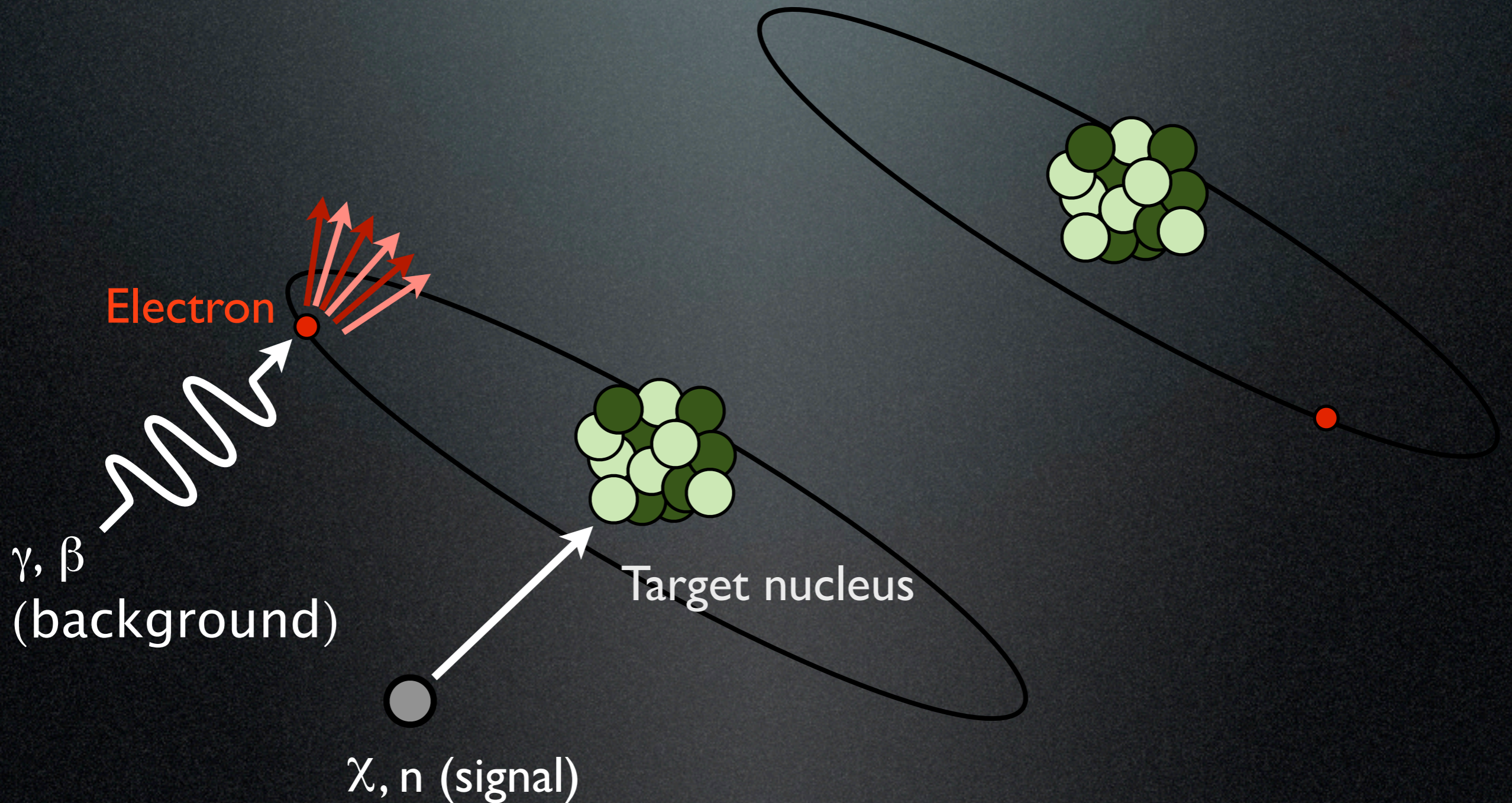
- “Invited Review Article: Physics and Monte Carlo Techniques as Relevant to Cryogenic, Phonon and Ionization Readout of CDMS Radiation-Detectors”, S.W. Leman, Review of Scientific Instruments (submitted)
- “Comparison of CDMS [100] and [111] oriented germanium detectors”, S.W. Leman, S.A. Hertel, P. Kim, et al, Low Temperature Physics Journal (accepted)
- “Validation of Phonon Physics in the CDMS Detector Monte Carlo”, K.A. McCarthy, S.W. Leman, P. Kim, et al, Proceedings of the 14th International Workshop on Low Temperature Detectors, Low Temperature Physics Journal (submitted)
- “Simulations of Noise in Phase-Separated Transition-Edge Sensors for SuperCDMS”, A.J. Anderson, S.W. Leman, et al, Low Temperature Physics Journal (accepted)
- “Modeling phase-separated transition-edge sensors in SuperCDMS detectors”, A.J. Anderson, S.W. Leman, et al, Nuclear Instruments and Methods A (submitted)
- “Monte Carlo Comparisons to a Cryogenic Dark Matter Search Detector with low Transition-Edge-Sensor Transition Temperature”, S.W. Leman, K.A McCarthy, P. Kim, et al, Journal of Applied Physics 110, 094515 (2011)
- “Phonon Quasidiffusion in CDMS Large Germanium Detectors”, S.W. Leman, K.A. McCarthy, et al, Chinese Journal of Physics, vol 49 (2011) p. 349 (PHONONS 2010 conference proceedings)

Event Classification

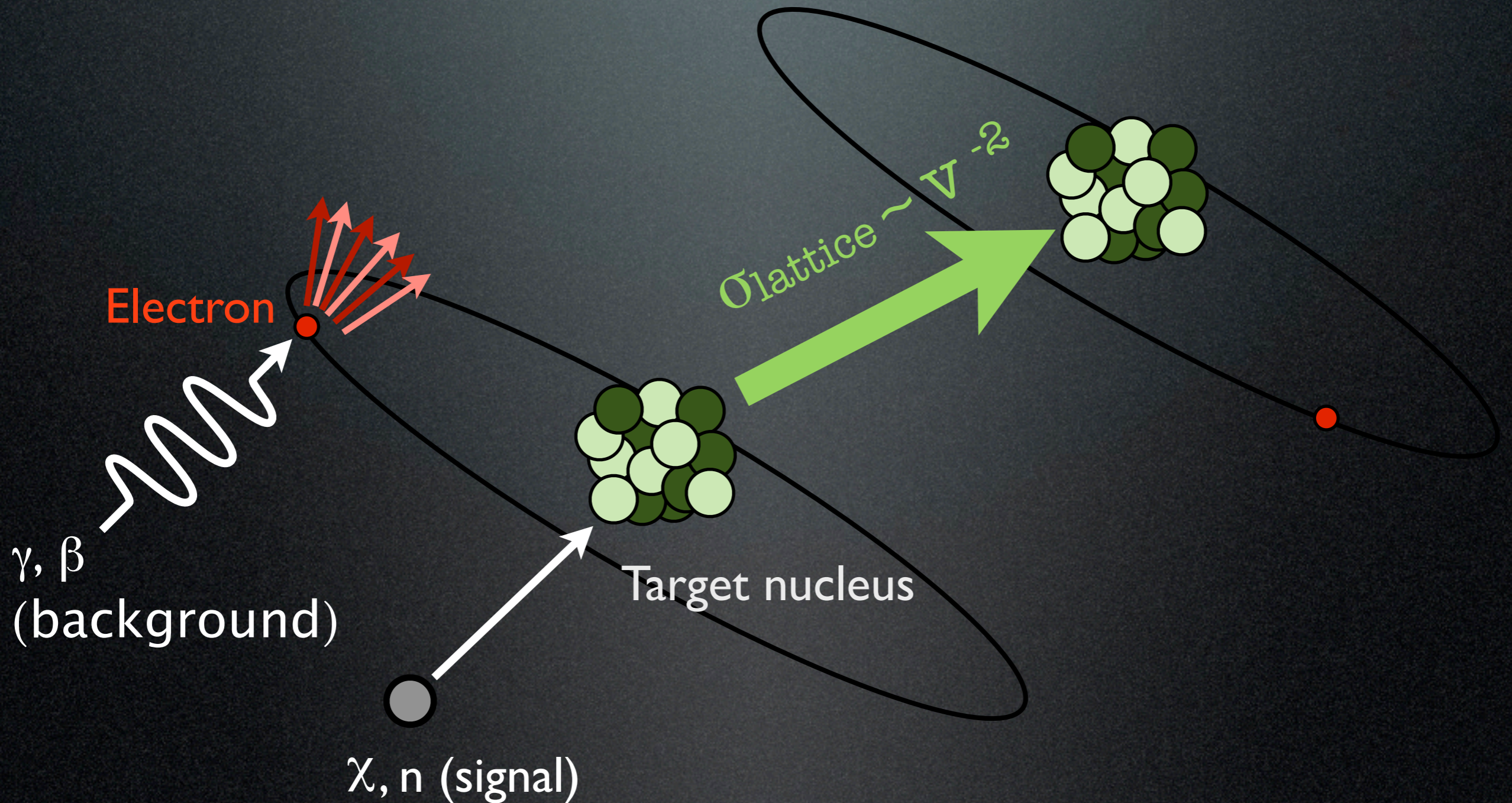
Charge vs Lattice Interactions



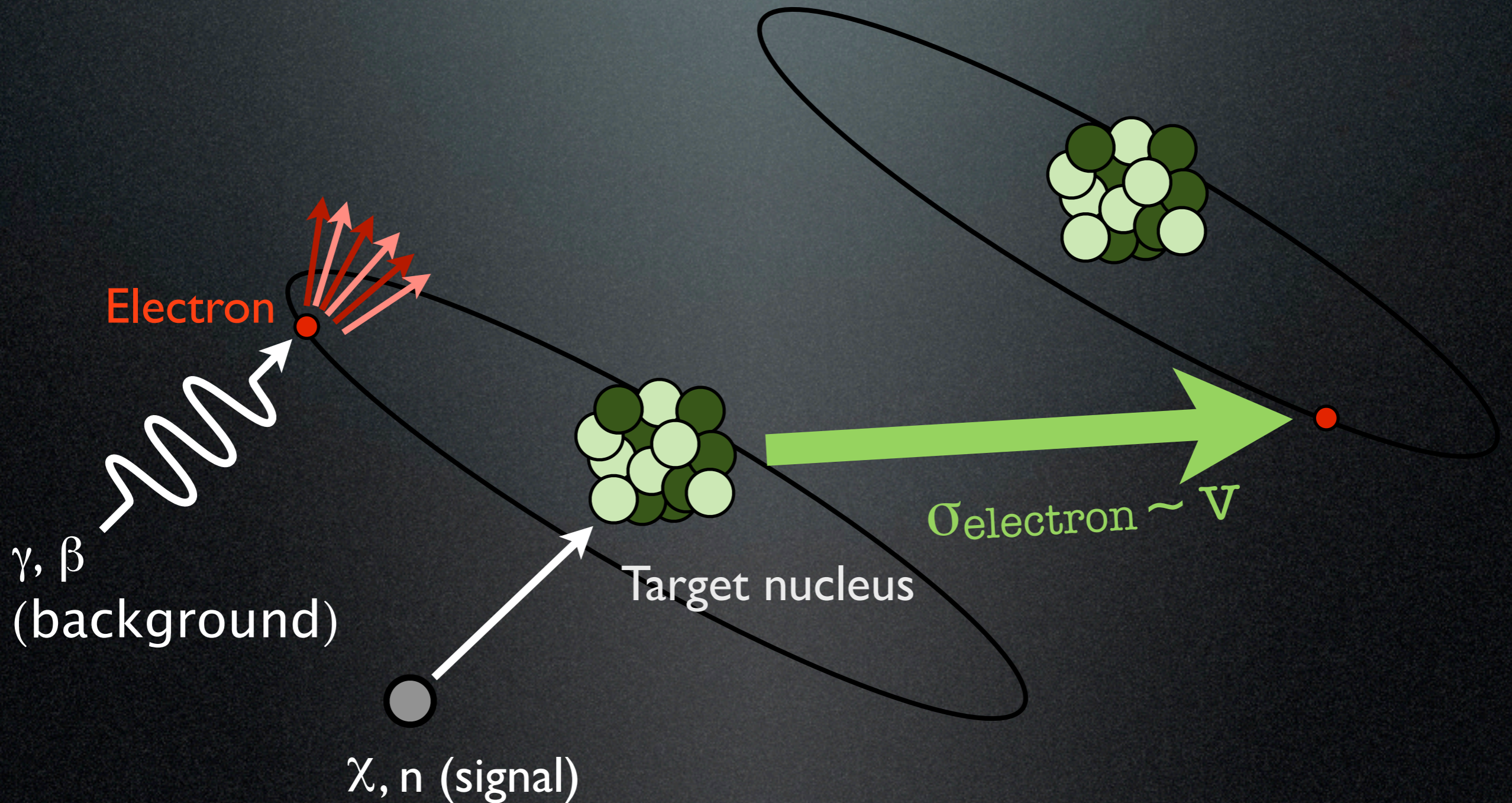
Charge vs Lattice Interactions



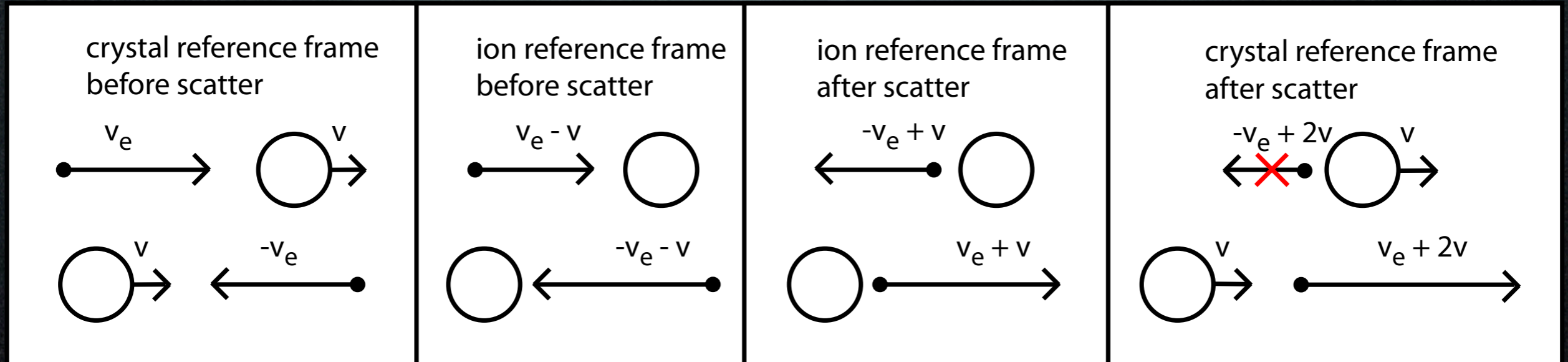
Charge vs Lattice Interactions



Charge vs Lattice Interactions



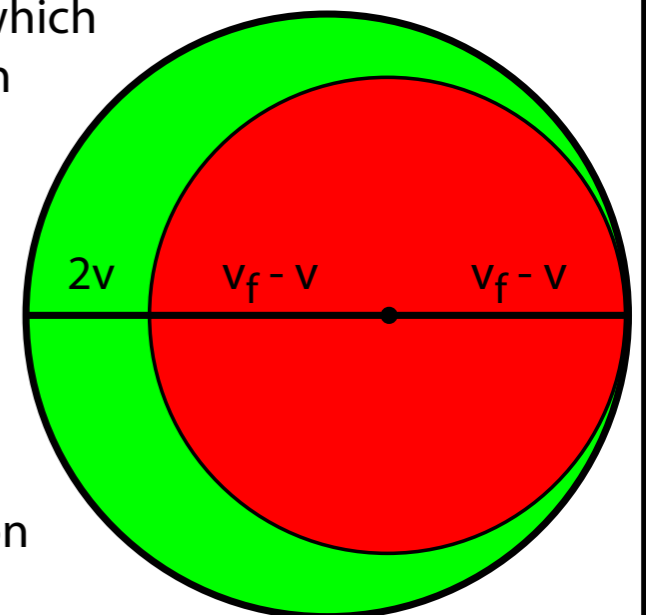
Electron-Ion Interaction



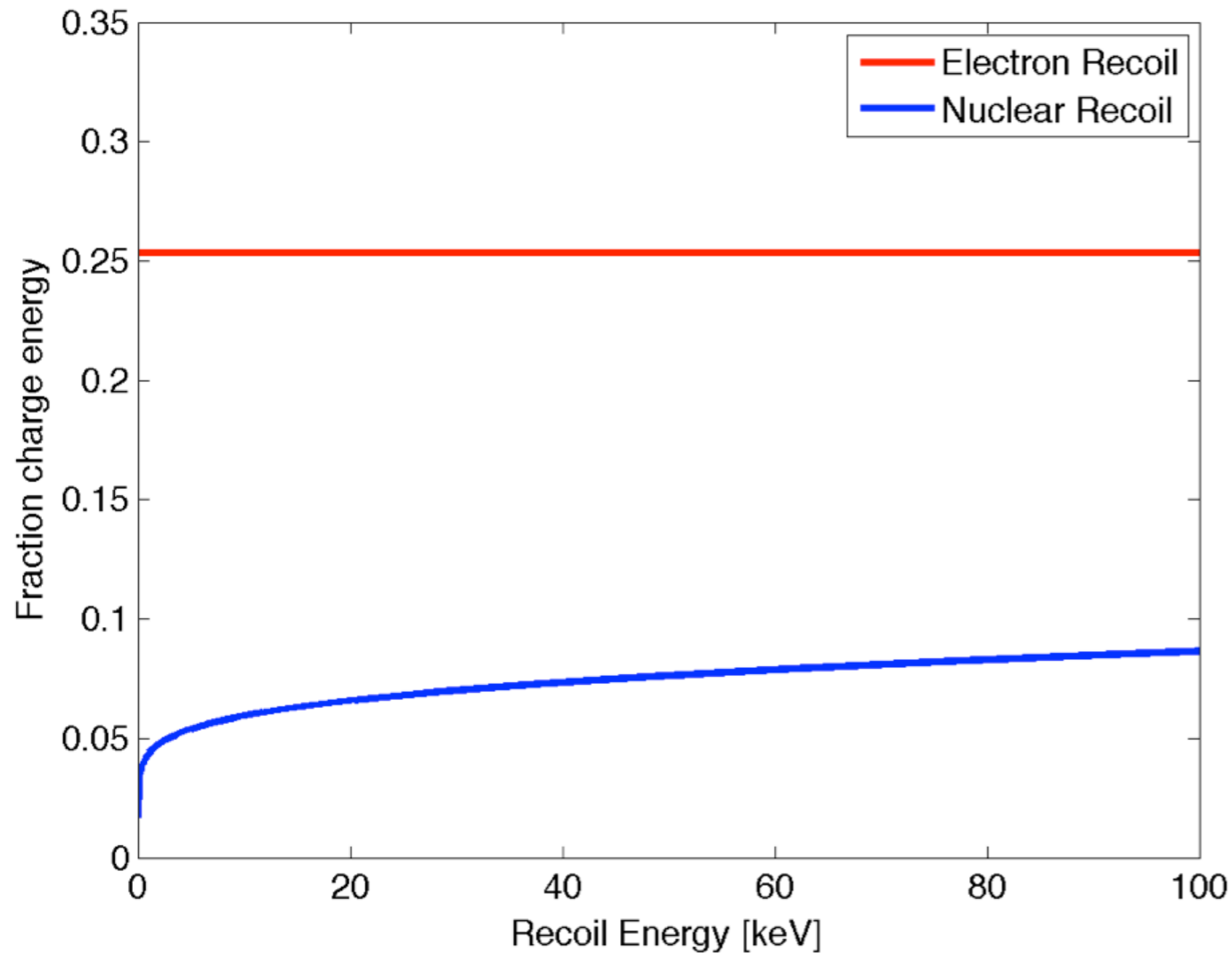
- electron
 - ion
- Ion-electron interactions are via a potential and hence can only change the direction of the electron velocity in the ion reference frame.

Two hypothetical ion-electron interactions, shown before and after the scatter and in the crystal and ion reference frames. In the parallel interaction, the final electron velocity is too small to scatter to an unoccupied region outside of the Fermi sphere and is forbidden. In the anti-parallel process, the electron can be scattered to an unoccupied state outside of the Fermi sphere.

- Region in Fermi sphere in which ion-electron interaction can scatter electrons to unoccupied region outside of sphere (allowed)
- Region in Fermi sphere in which ion-electron interaction can scatter electrons to occupied region inside of sphere (forbidden)



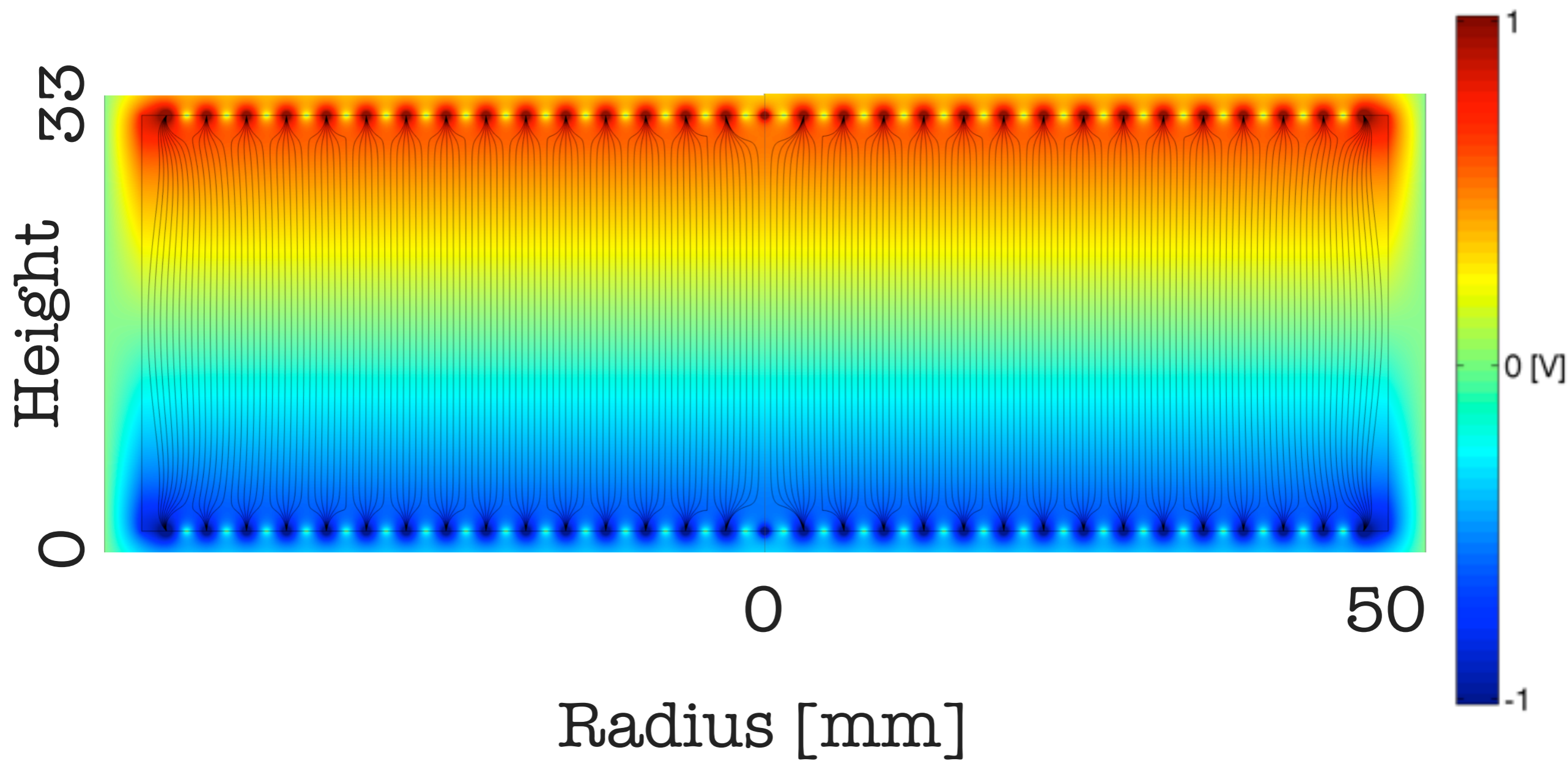
Lindhard Theory



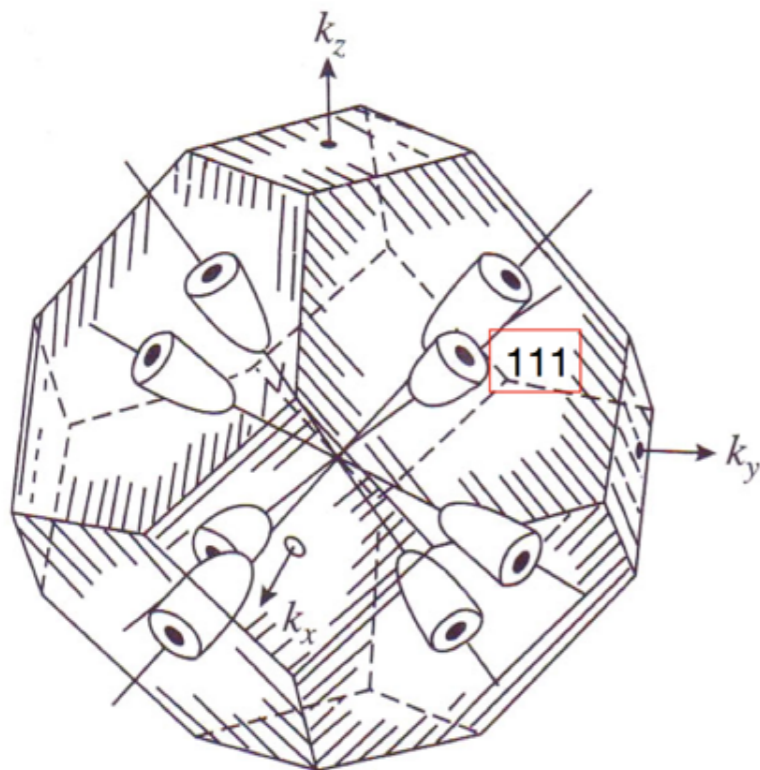
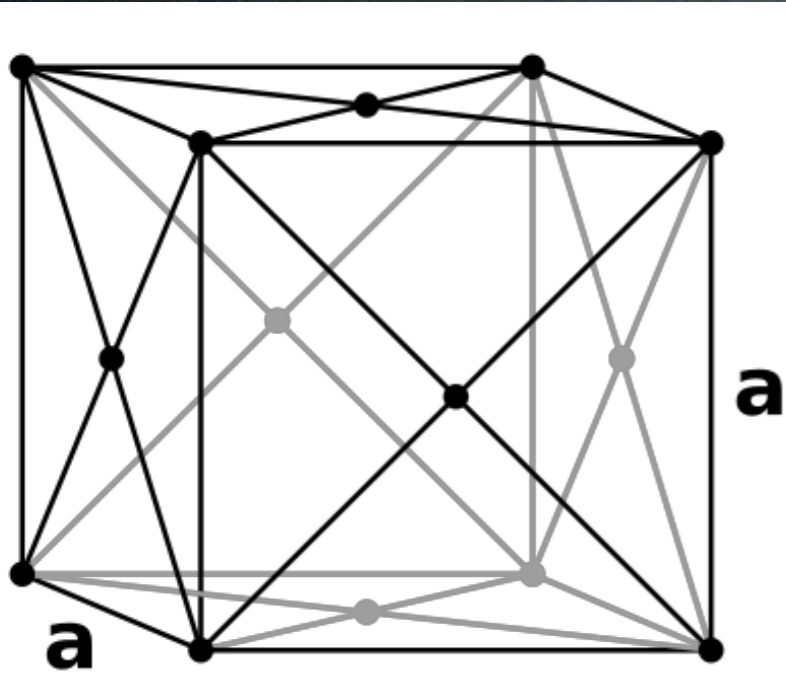
- $\sigma_{\text{lattice}} \sim v^{-2}$
(Rutherford scattering)
- $\sigma_{\text{electron}} \sim v$
(Accessible electron states)

Charge Transport

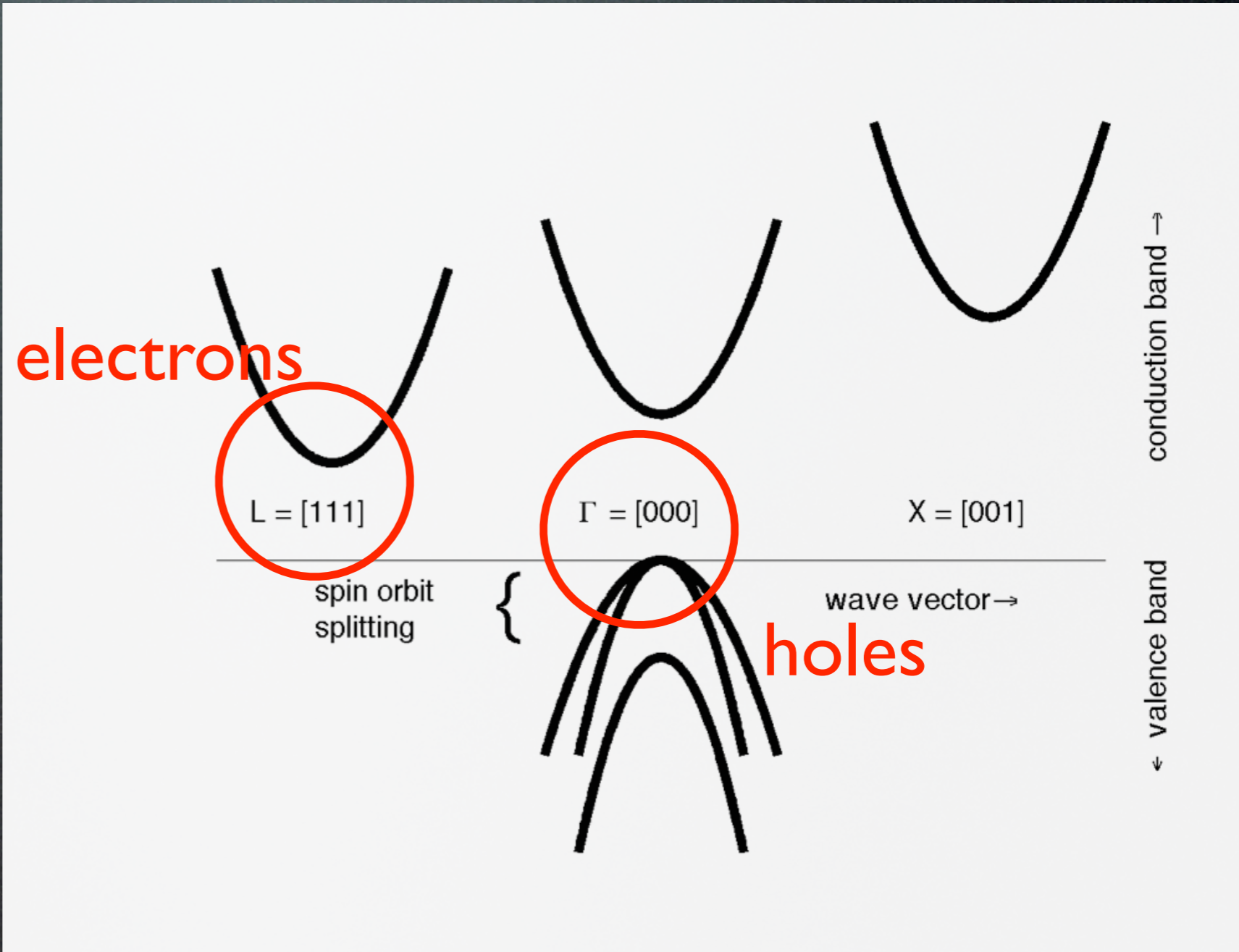
100x33 mm iZIP E-Field



Germanium Band Structure



L valleys of Ge



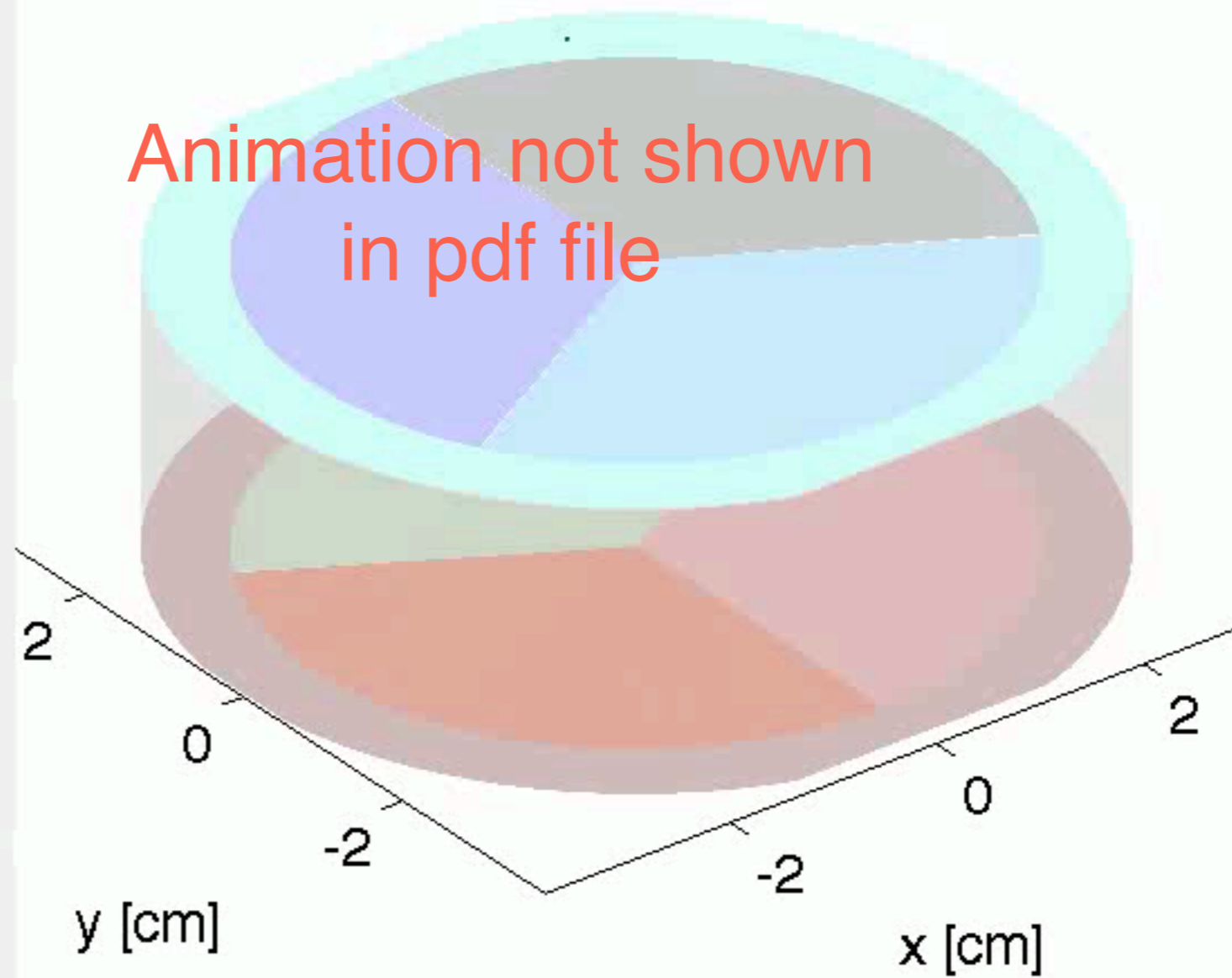
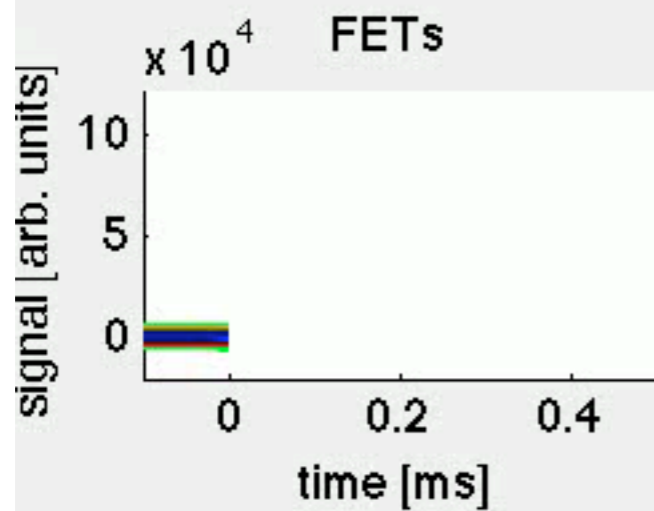
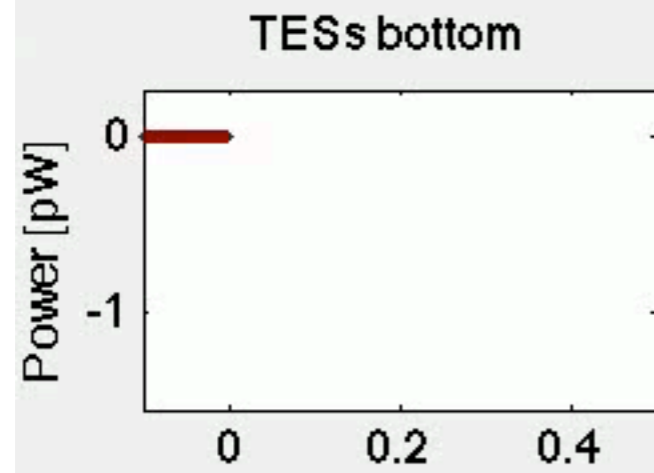
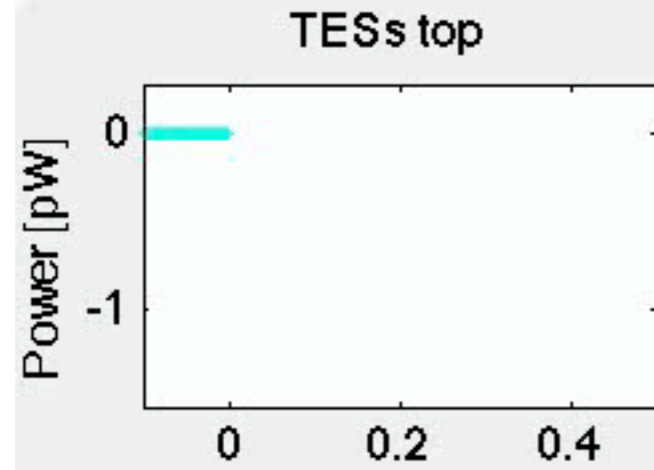
Electron Mass Tensor

- Holes exist in the Γ band with mass scalar, $m = 0.35 m_e$
- In germanium, electrons exist in the L band with mass tensor

$$m = \begin{pmatrix} 1.58 & 0 & 0 \\ 0 & 0.081 & 0 \\ 0 & 0 & 0.081 \end{pmatrix} m_e$$

in the longitudinal (111), transverse,
transverse basis

Animation not shown
in pdf file



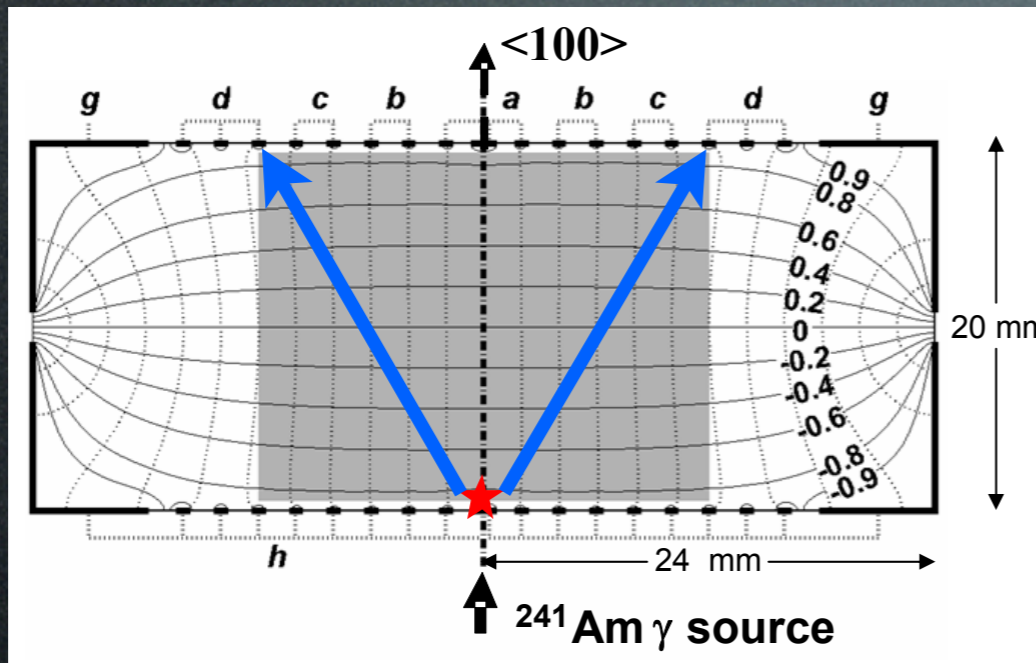
Q top, outer
Q top, inner
Q bottom, inner
Q bottom, outer

fast transverse
slow transverse
longitudinal
 $t = 1.7e-10$

Inter-valley Scattering

- 4 different valleys $[111]$, $[\bar{1}11]$, $[1\bar{1}1]$, $[\bar{1}\bar{1}1]$
- Can scatter between valleys at high energy or near impurities

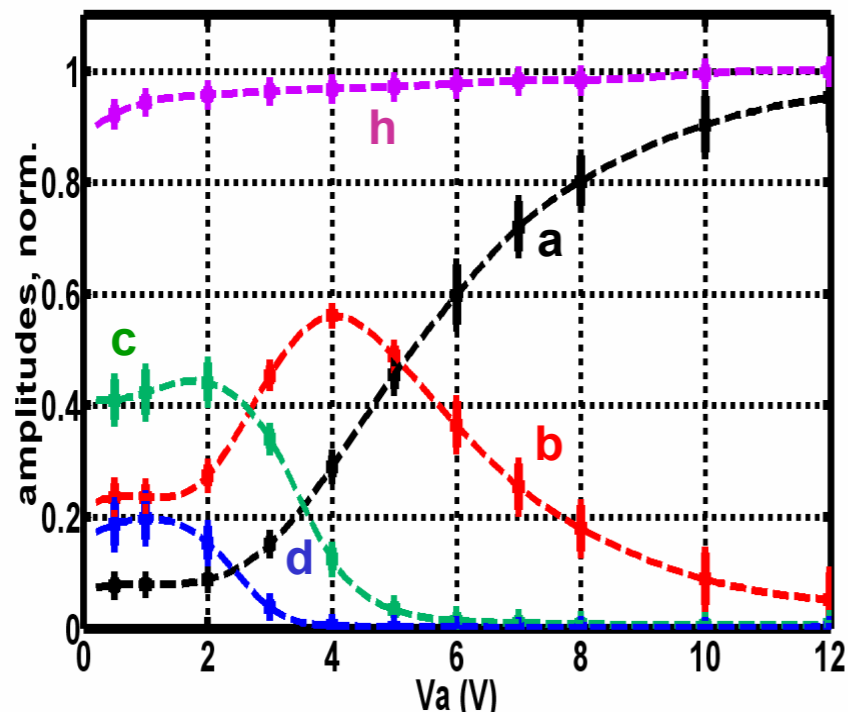
Edelweiss Measurement



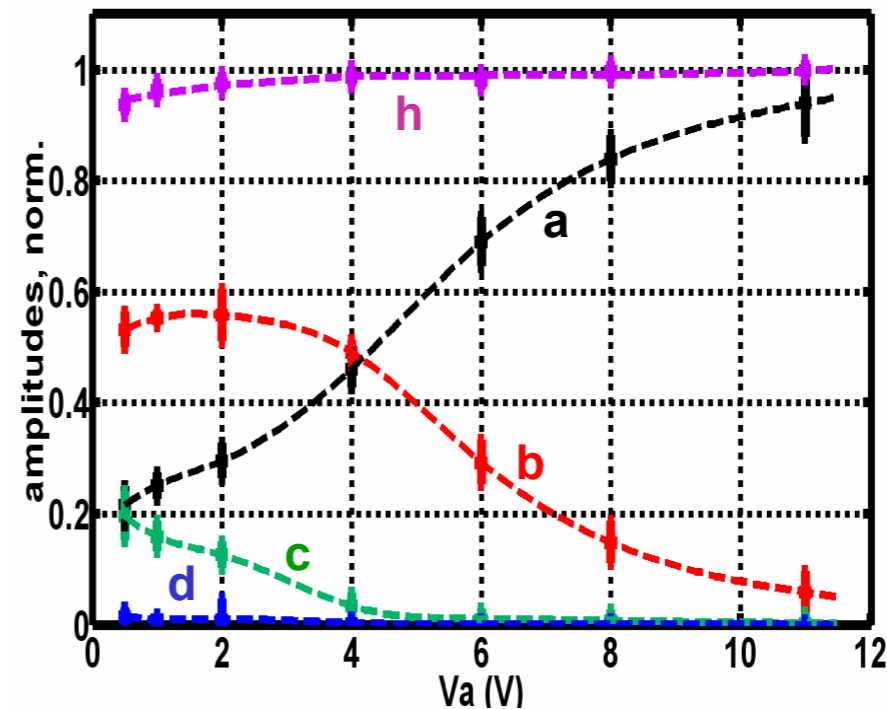
Signal entirely in **d**
if no IV scattering

Increased signal in **a**
with increased field

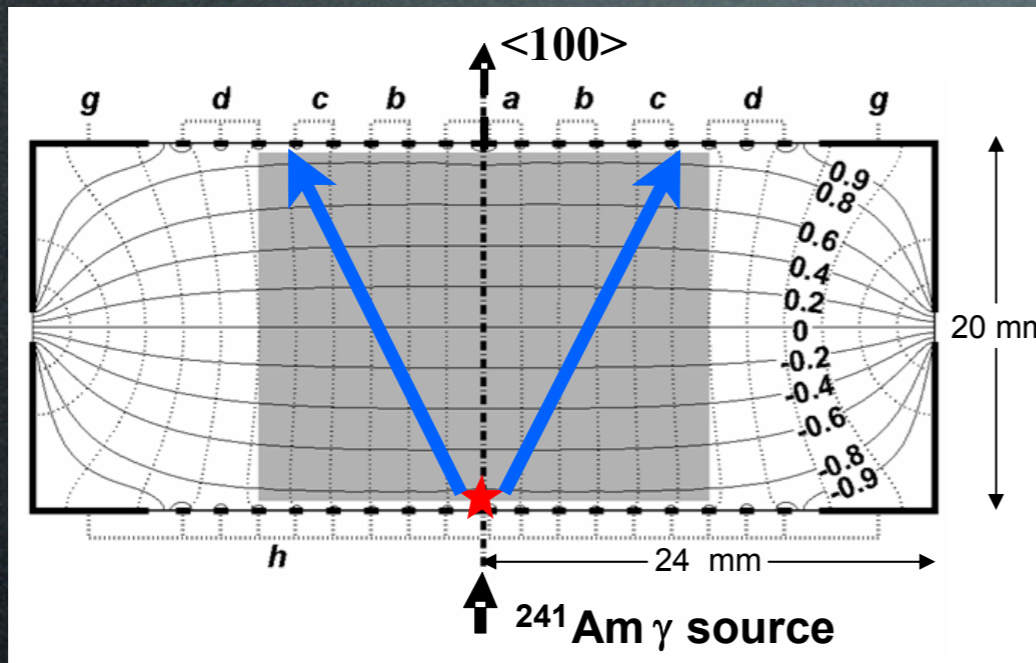
(a) ID203 (*p*-type Ge, In doped to 10^{11} cm^{-3})



(b) ID201 (*n*-type, high-purity $|N_a - N_d| < 10^{10} \text{ cm}^{-3}$)



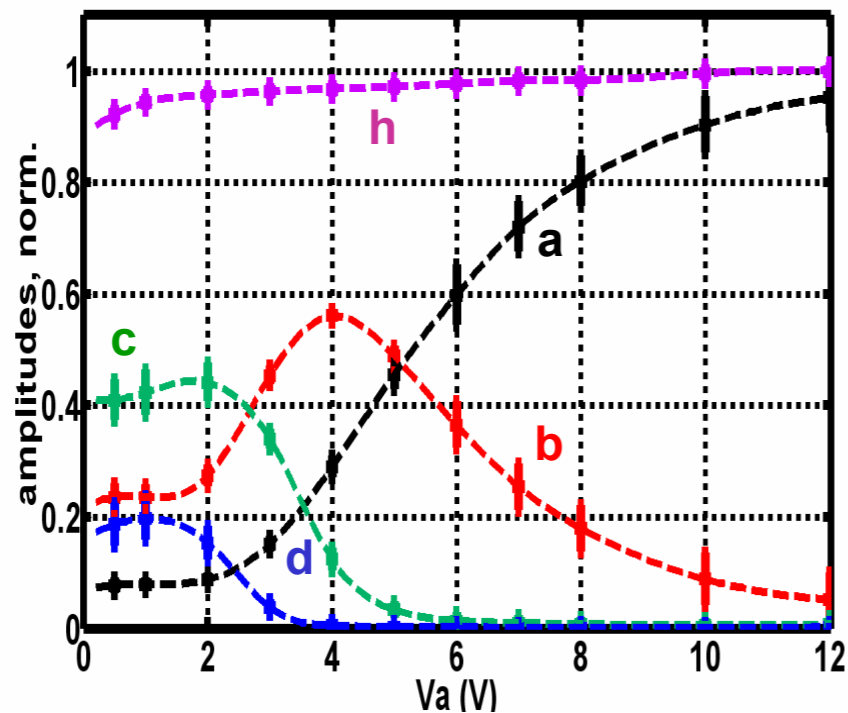
Edelweiss Measurement



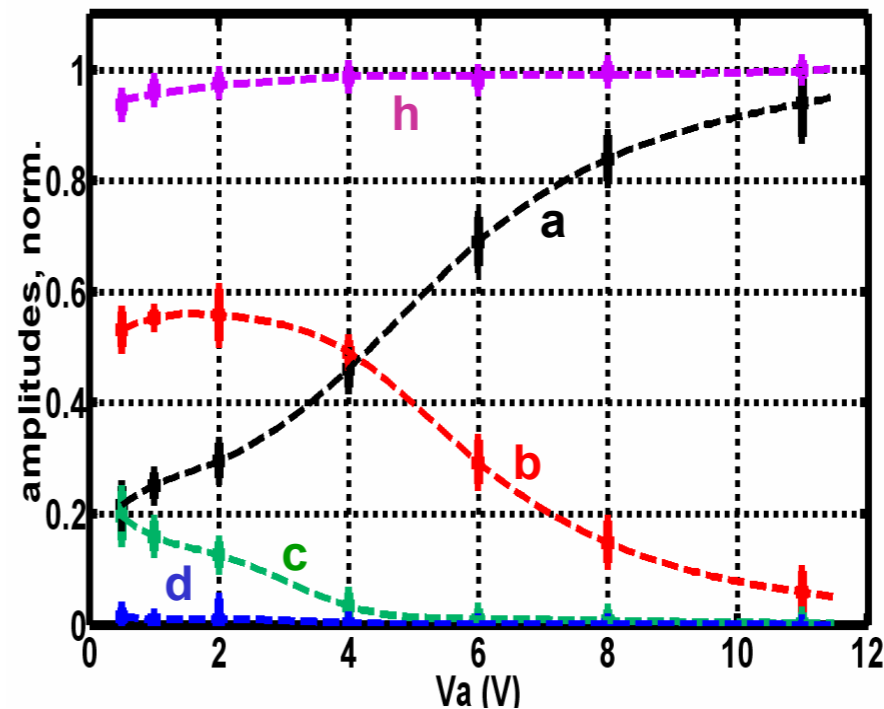
Signal entirely in **d**
if no IV scattering

Increased signal in **a**
with increased field

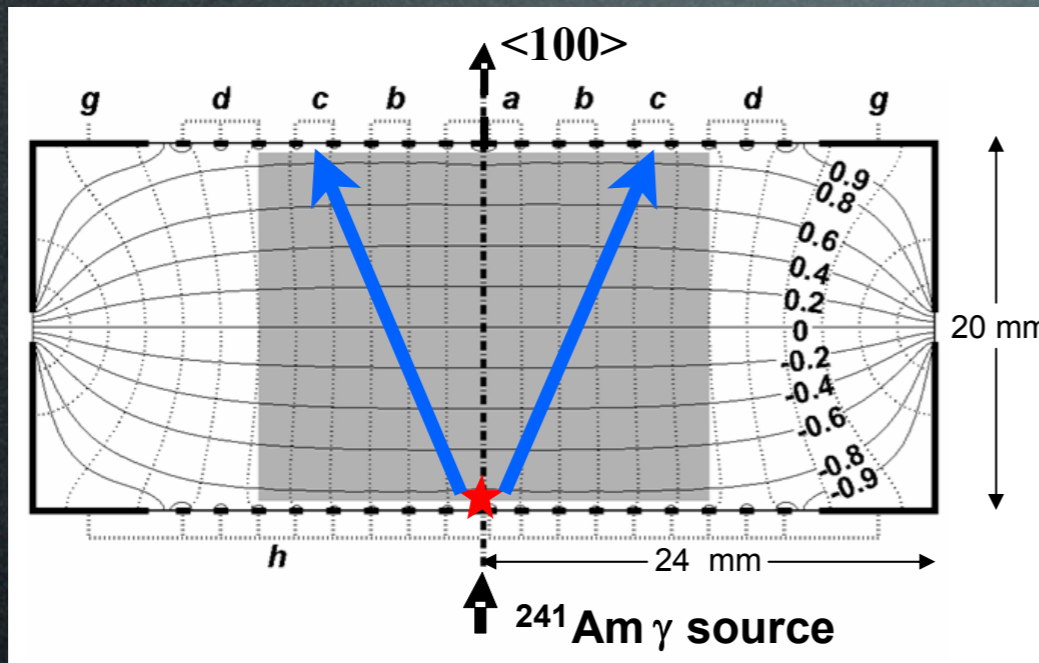
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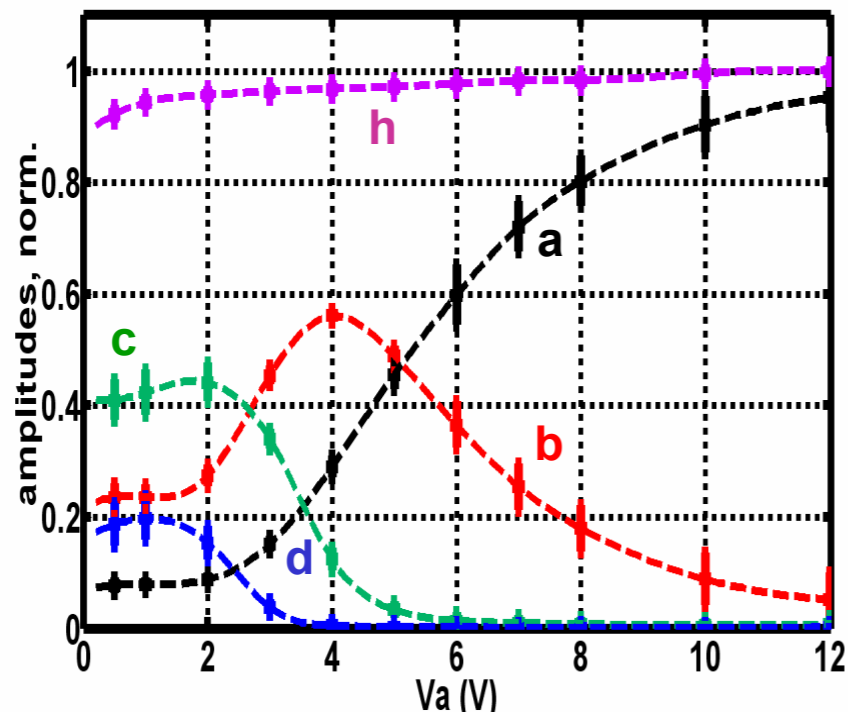
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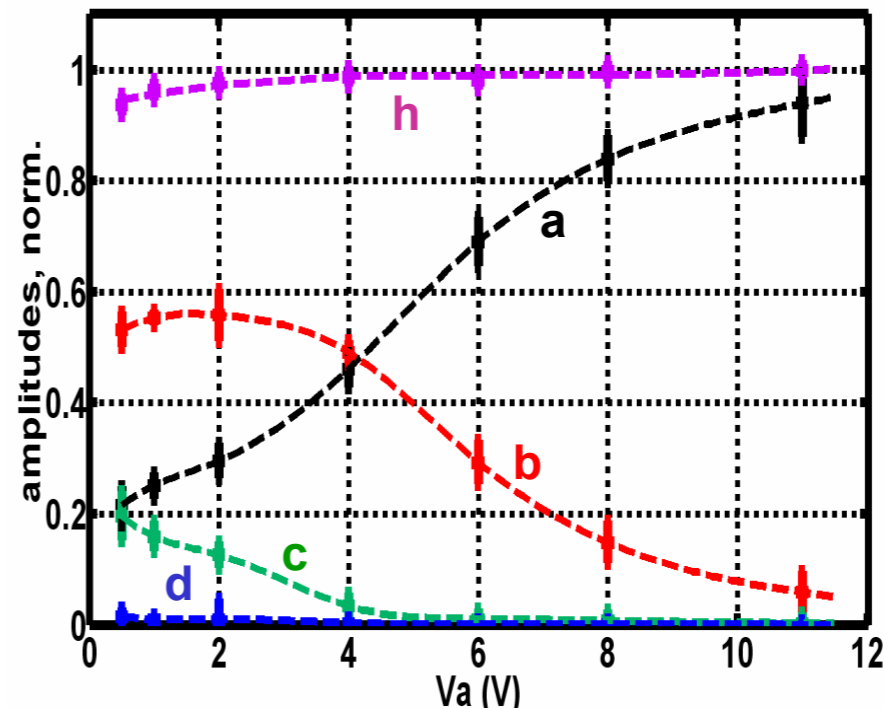
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with increased field

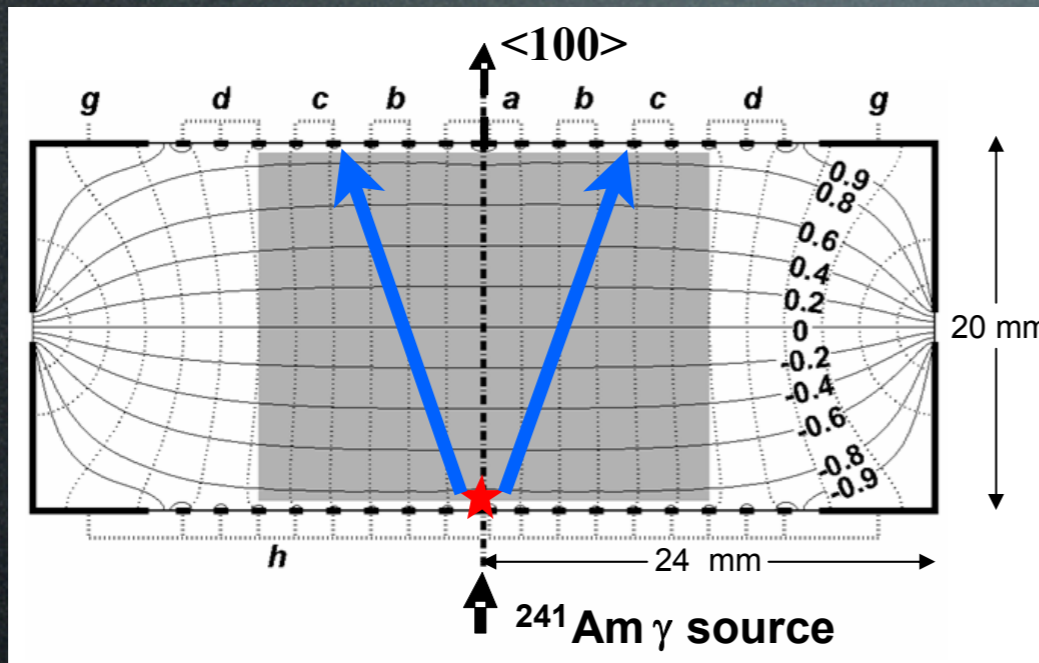
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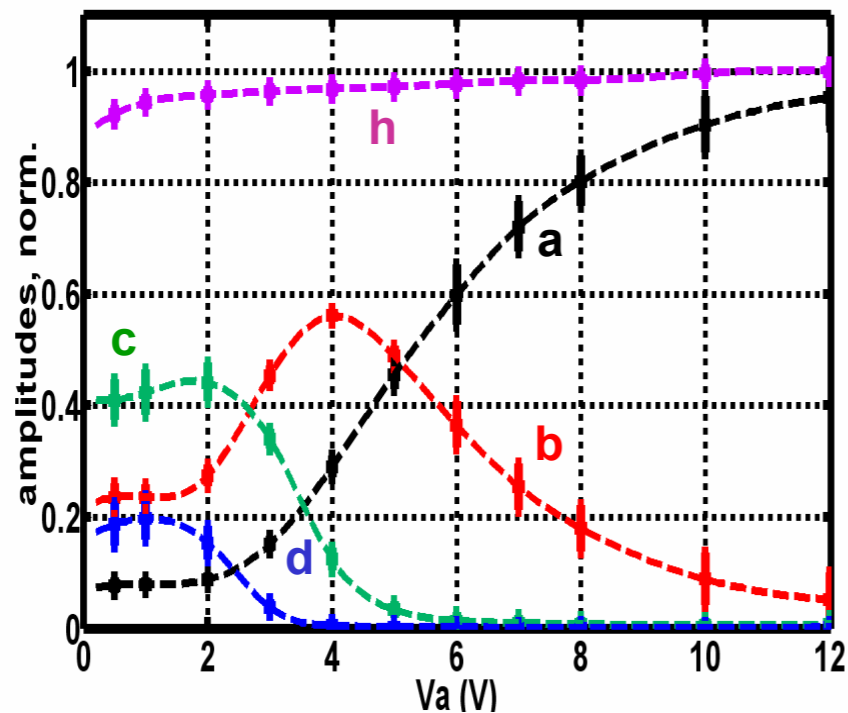
Edelweiss Measurement



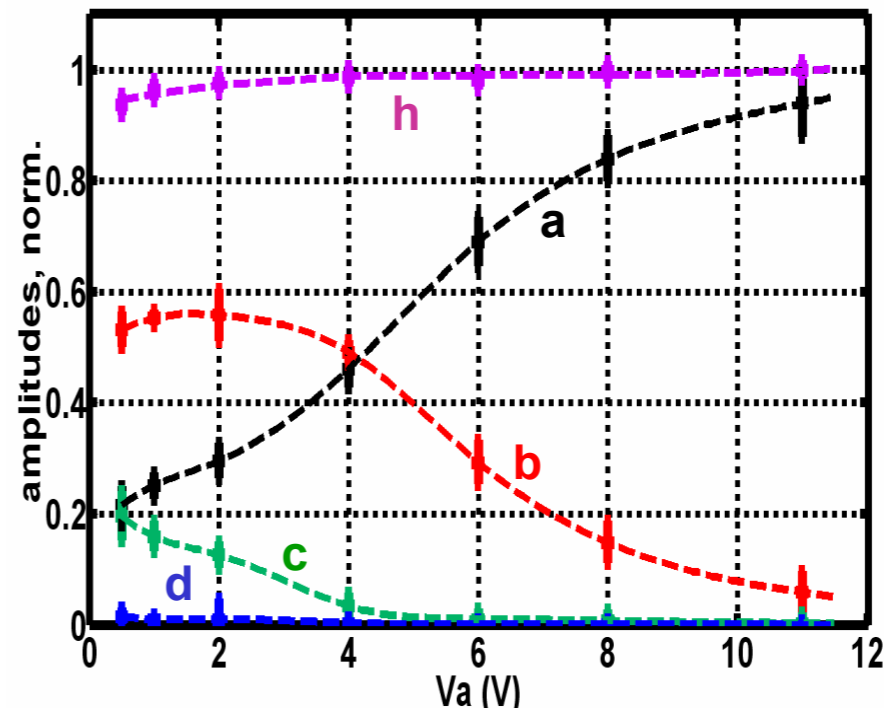
Signal entirely in **d**
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Increased signal in **a**
with increased field

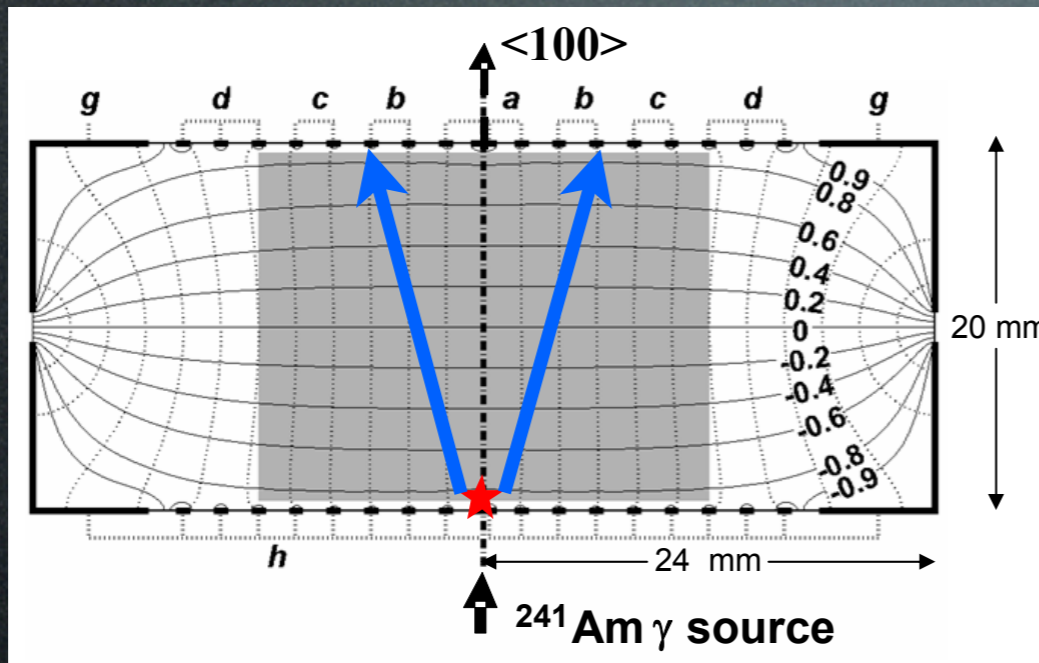
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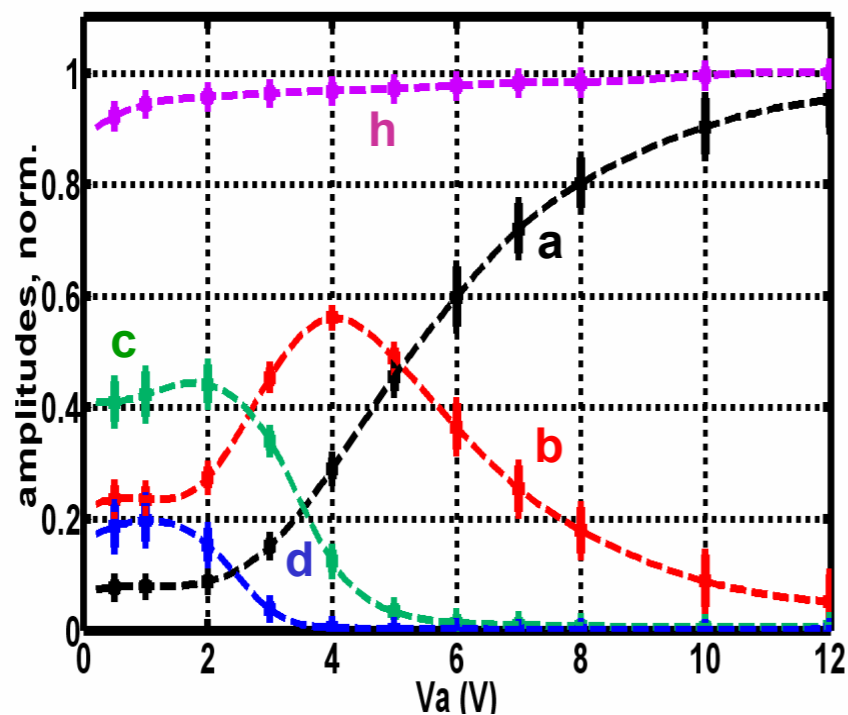
Edelweiss Measurement



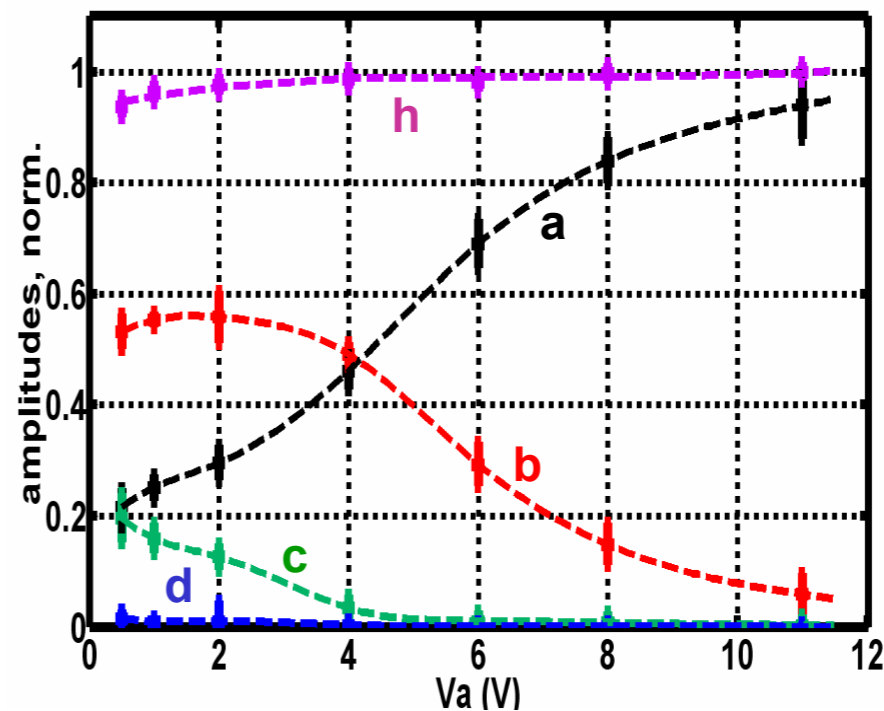
Signal entirely in **d**
if no IV scattering

Increased signal in **a**
with increased field

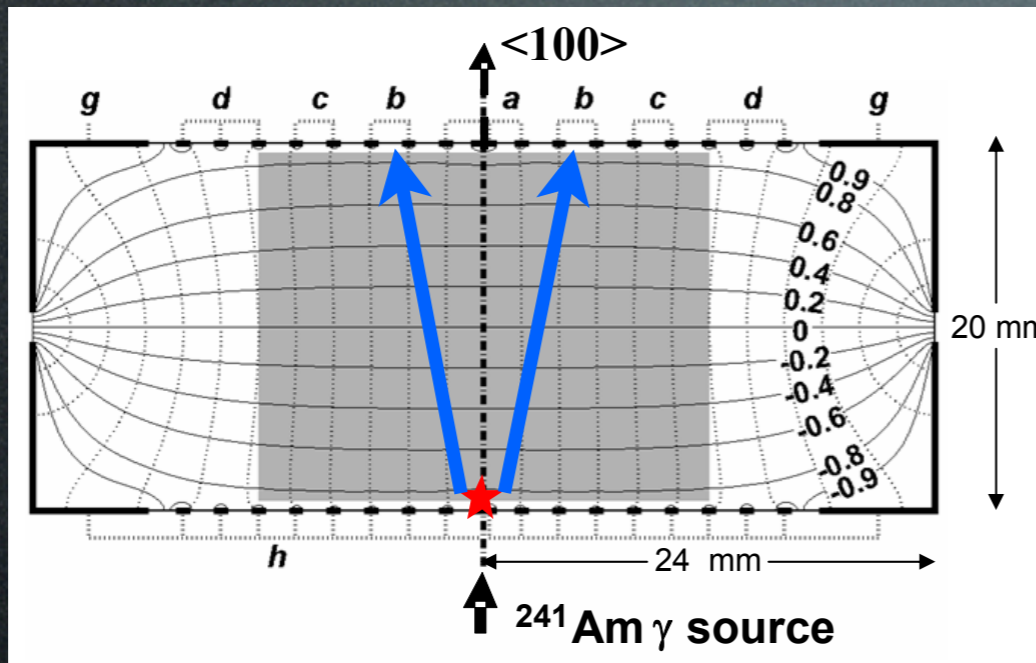
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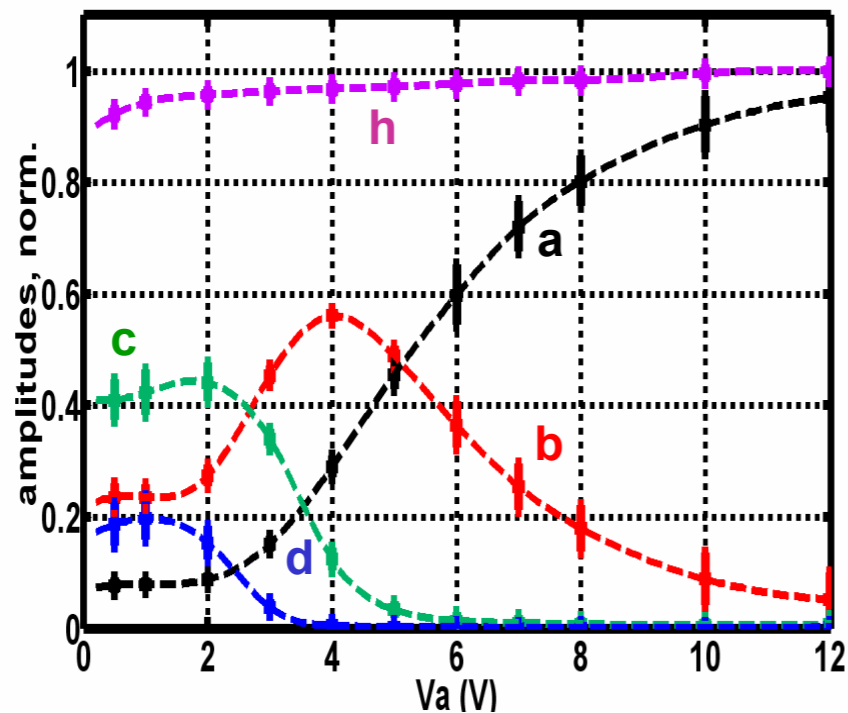
Edelweiss Measurement



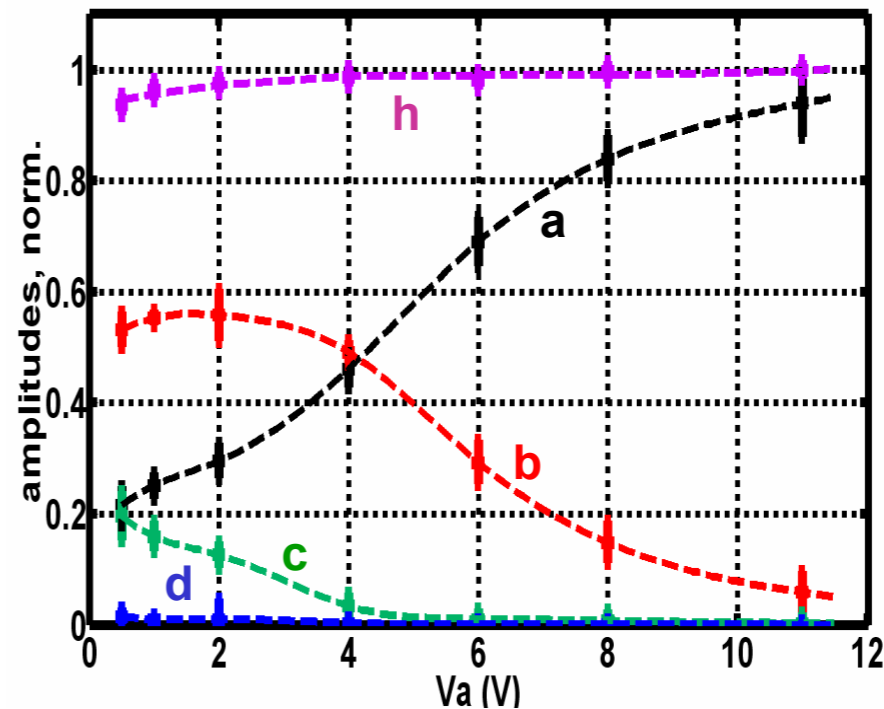
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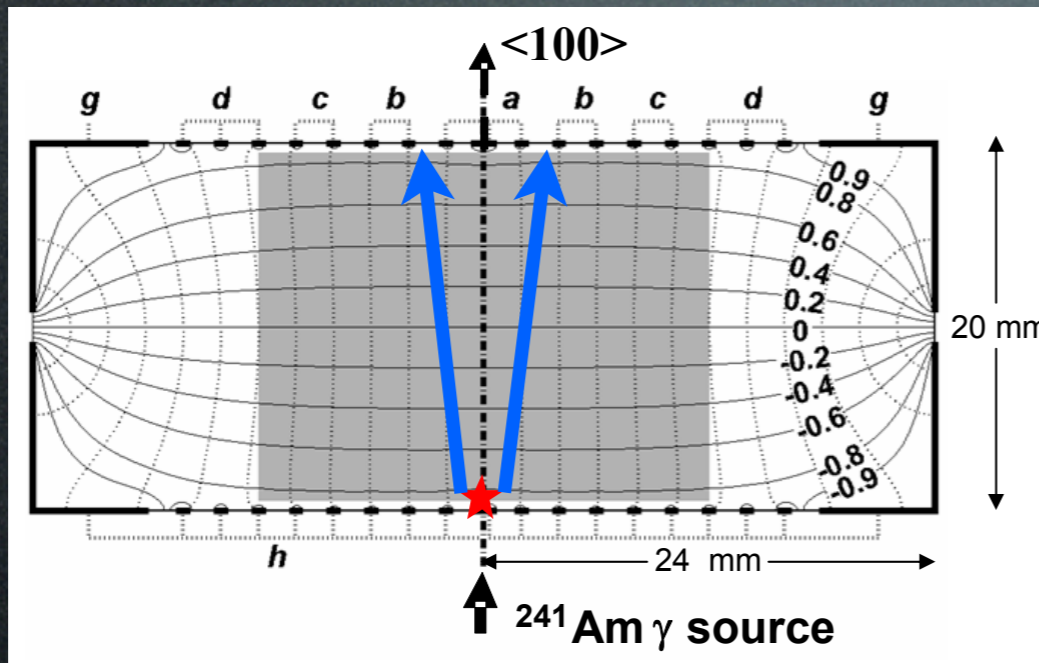
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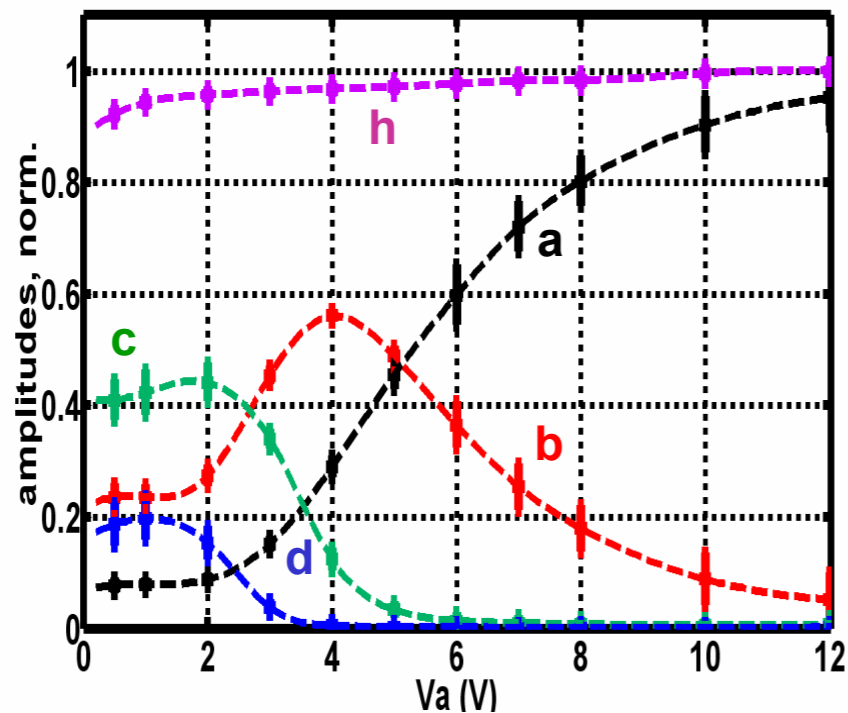
Edelweiss Measurement



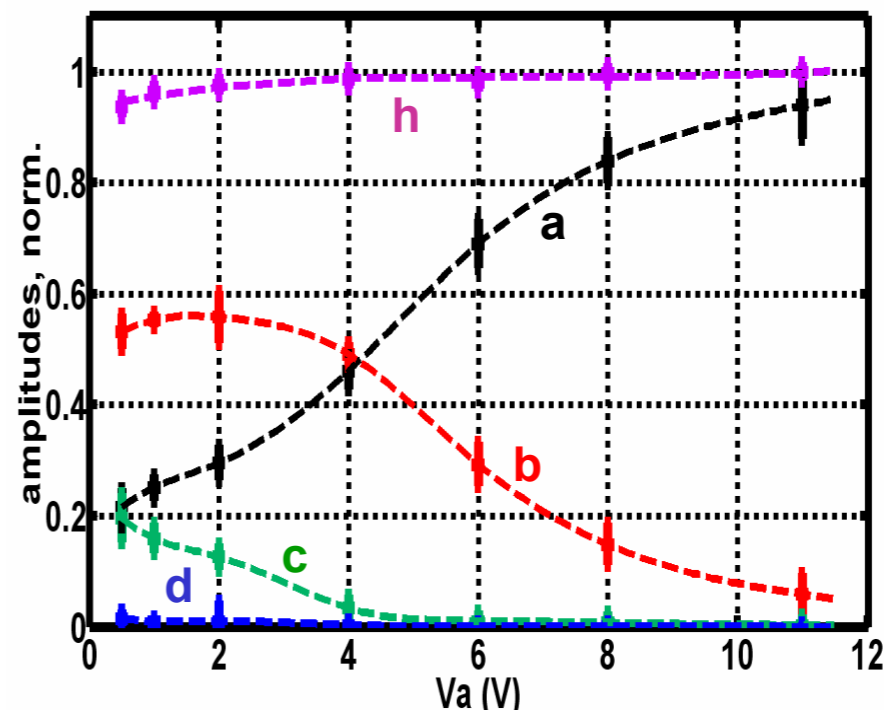
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if no IV scattering

Increased signal in **a**
with increased field

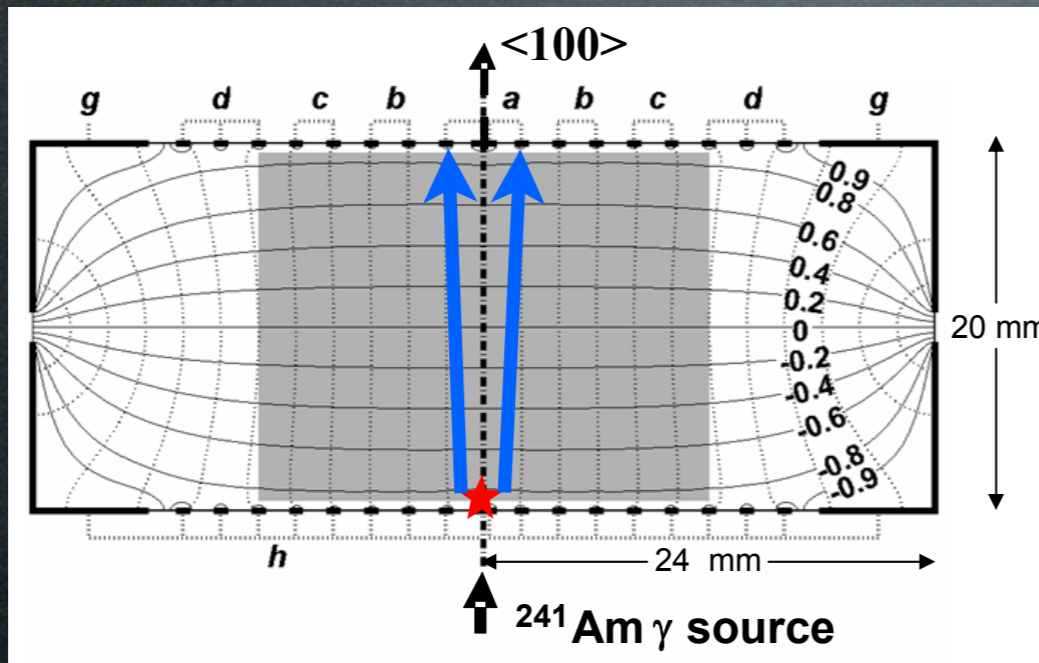
(a) ID203 (*p*-type Ge, In doped to 10^{11} cm^{-3})



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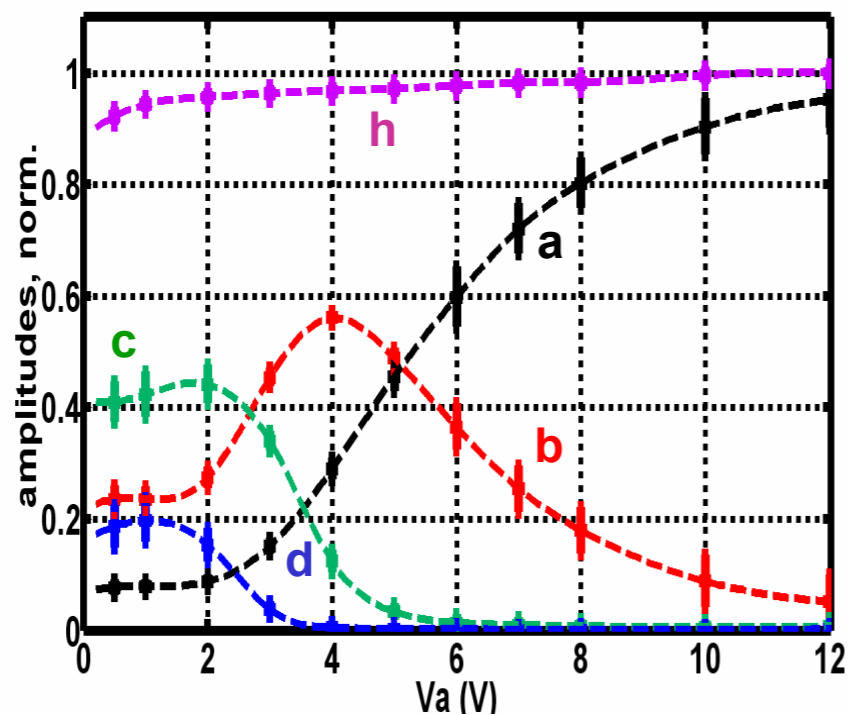
Edelweiss Measurement



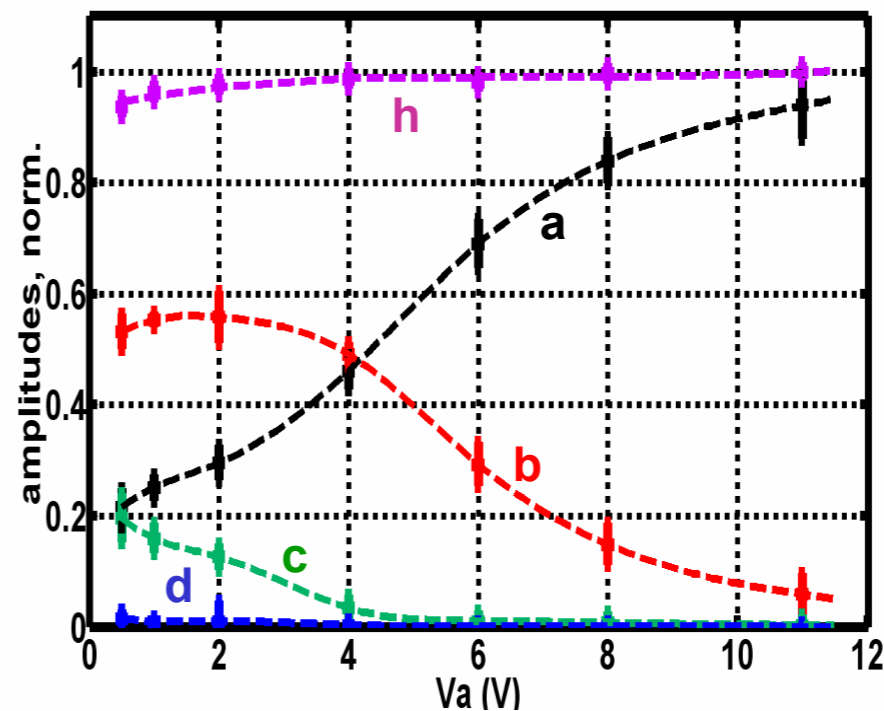
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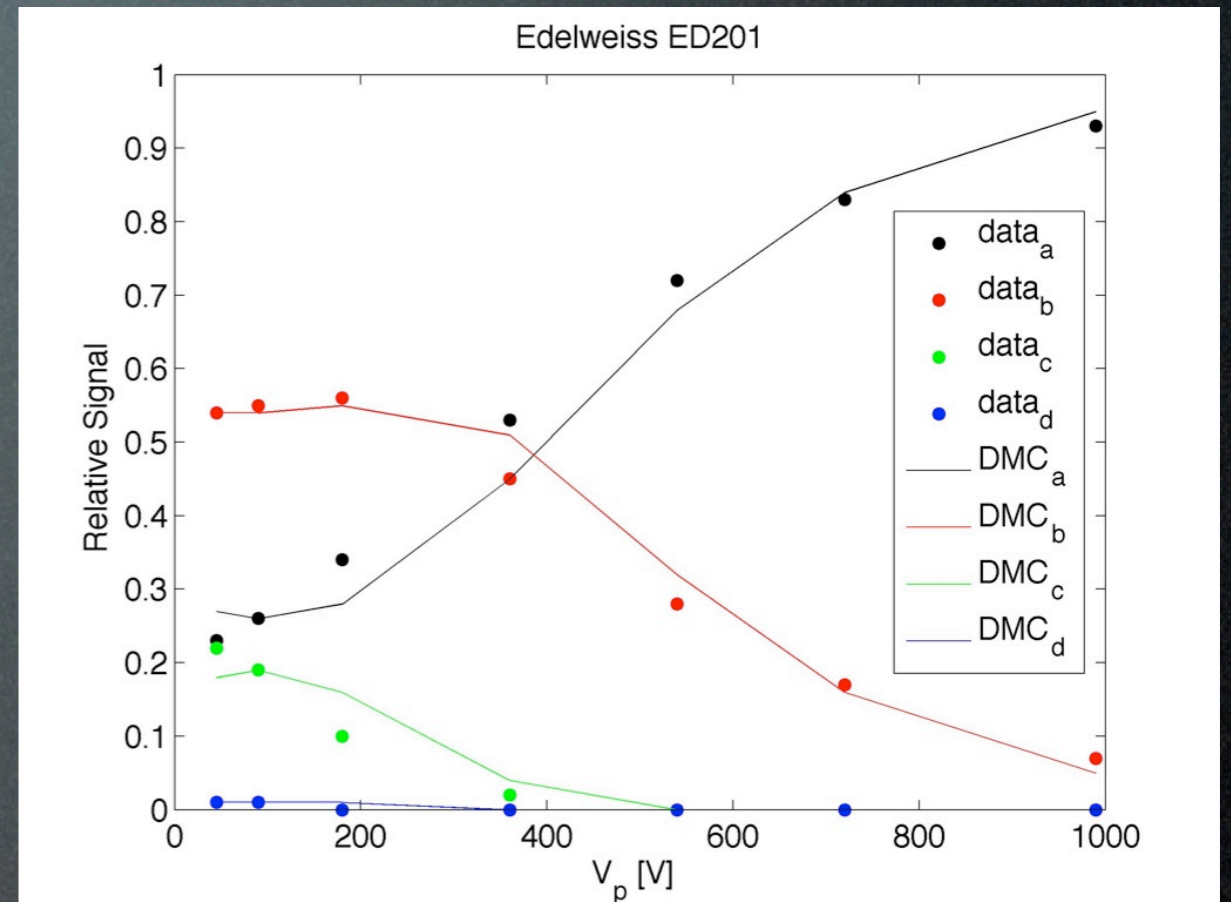
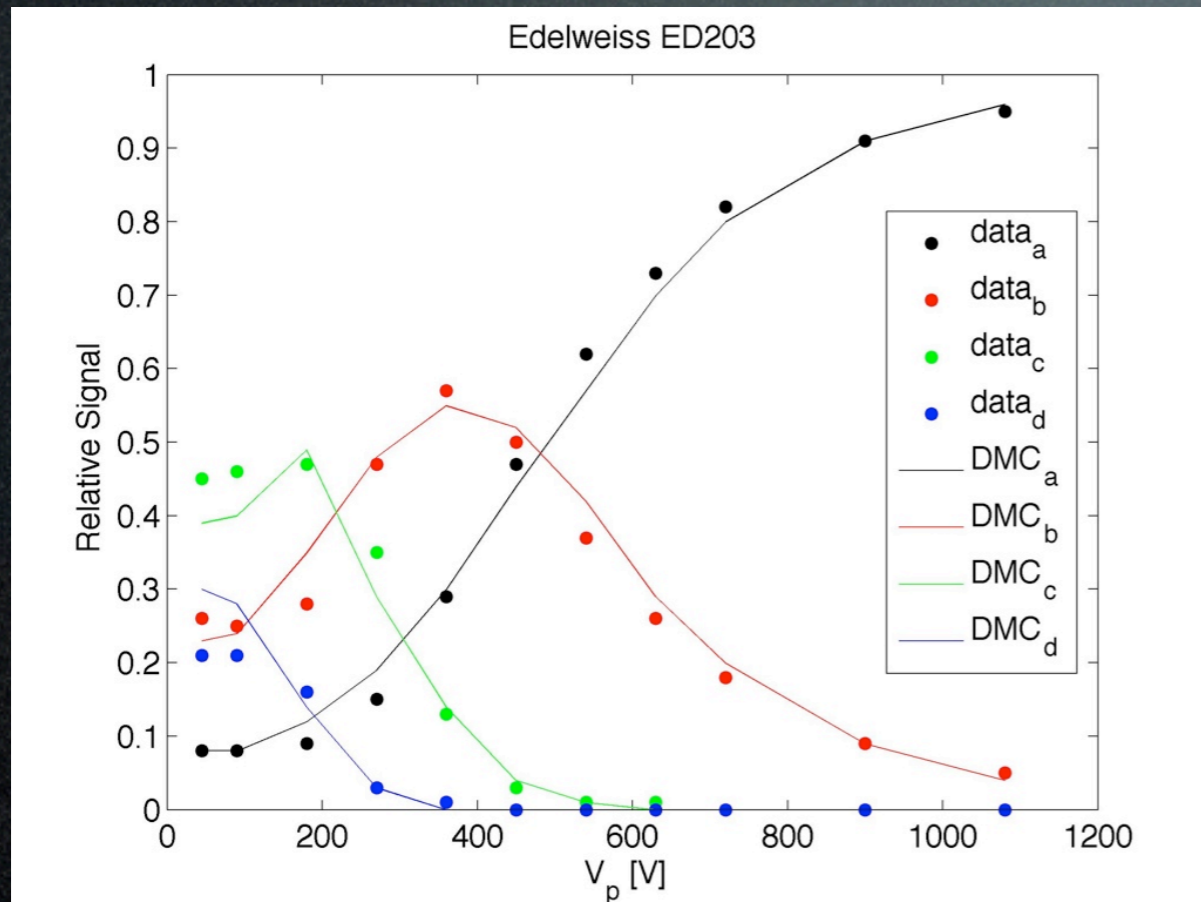
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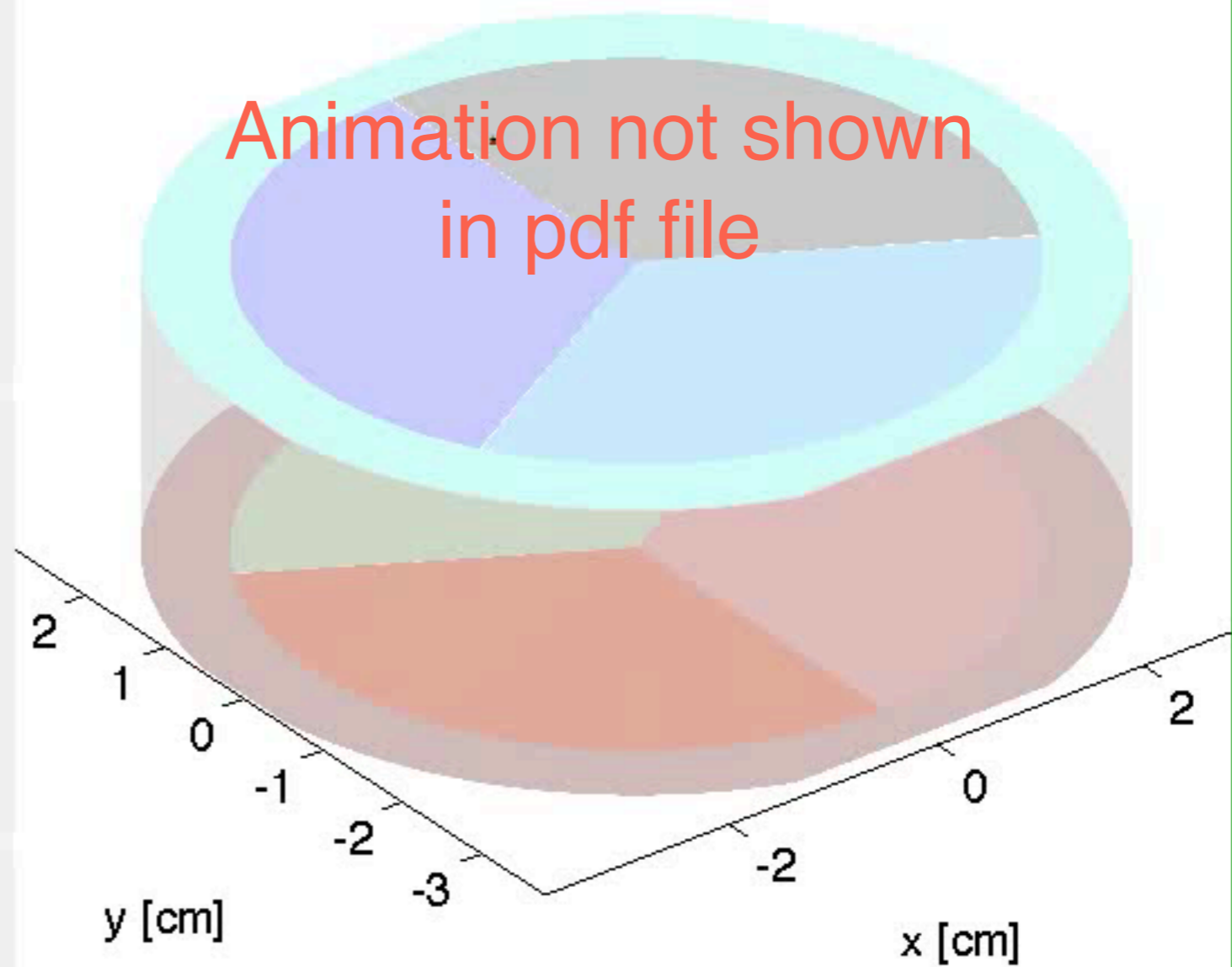
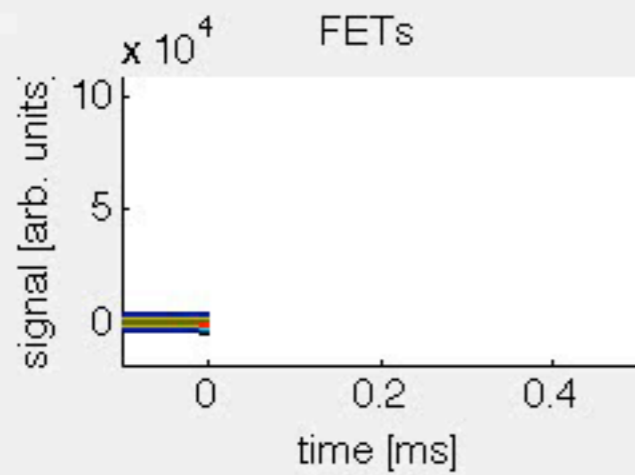
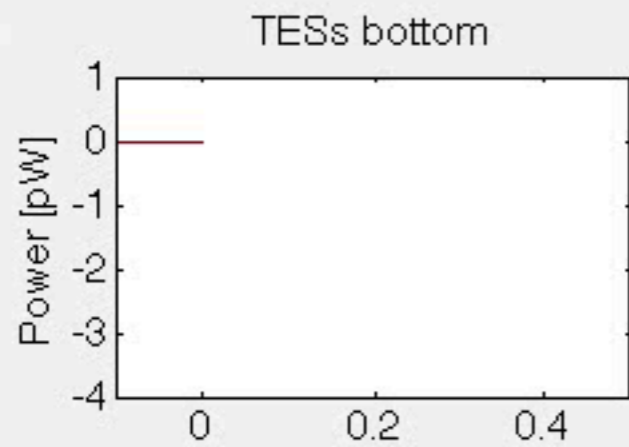
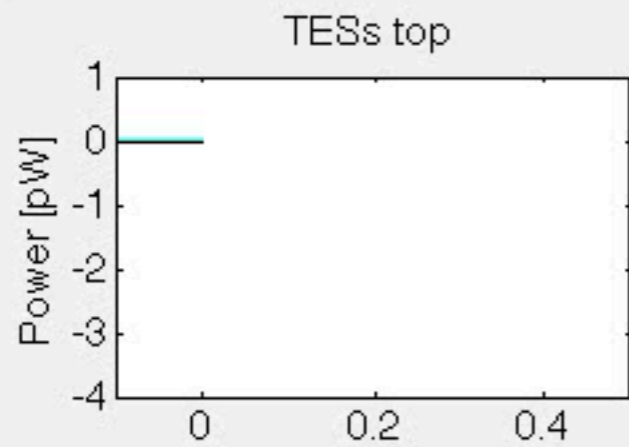


Signal vs Bias Voltage



- $\sigma = 6.72e-2 [s^{-1}] (E_0^2 + |E_{HV}|^2)^{3.24/2}$
- $E_{0,ED203} = 217, E_{0,ED201} = 352$

Animation not shown
in pdf file



- Q top, outer
- Q top, inner
- Q bottom, inner
- Q bottom, outer

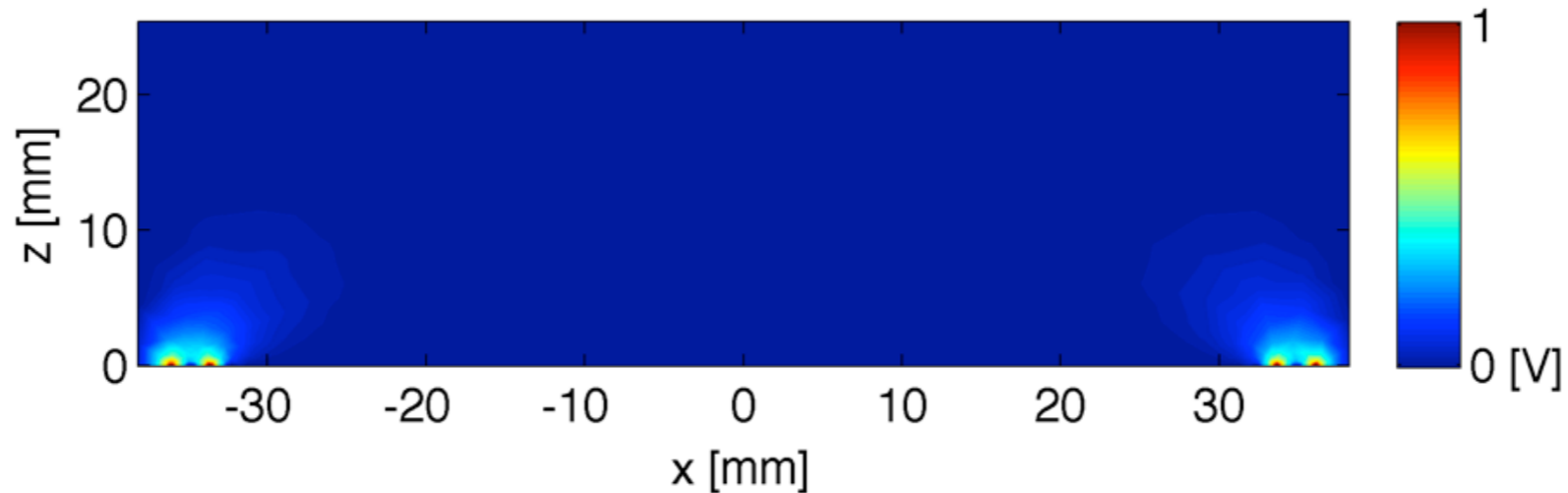
- fast transverse
- slow transverse
- longitudina
- $t = 1.7e-10$

Charge Readout

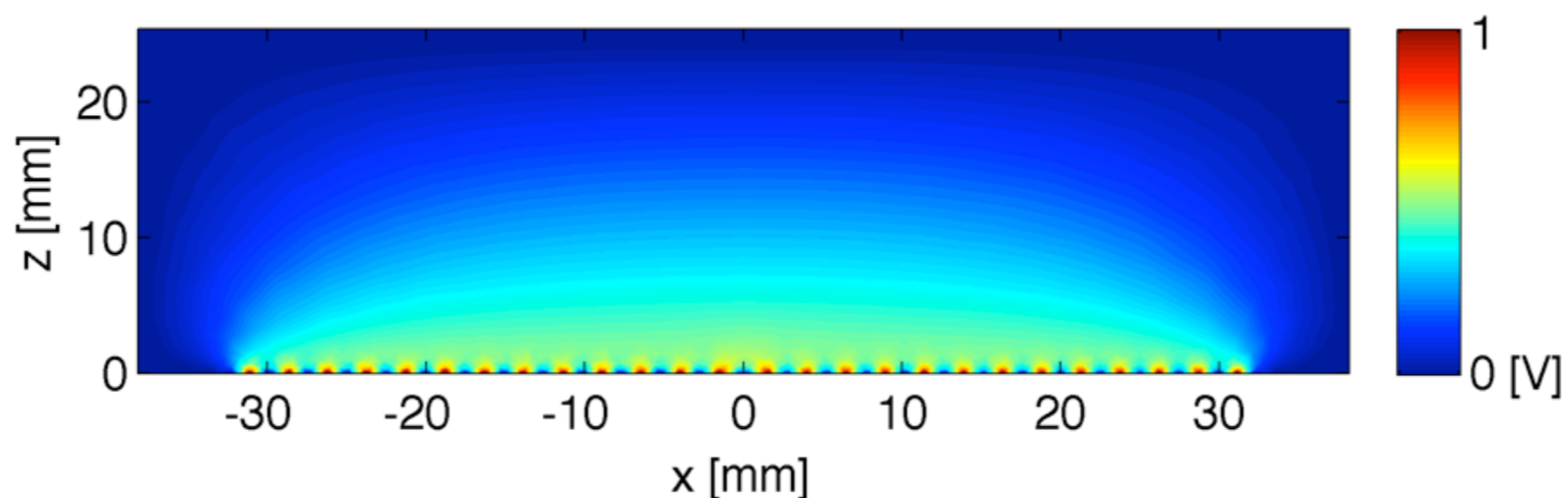
Ramo-Shockley Potentials

$$\text{signal}_i(t) = \sum_j V_{i,\text{hole}_j}(t) - V_{i,\text{electron}_j}(t)$$

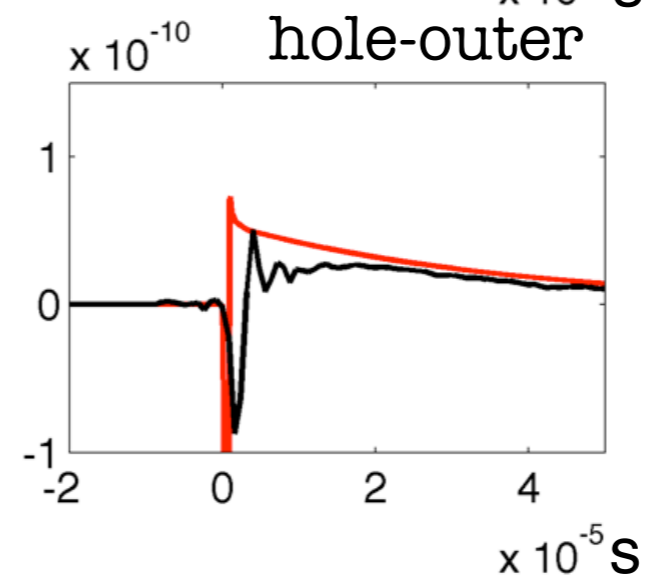
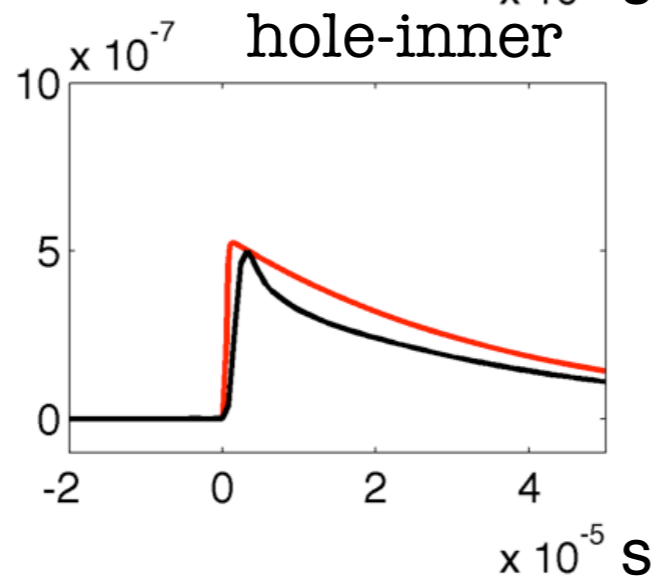
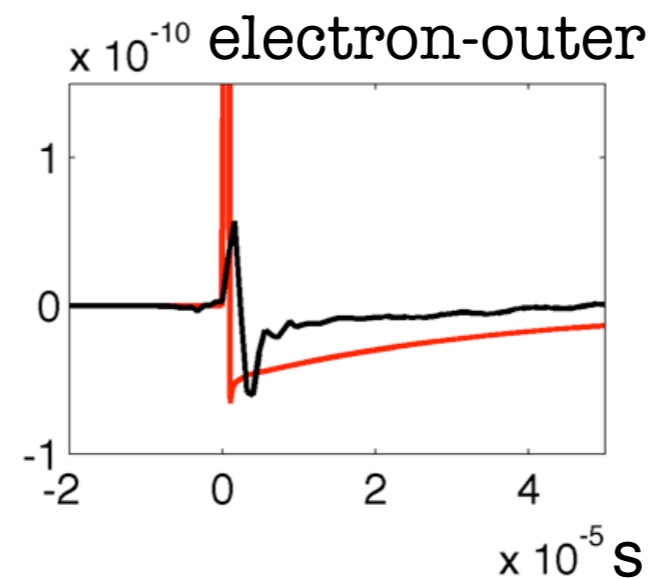
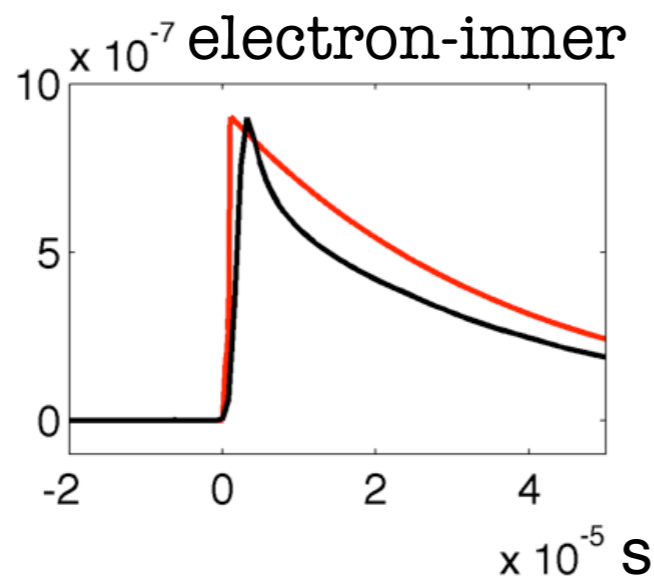
Outer Channel Ramo Potential



Inner Channel Ramo Potential



Tracking of Charges Through Ramo-Shockley Potentials

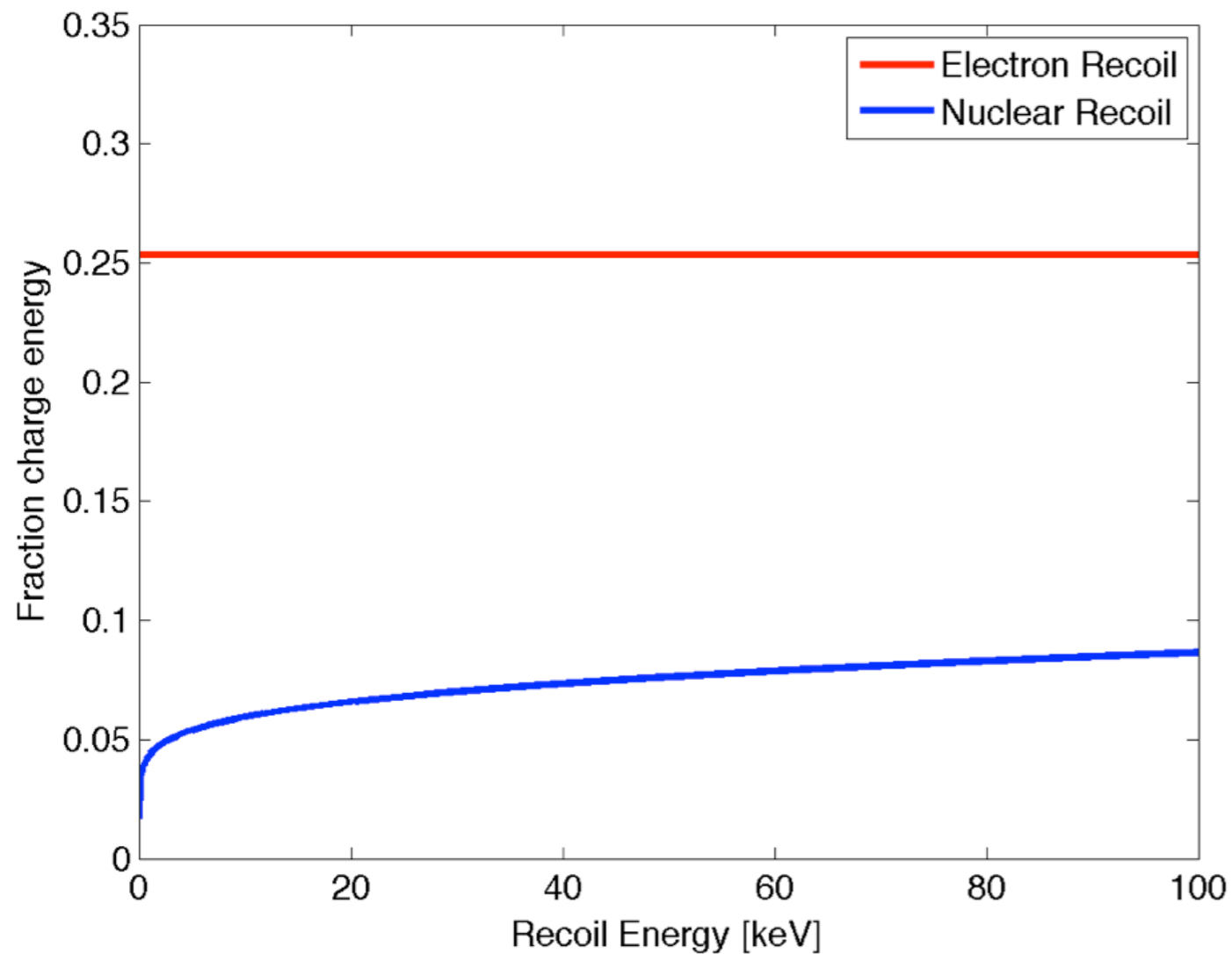


calibration

MC

Phonon Production

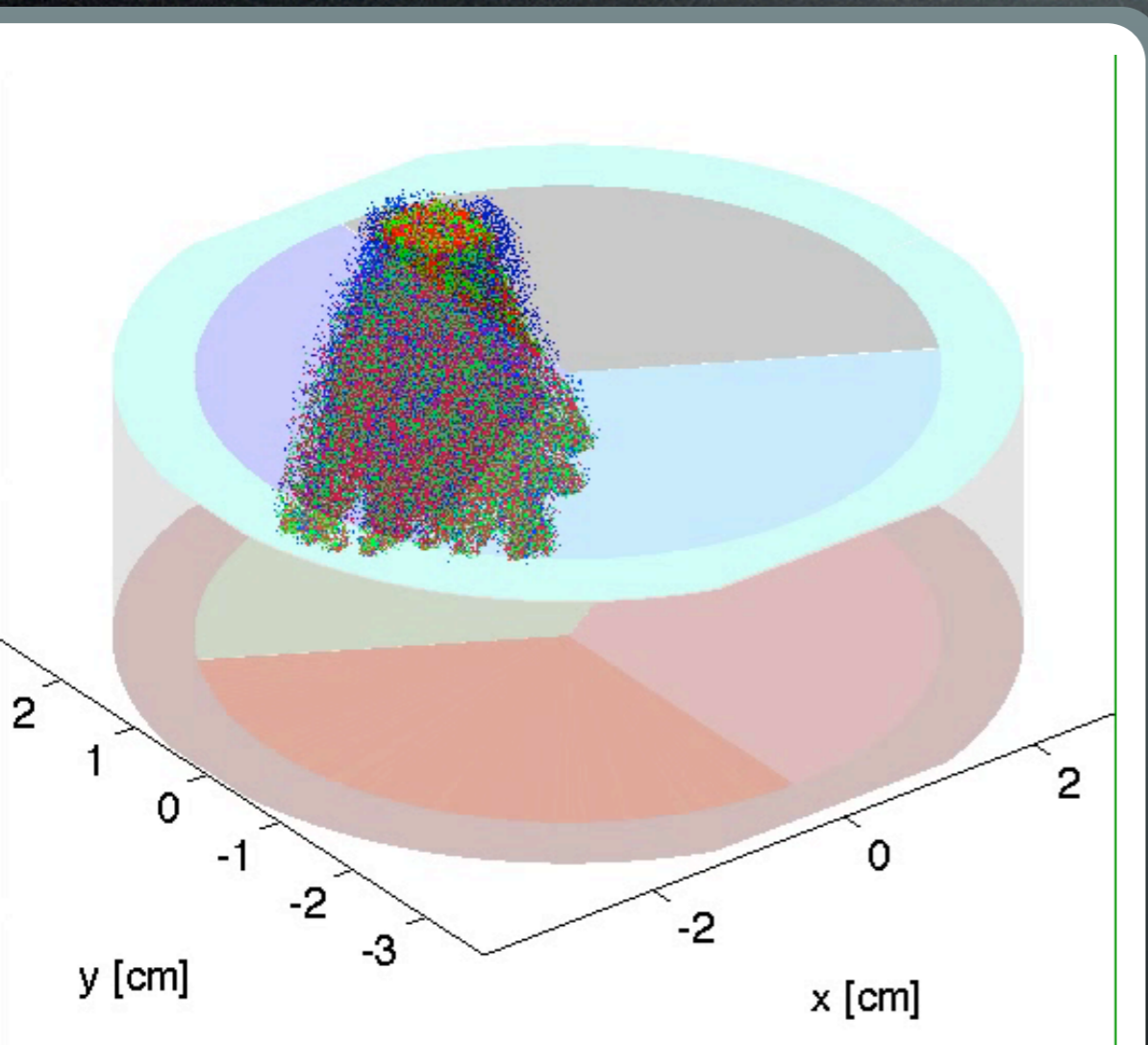
Lindhard Theory



- Prompt phonons produced at Debye frequency.
- Details quickly wash out due to downconversion.

Neganov-Luke Phonons

$$P_{k, k' \pm q} = \frac{2\pi V}{\hbar} \left| \langle \vec{k} \pm \vec{q} | H | \vec{k} \rangle \right|^2 \delta(E - E' \mp \hbar\omega)$$

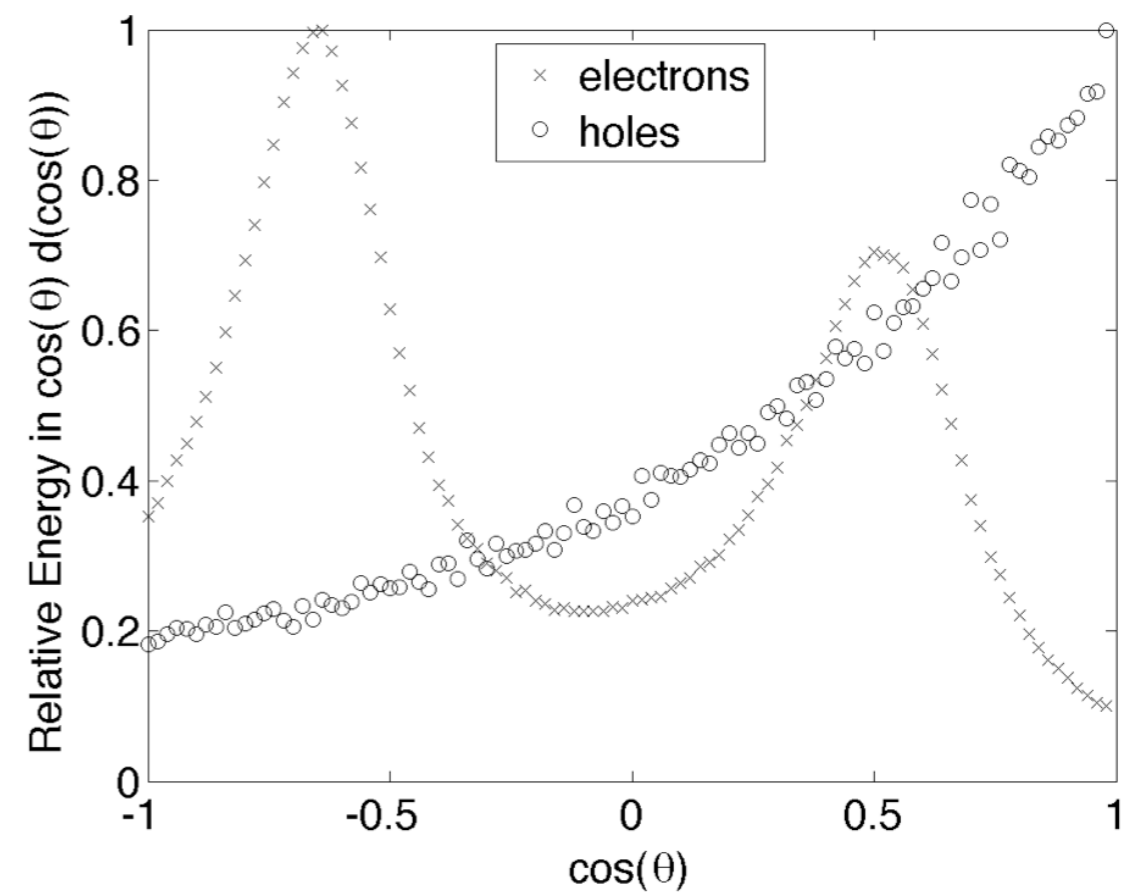
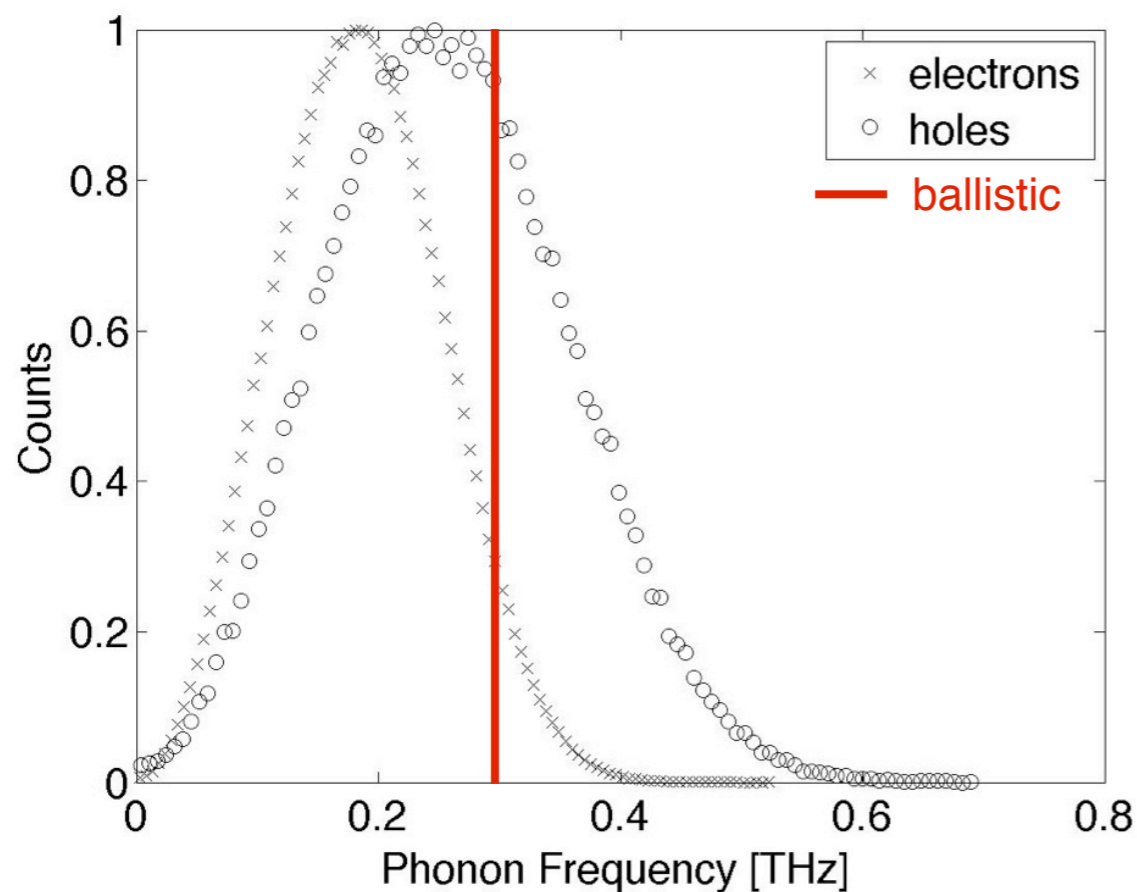


From Fermi's Golden Rule

Angles given by energy -
momentum conservation

Neganov-Luke Phonons

- Ballistic and directed in $\pm z$ direction



Phonon Transport

Phase Velocities

$$\rho\omega^2 \epsilon_\mu = \sum_{\tau} \left(\sum_{\sigma\nu} c_{\mu\sigma\nu\tau} k_\sigma k_\nu \right) \epsilon_\tau$$

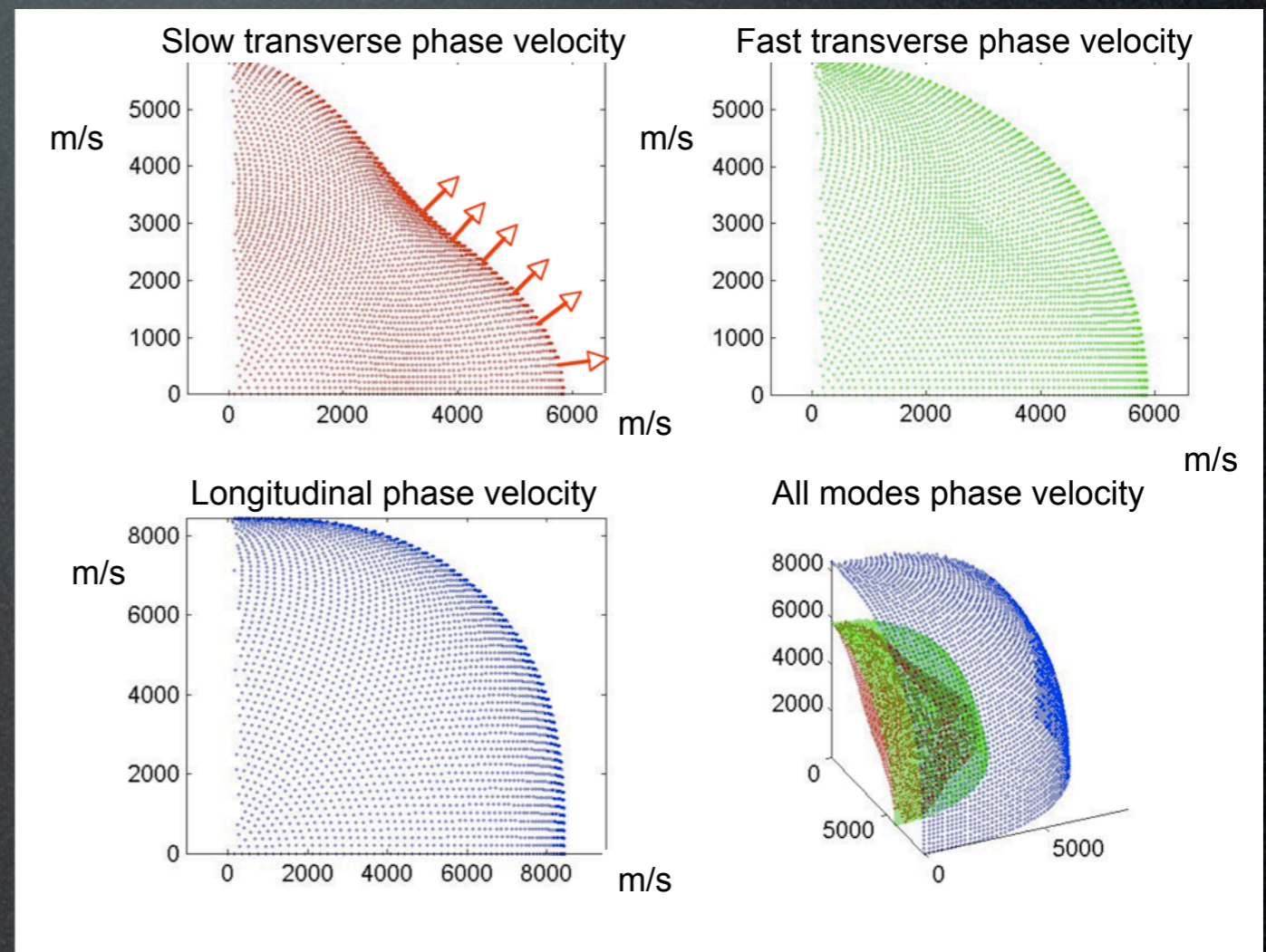
ρ = density

ω = phonon
frequency

ϵ = polarization
vector

c = elastic constants

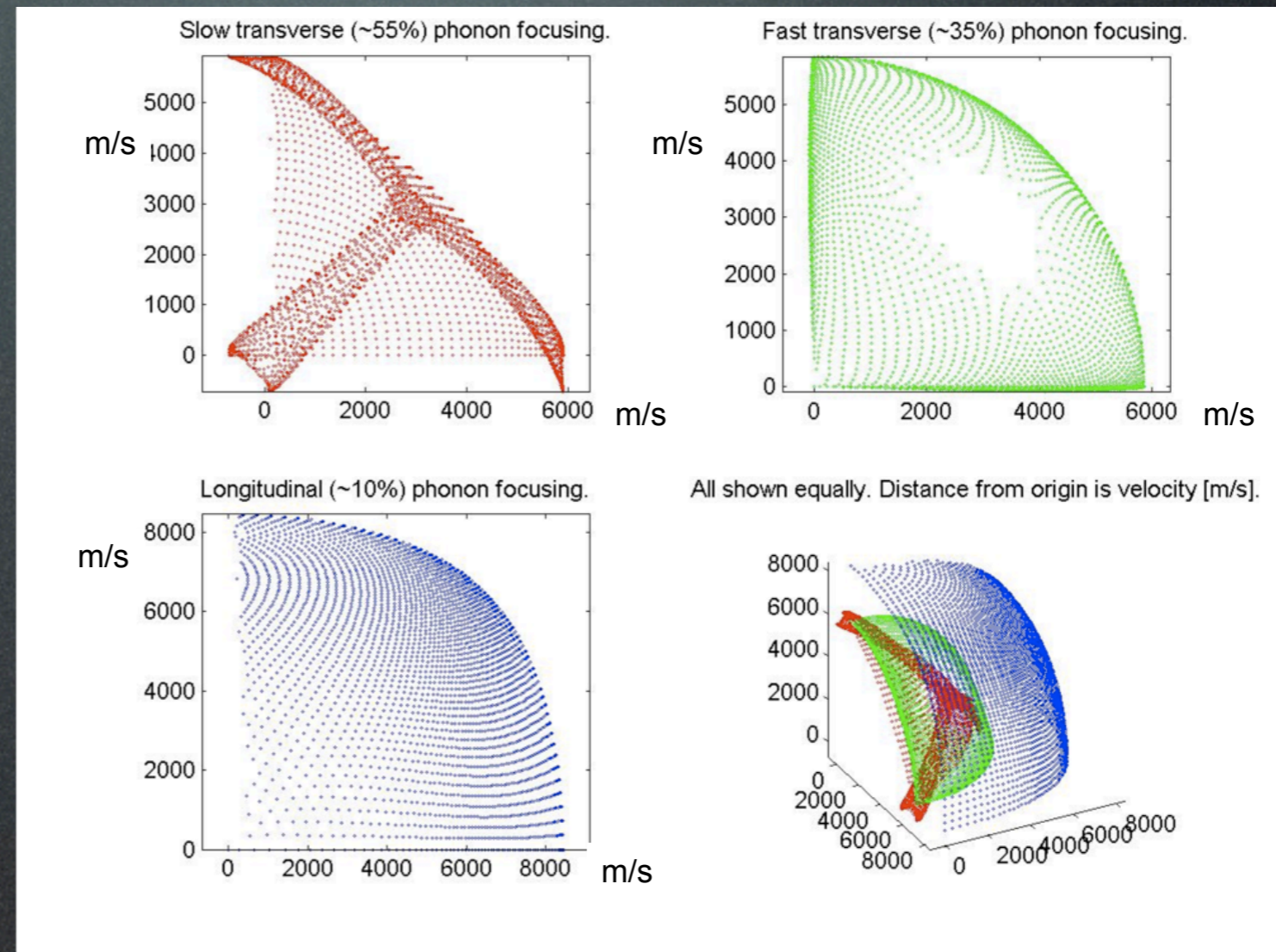
k = wave vector



Group Velocity

$$\vec{v}_p = \frac{\omega(\theta, \phi)}{\vec{k}}$$

$$\vec{v}_g = \frac{d\omega(\theta, \phi)}{d\vec{k}}$$



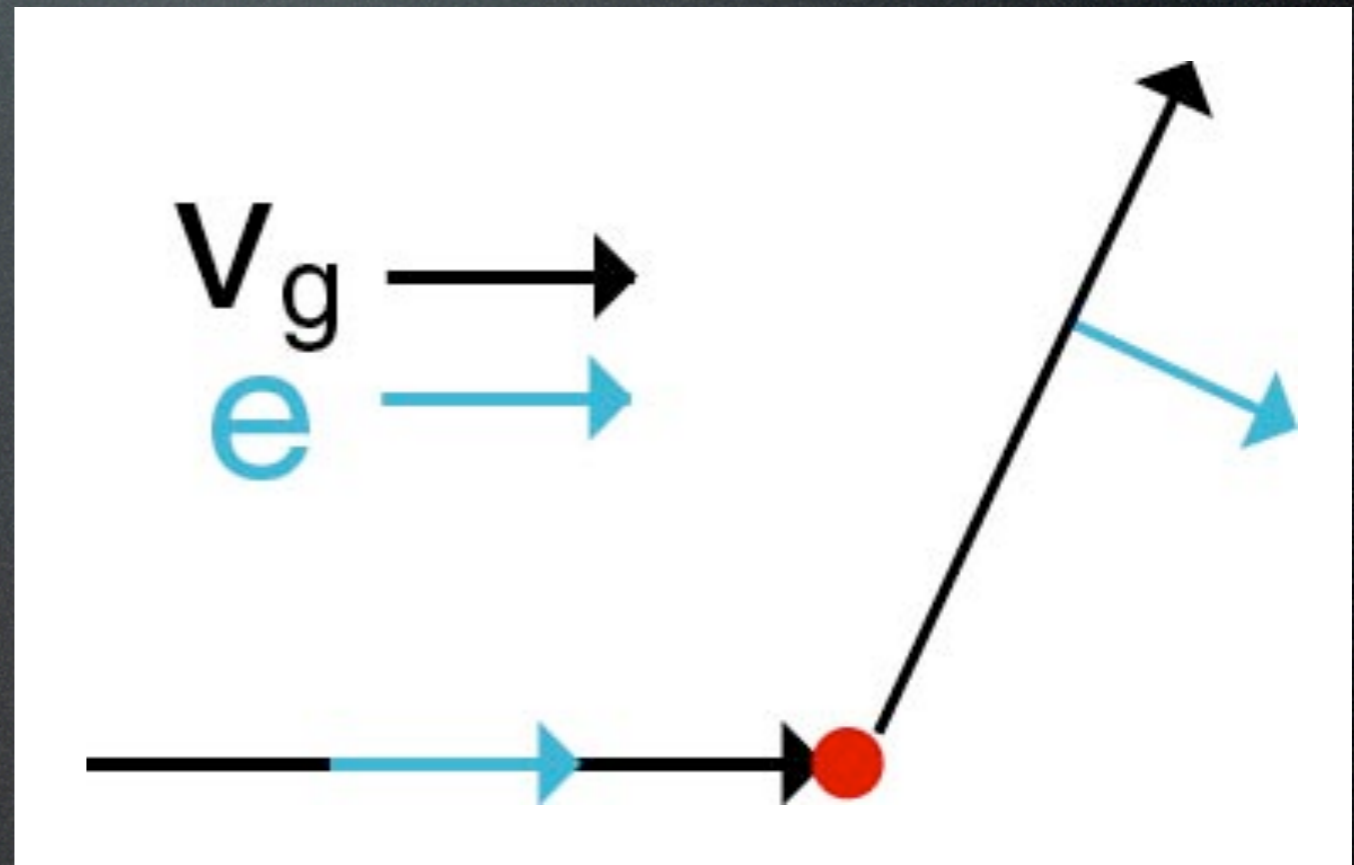
Anisotropic Isotope Scattering

$$\Gamma_{B,Ge} = 3.67 \times 10^{-41} [s^3] \nu^4$$

$$\gamma = \frac{|\vec{e}_\lambda \cdot \vec{e}_{\lambda'}|^2}{v_{\lambda'}^3}$$

Intrinsic
mass defects due
to natural
abundance

Gives rise to
phonon diffusion

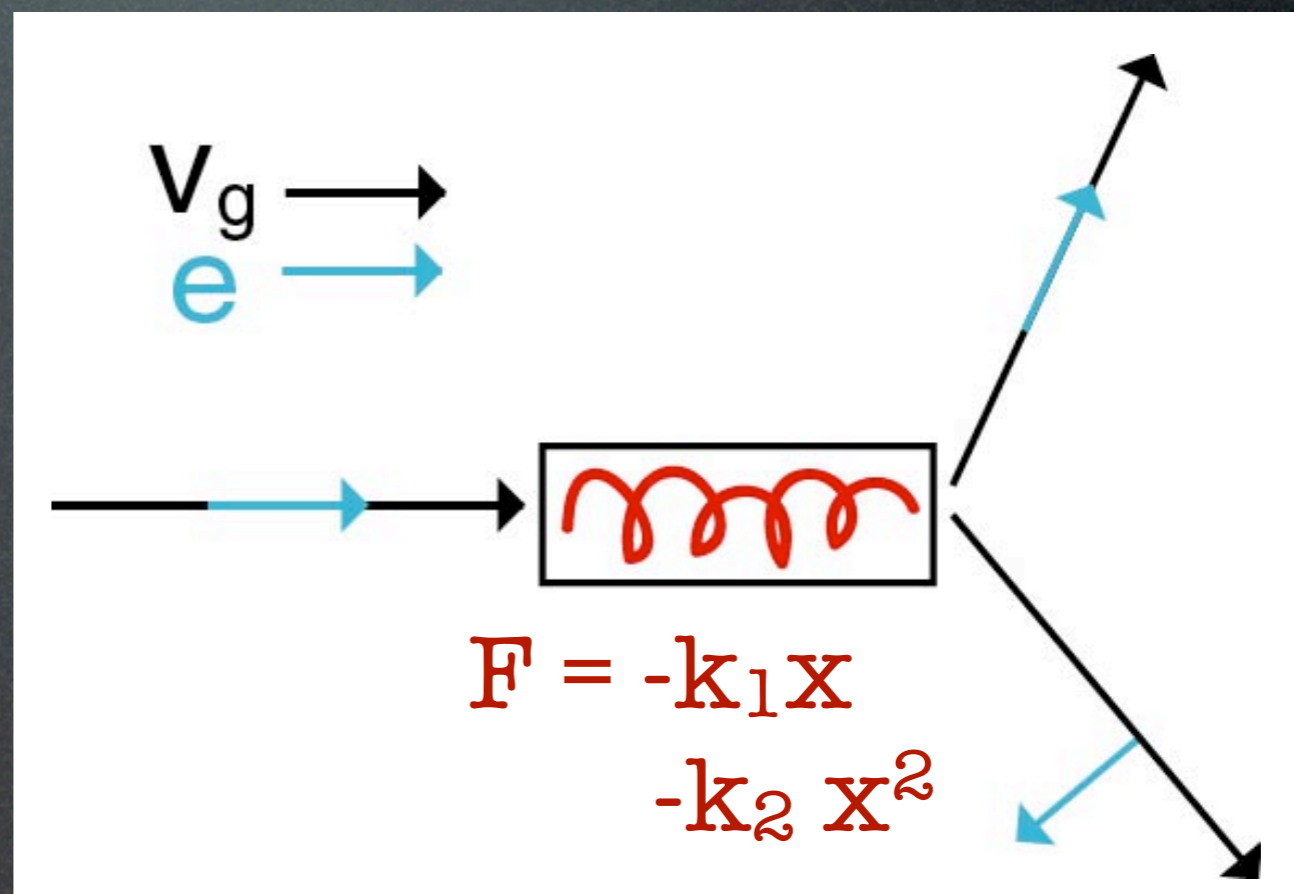


Anharmonic Decay

Diffusion length increases with time.

Three body problem, difficult to solve due to non-isotropic dispersion relation.

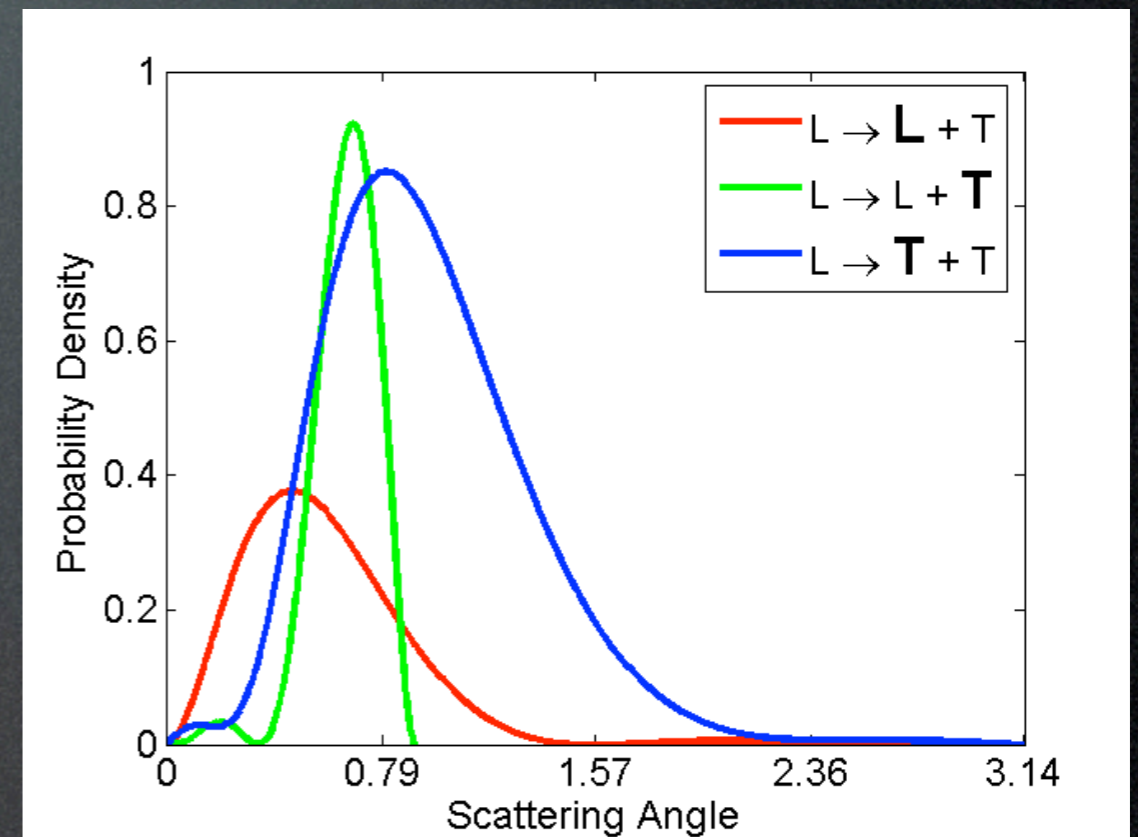
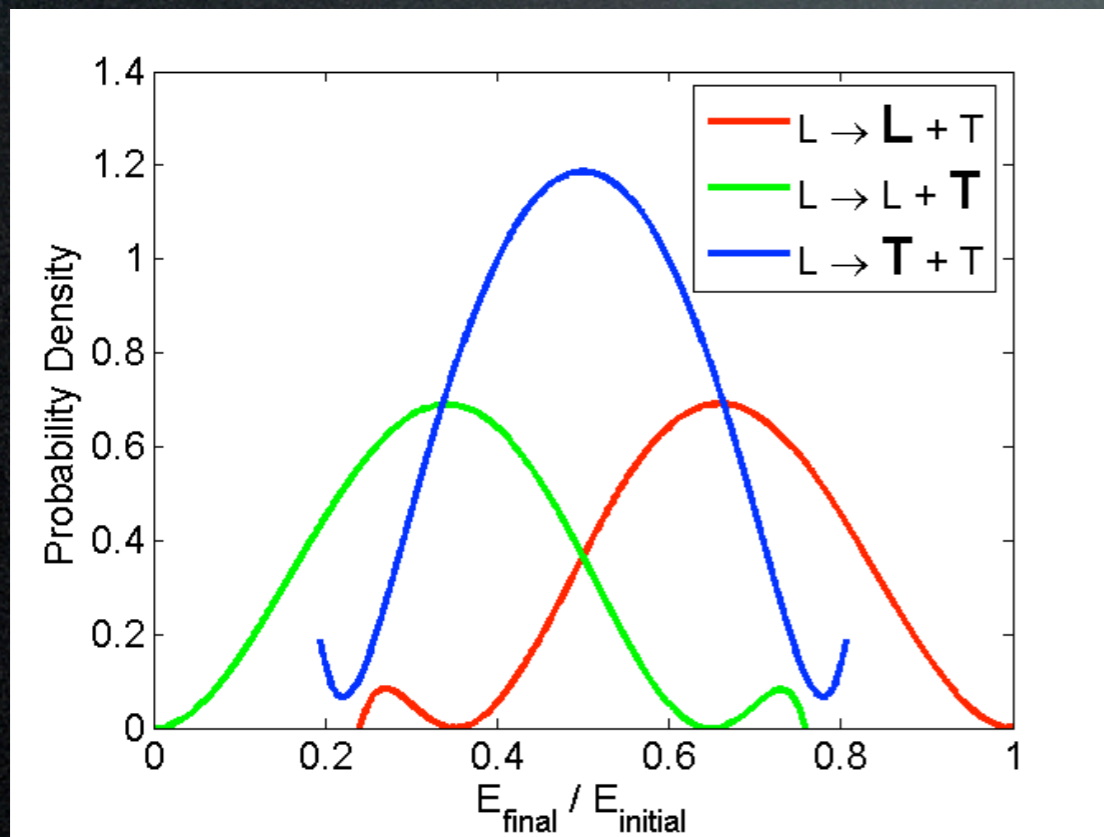
$$\Gamma_{A(LA),Ge} = 1.62 \times 10^{-54} [s^4] \nu^5$$



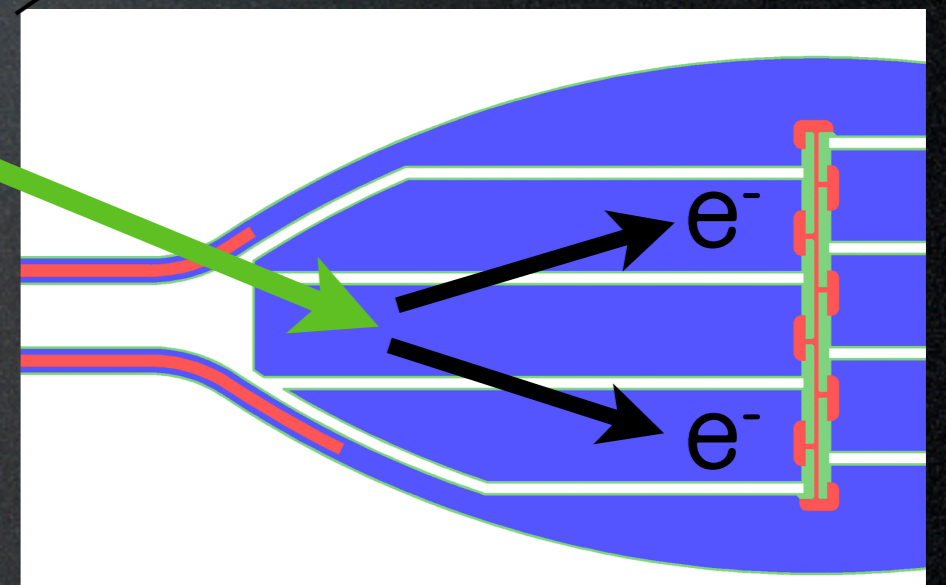
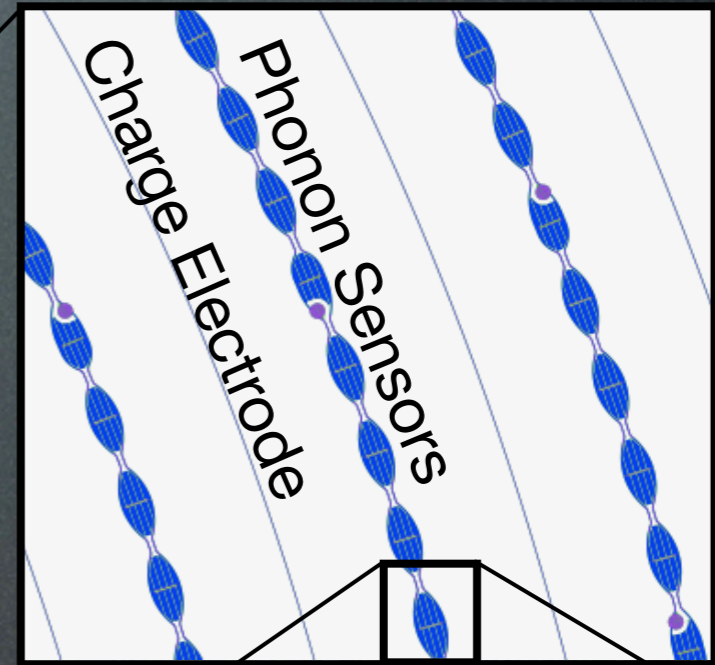
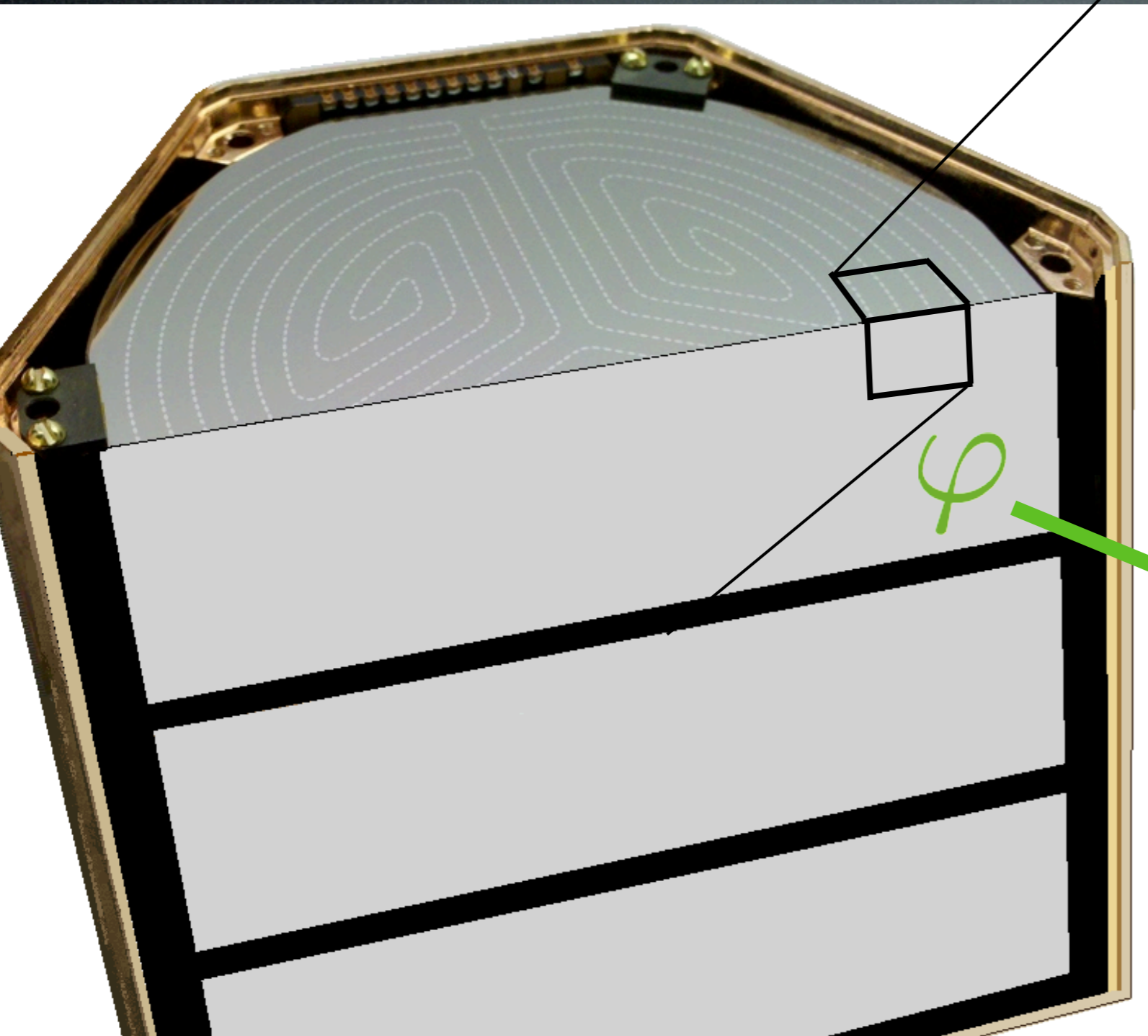
Anharmonic Decay Distributions

$L \rightarrow T+T$ (74%)

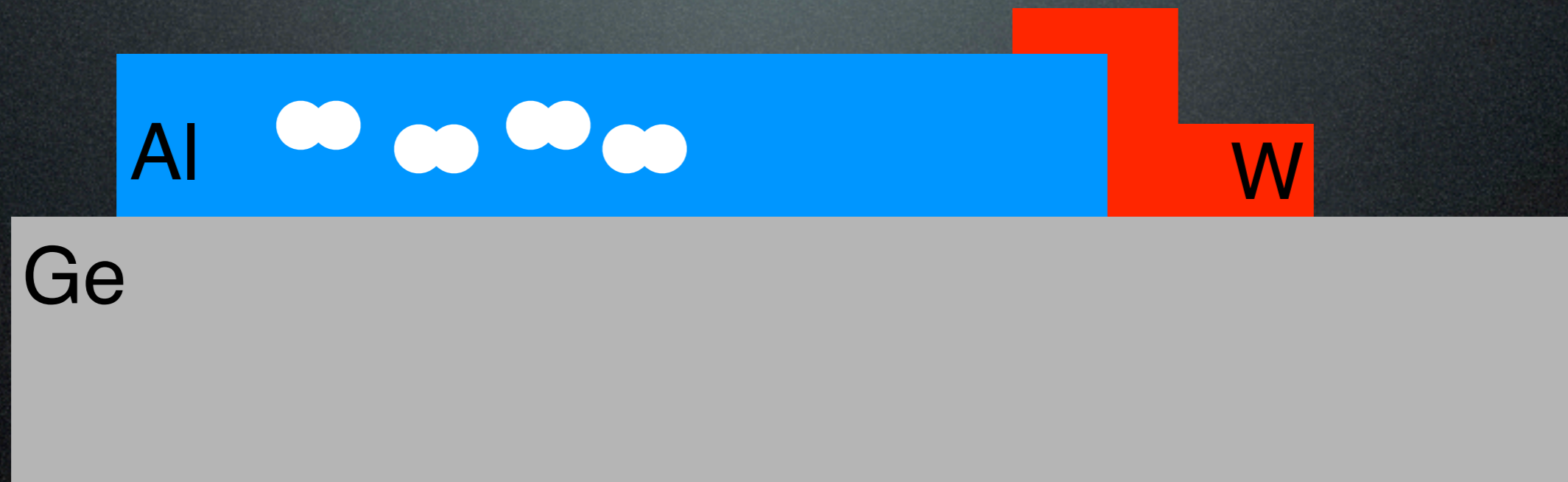
$L \rightarrow L+T$ (26%)



SCDMS iZIP Detector

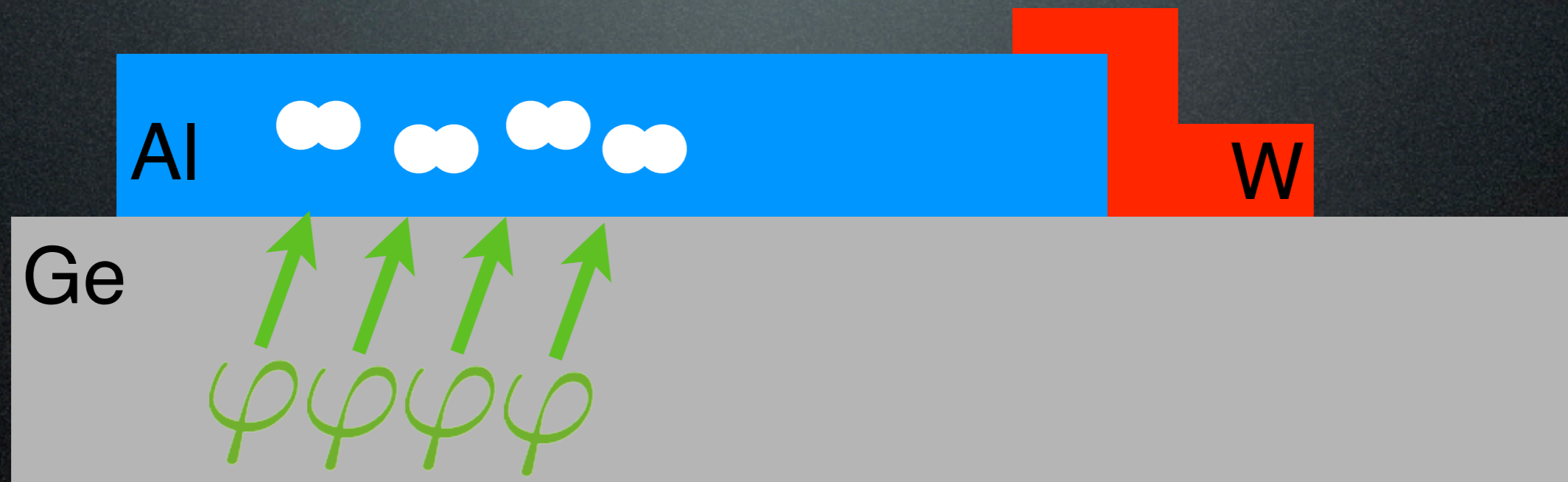


Quasiparticle / Phonon Downconversion



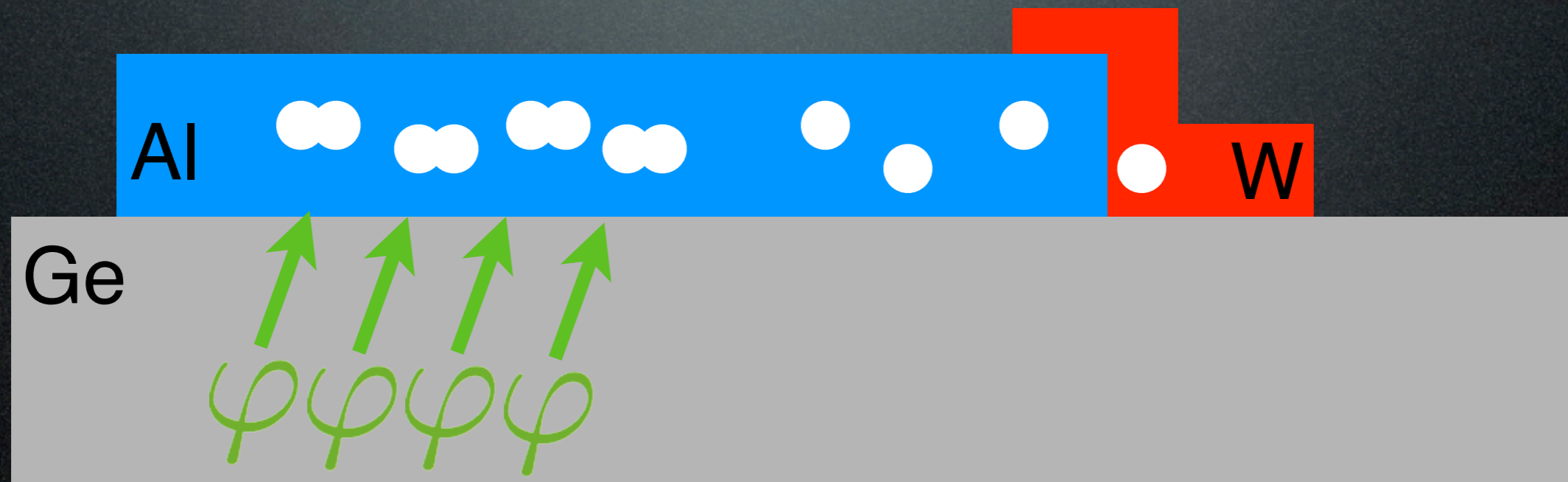
- Downconversion process
 - Production of quasiparticles
 - Phonon energy escapes back to crystal

Quasiparticle / Phonon Downconversion



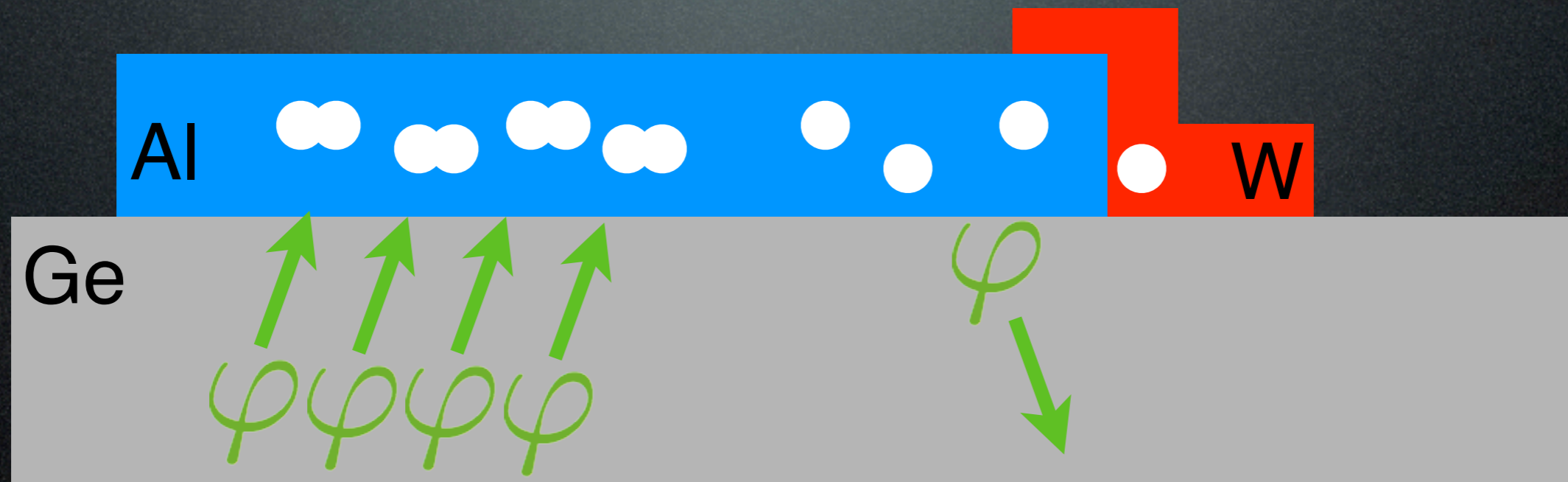
- Downconversion process
 - Production of quasiparticles
 - Phonon energy escapes back to crystal

Quasiparticle / Phonon Downconversion



- Downconversion process
 - Production of quasiparticles
 - Phonon energy escapes back to crystal

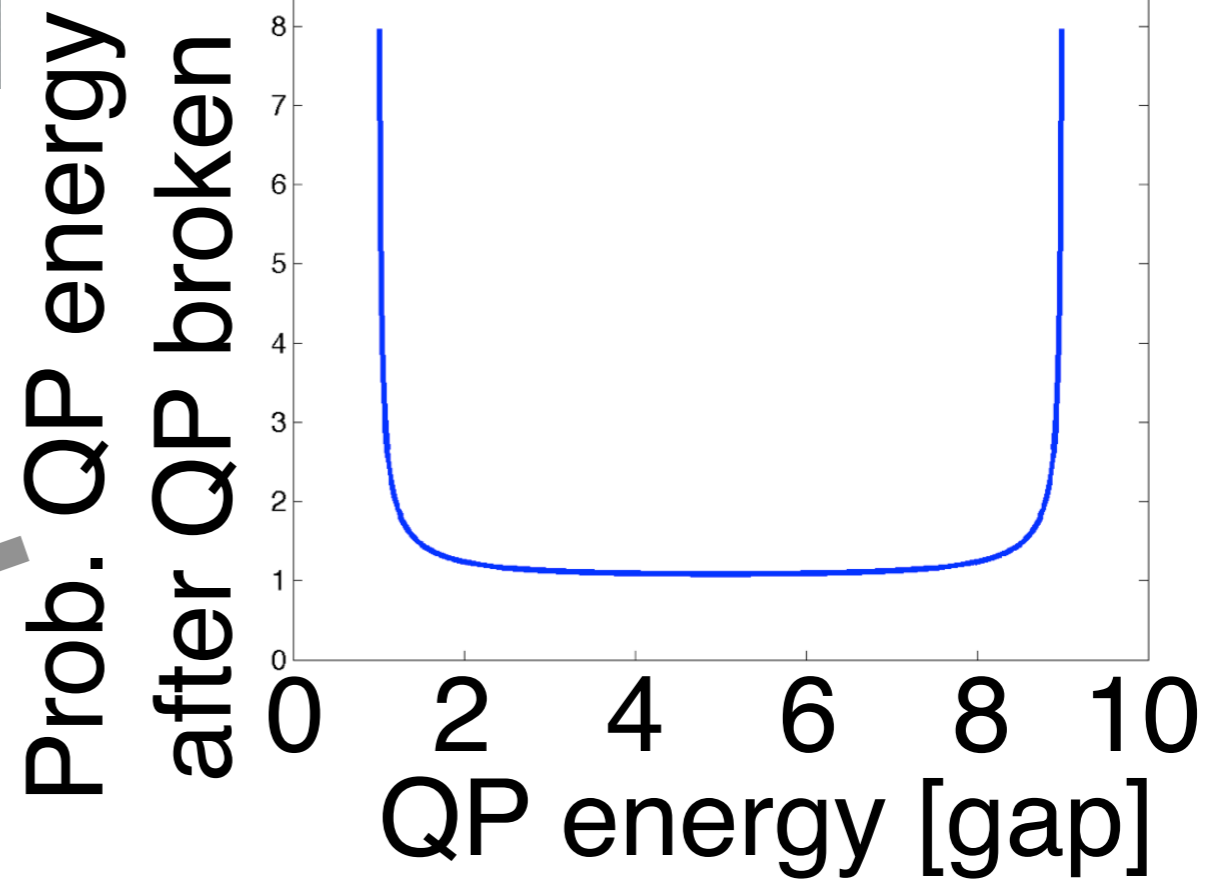
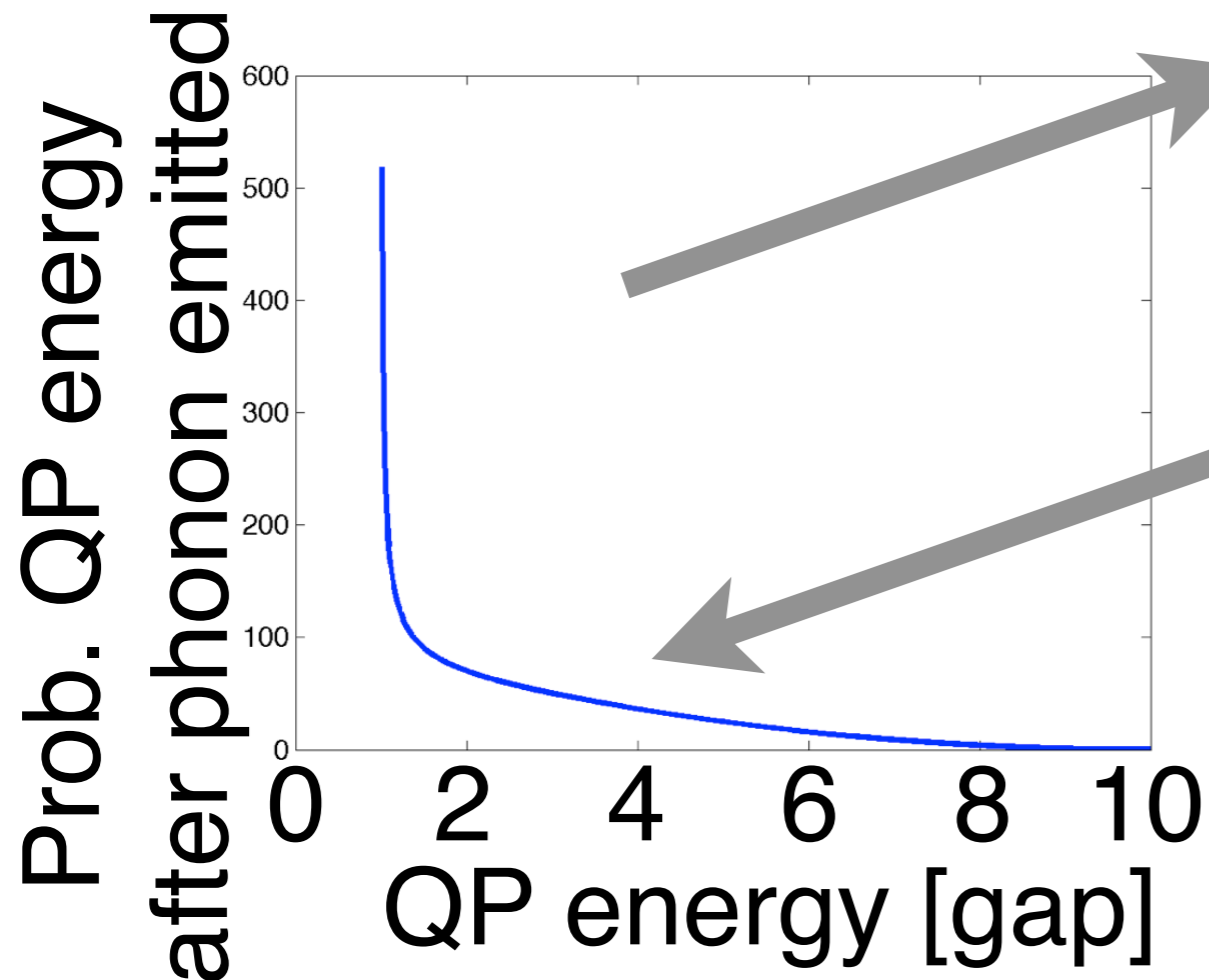
Quasiparticle / Phonon Downconversion



- Downconversion process
 - Production of quasiparticles
 - Phonon energy escapes back to crystal

Quasiparticle Cascade

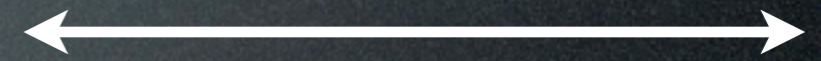
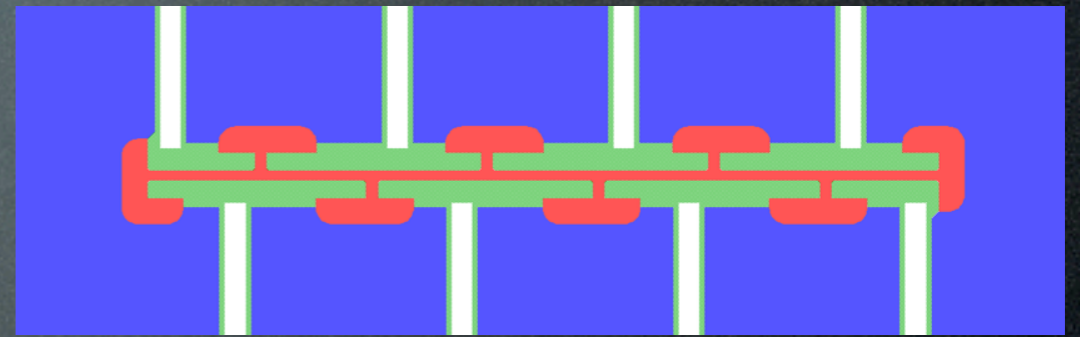
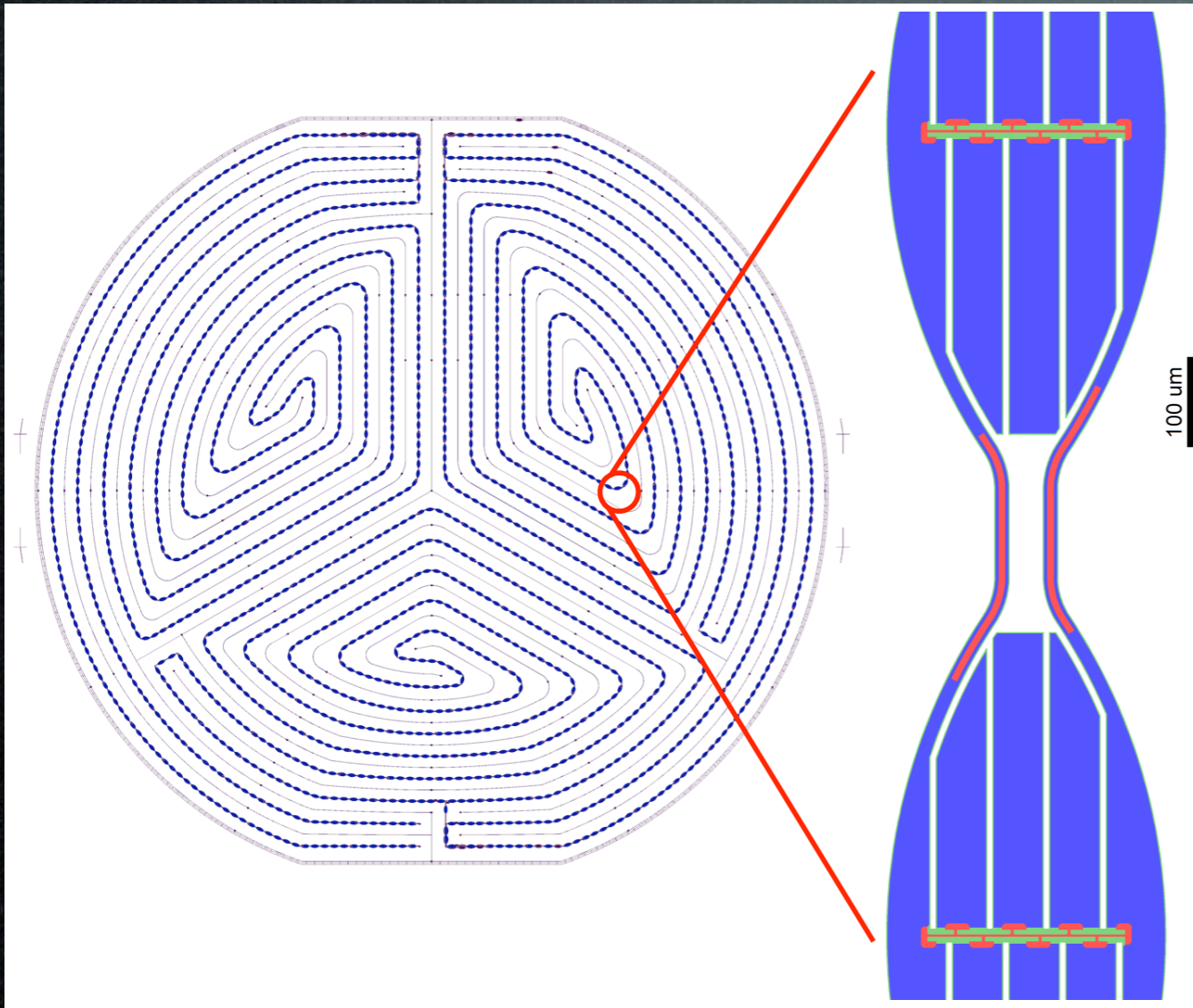
- Cascade until phonon energy < 2 gap or phonon escapes Al



Phonon Readout

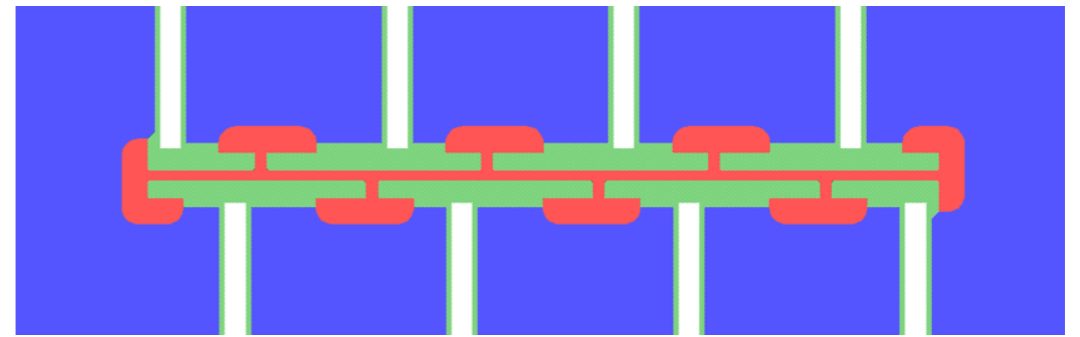
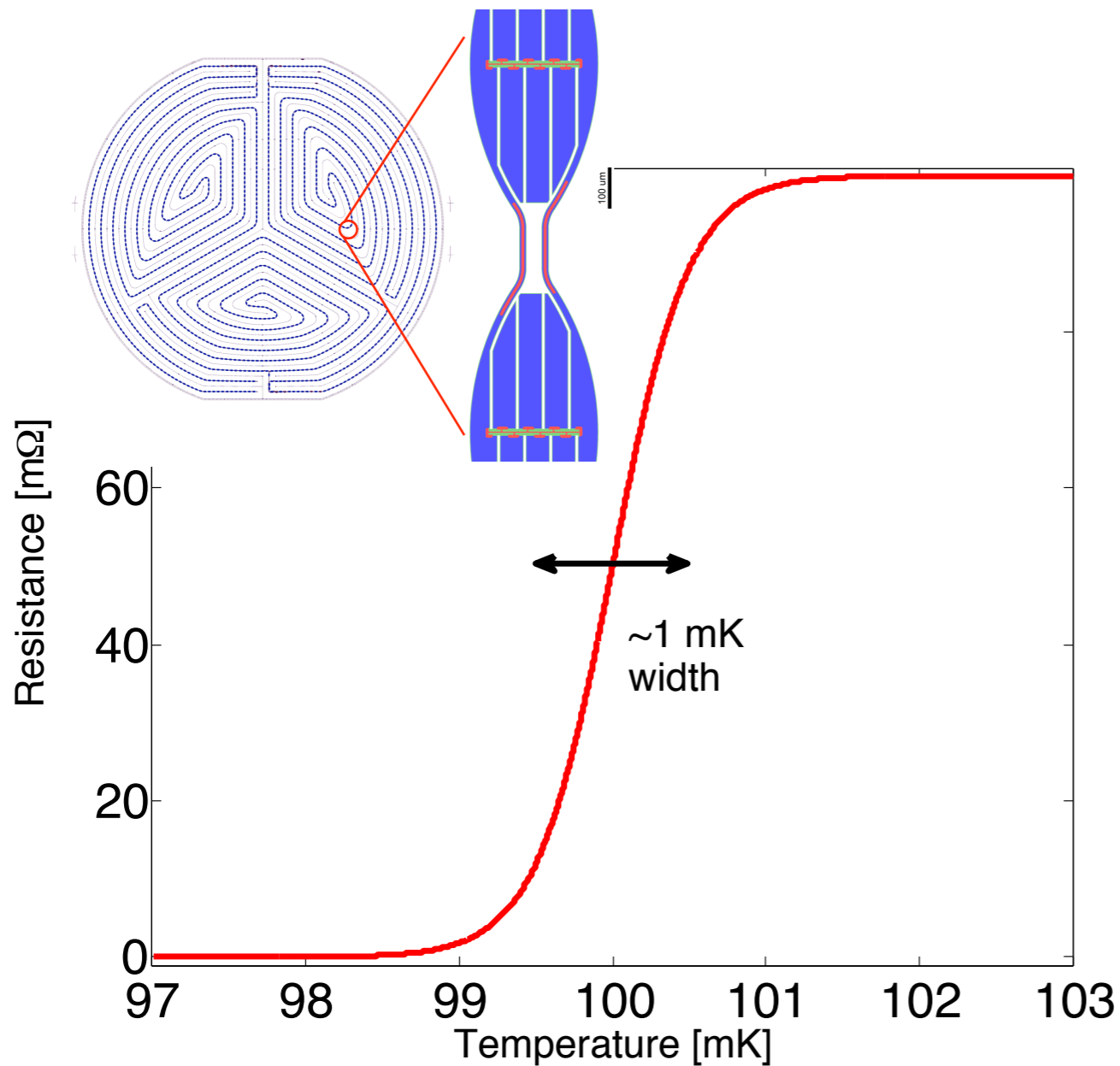
Transition Edge Sensors

TES Layout



220 μm

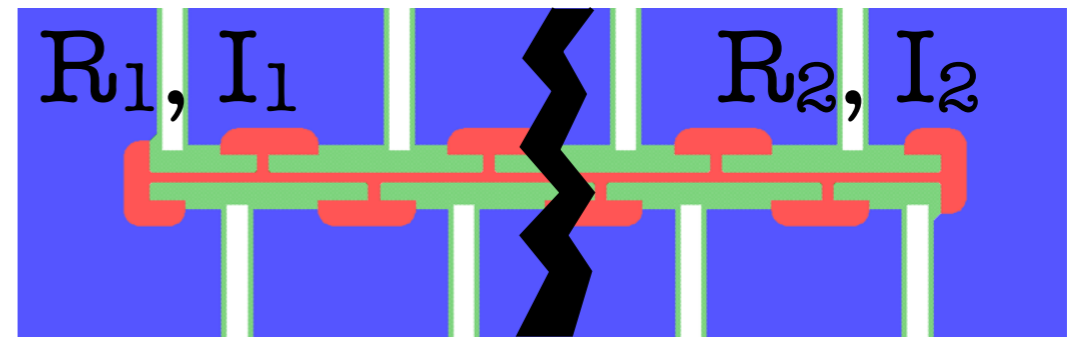
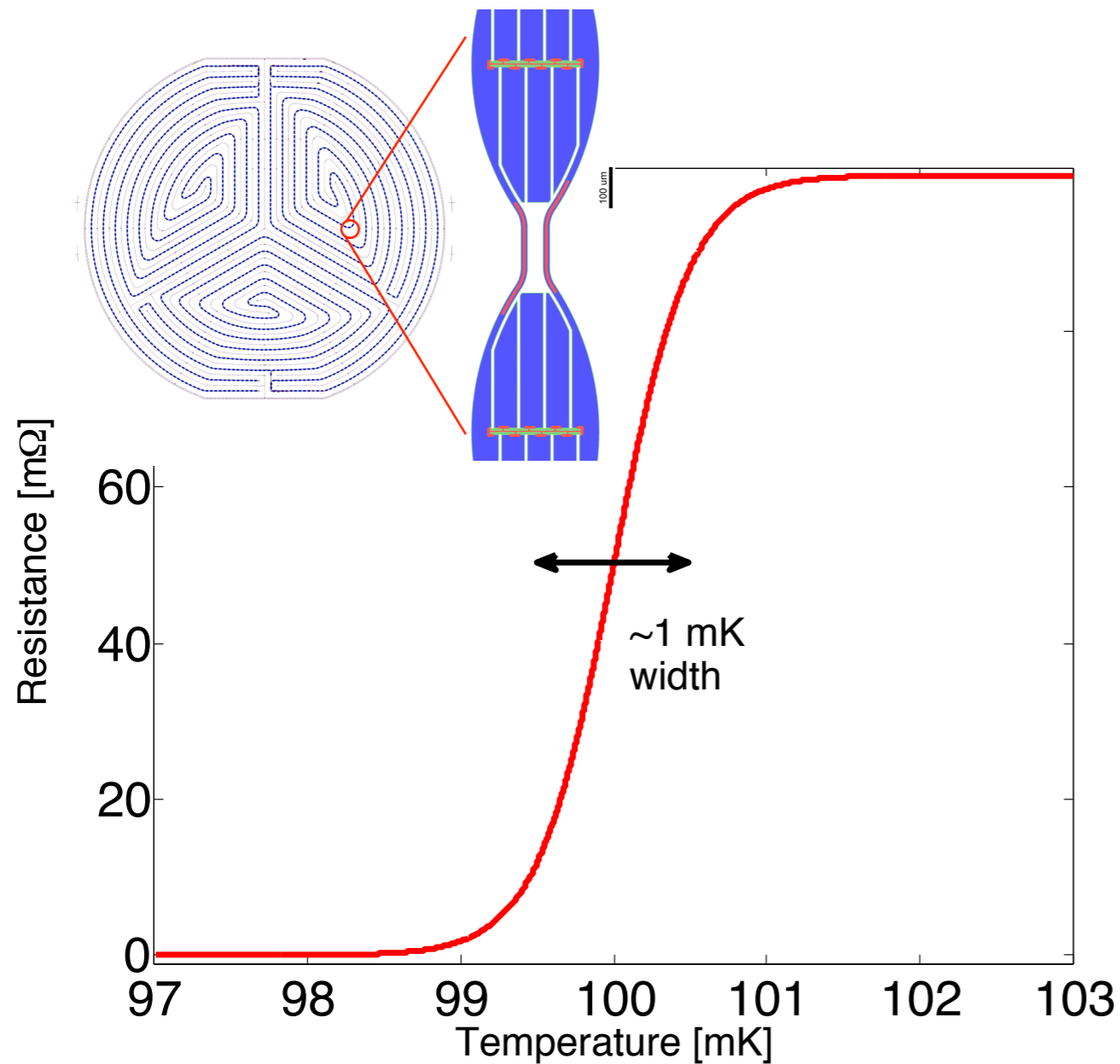
TES Joule Power



$$P_{\text{Joule}} = \frac{V^2}{R}$$

Negative
electro-thermal
feedback (stable)

TES Phase Separation

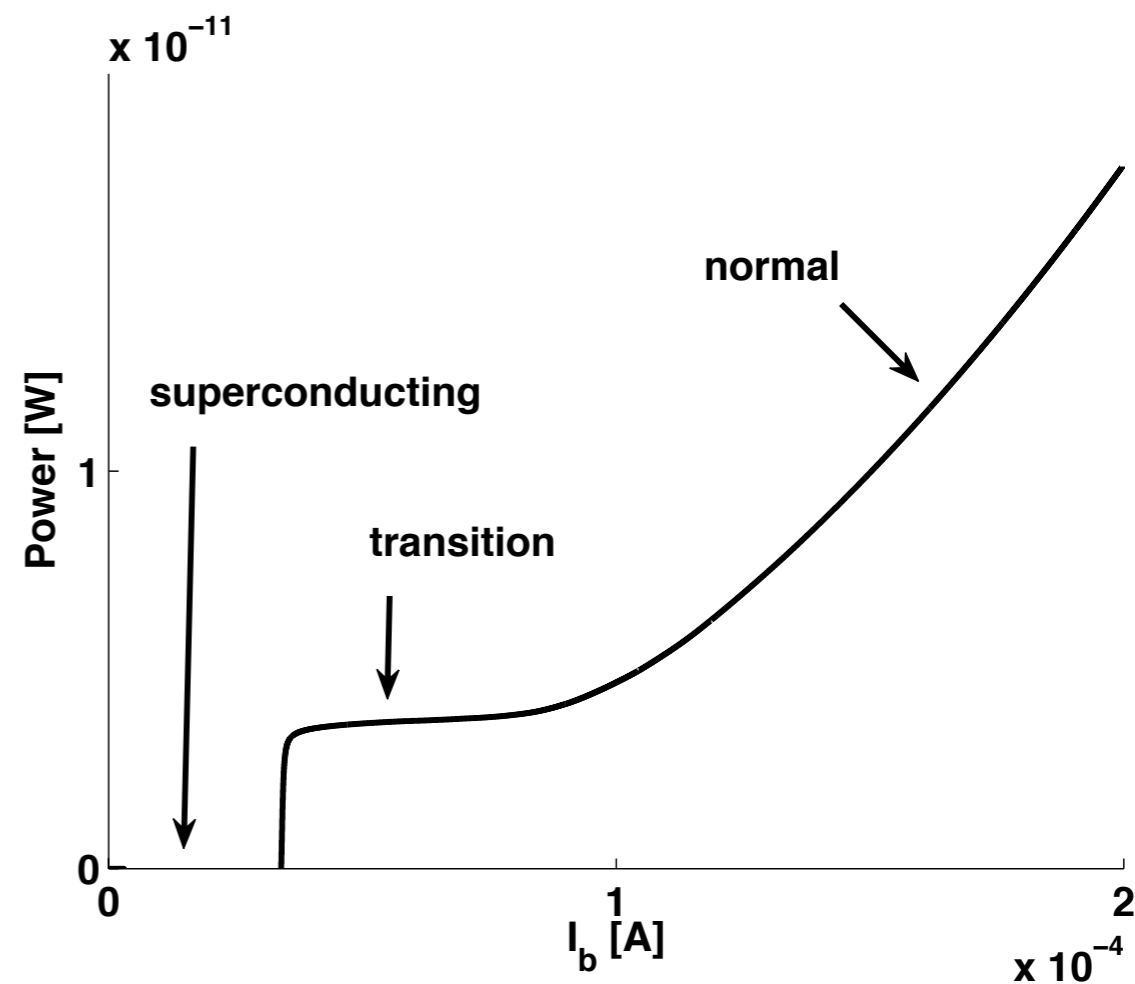
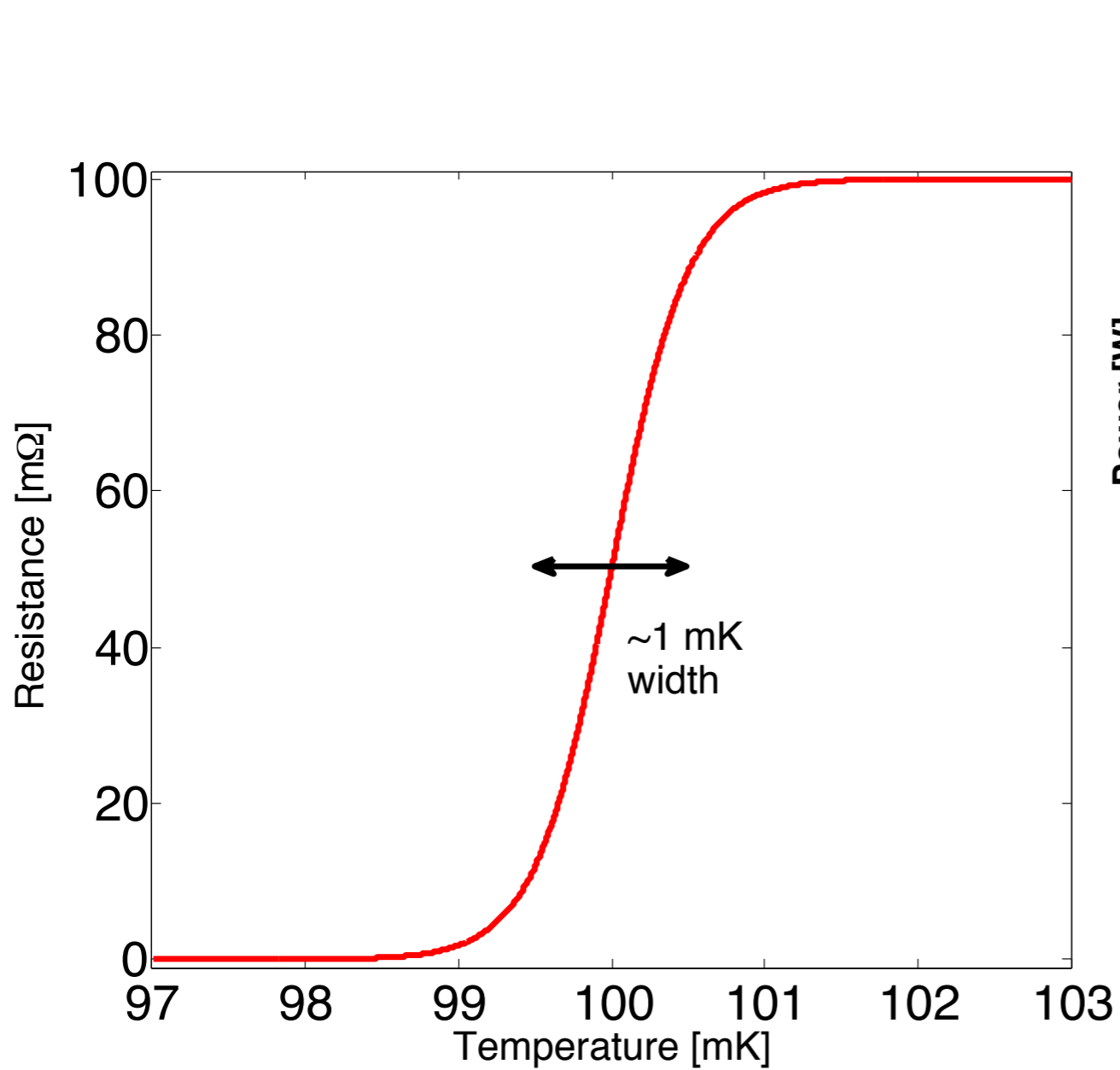


$$P_{\text{Joule},1} = I^2 R_1$$

$$P_{\text{Joule},2} = I^2 R_2$$

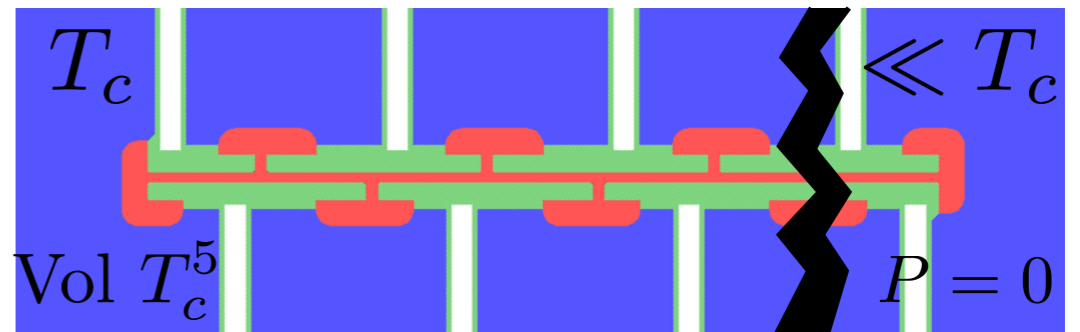
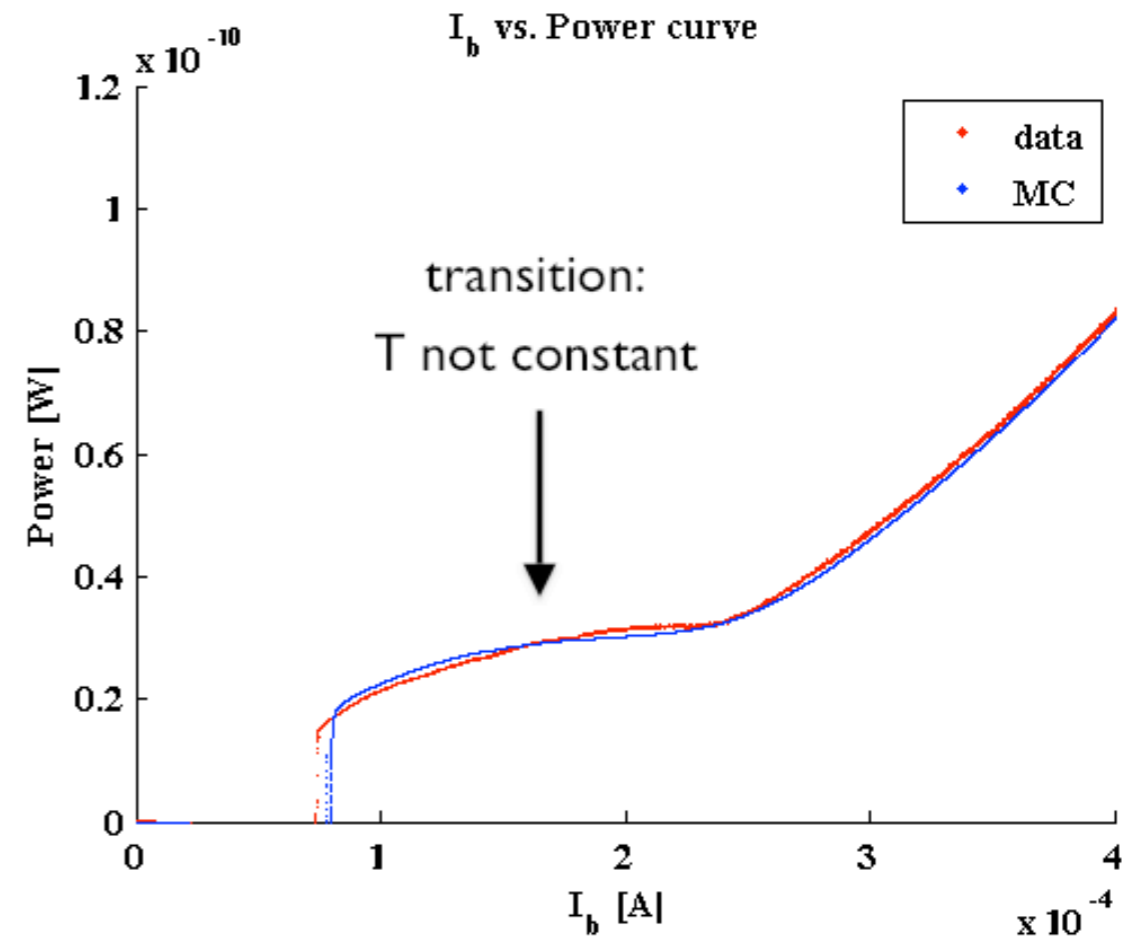
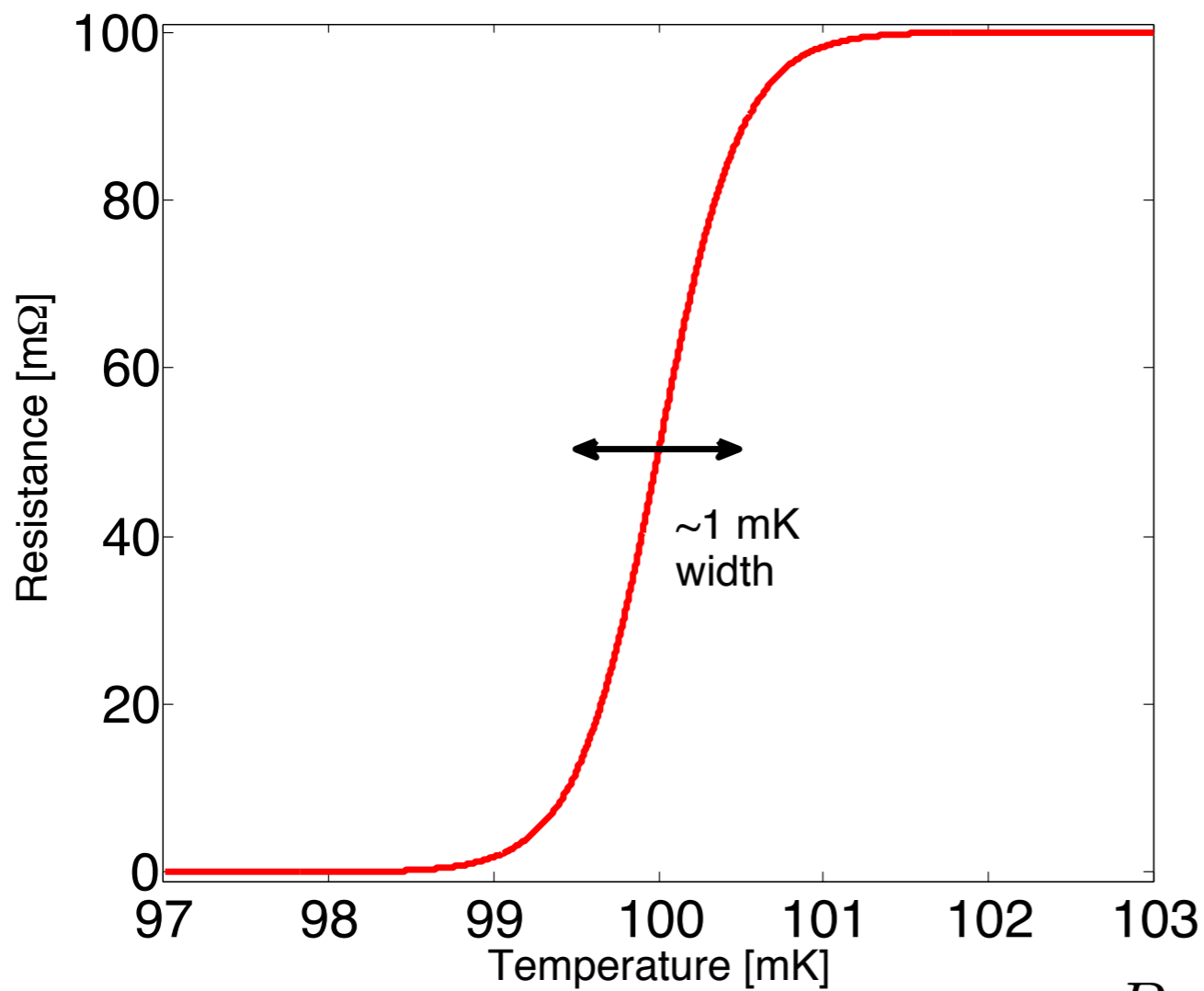
Positive
electro-thermal
feedback between
 R_1 & R_2 (unstable)

TES I-P Curve

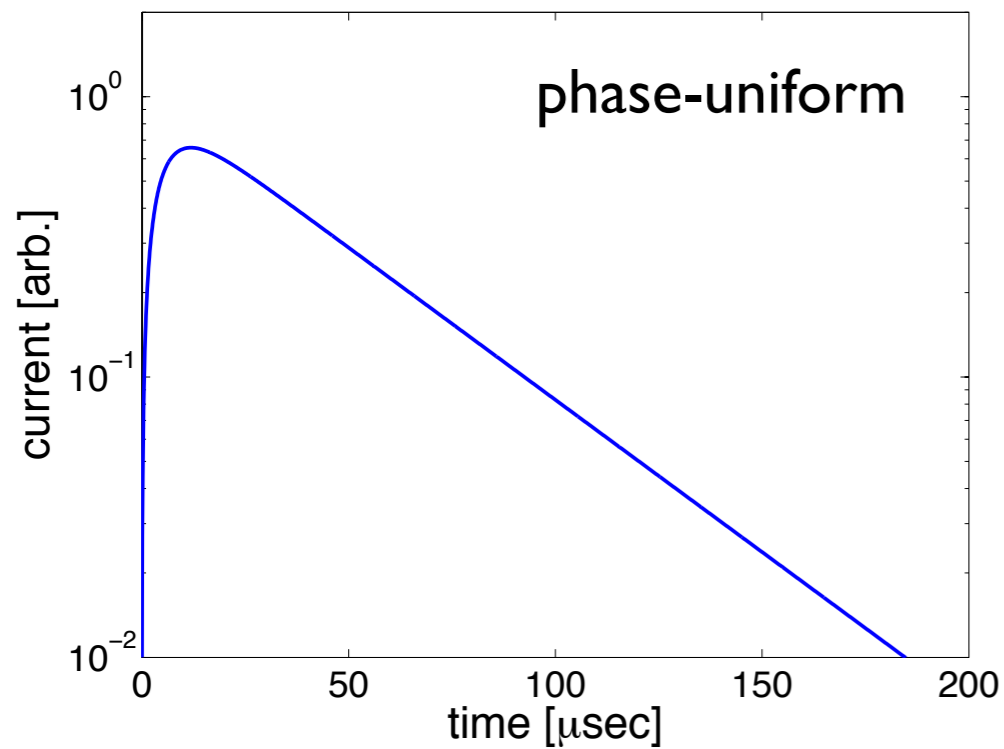


$$P_{\text{Joule}} = P_{\text{TES} \rightarrow \text{substrate}} \\ \sim \text{Vol} (T_{\text{TES}}^5 - T_{\text{substate}}^5)$$

Transition Edge Sensor I-P Curves

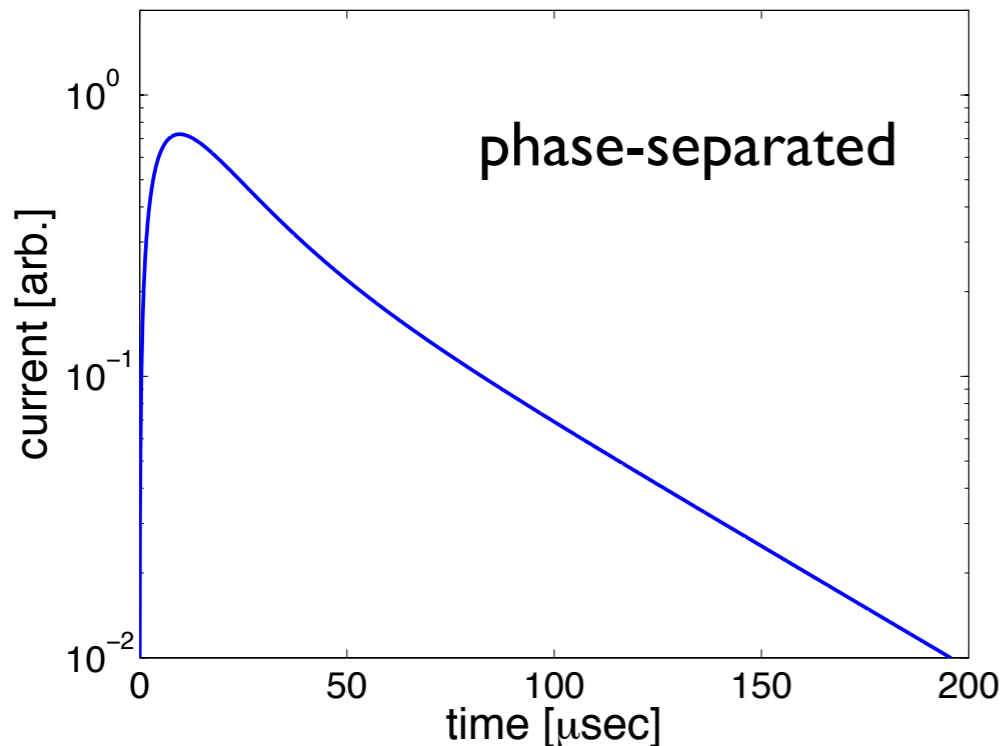


Heat Pulse Transient



Phase-uniform case
time constants

$$L/R$$
$$C/G$$



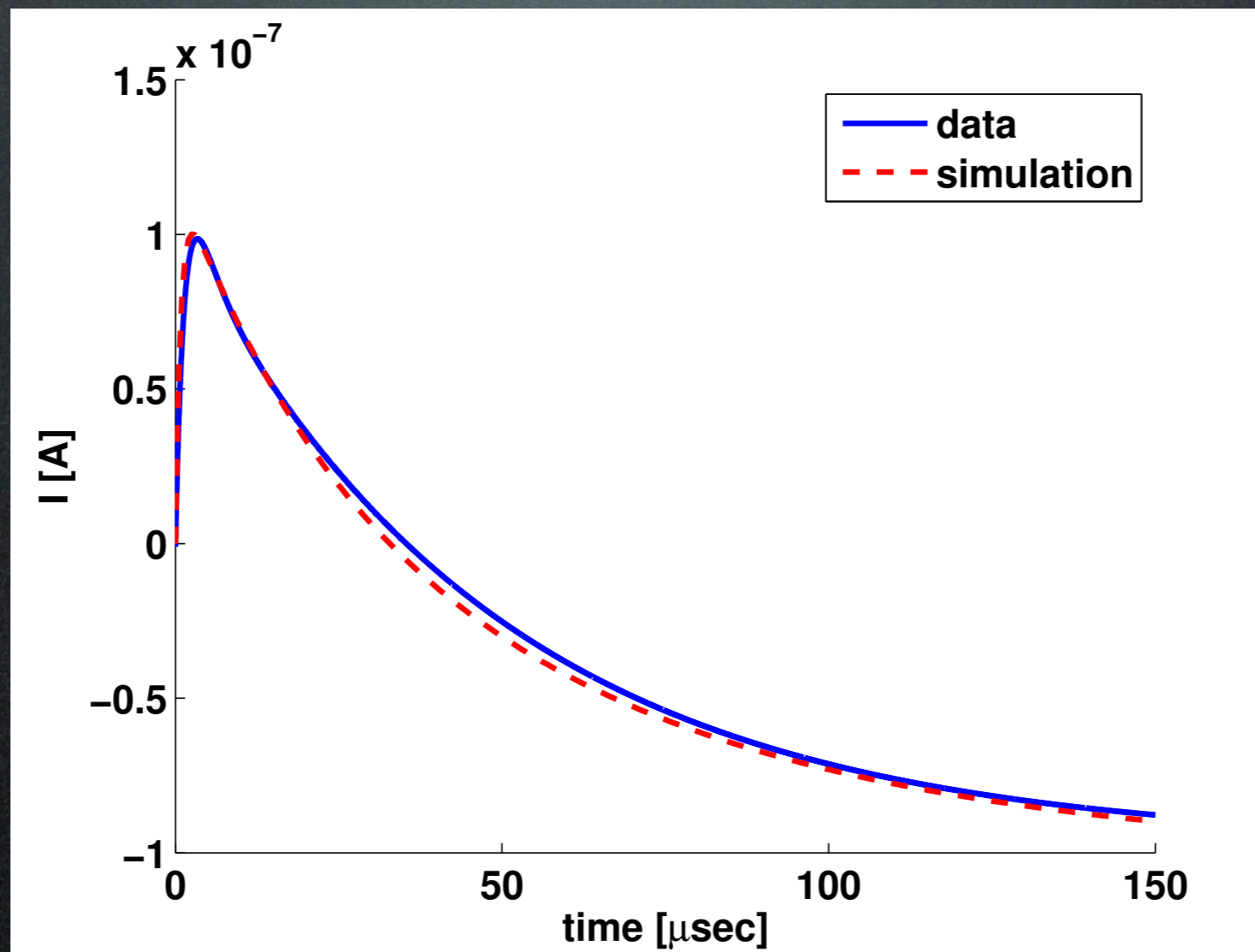
Phase separated case
time constants

$$L/R$$

thermal diffusion in TES

$$C/G$$

Heat Pulse Transient Model Tuning



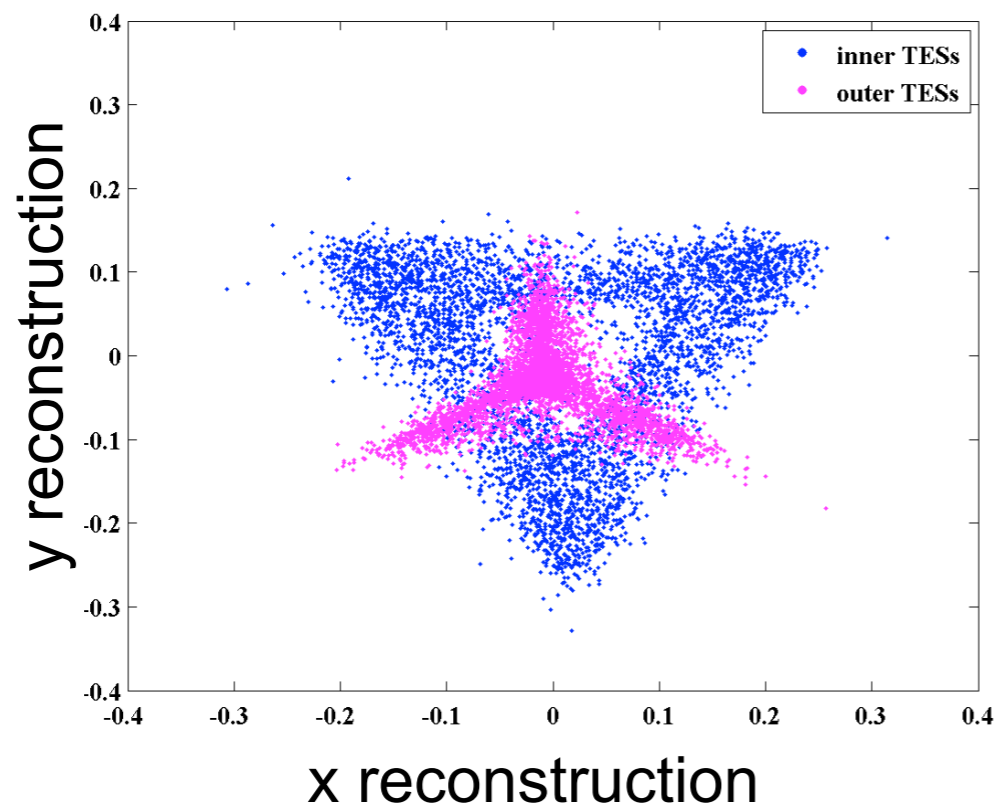
Model Validation :

Charge, Phonon, TES

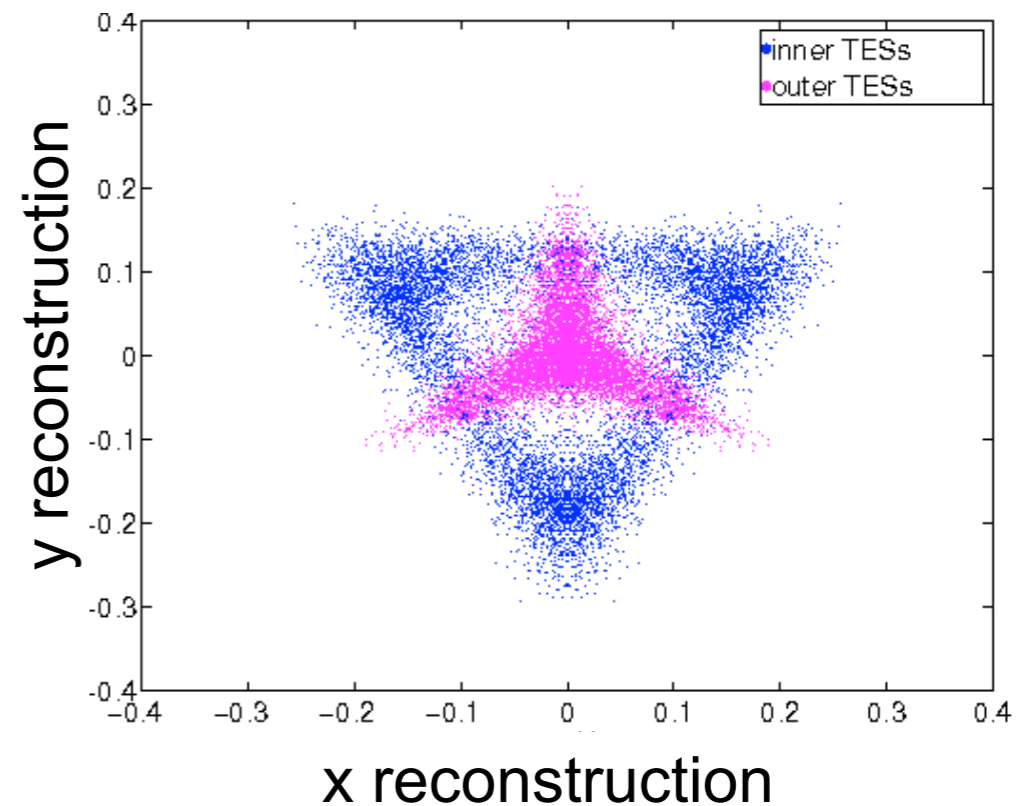
Position Reconstruction

- Phonon-aluminum interaction probability
 - No QP-phonon downconversion
 - No TES physics

Calibration

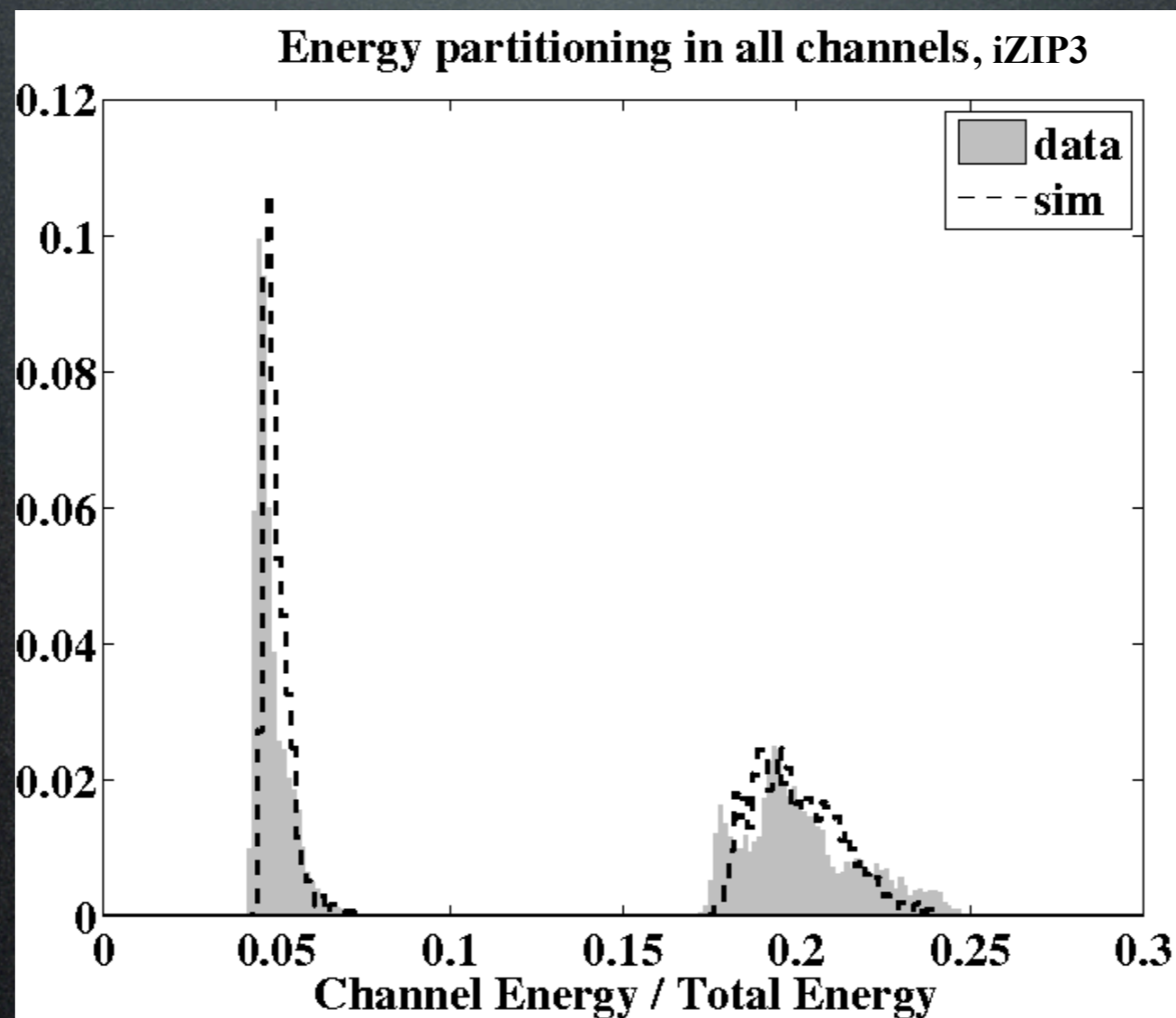


Monte Carlo



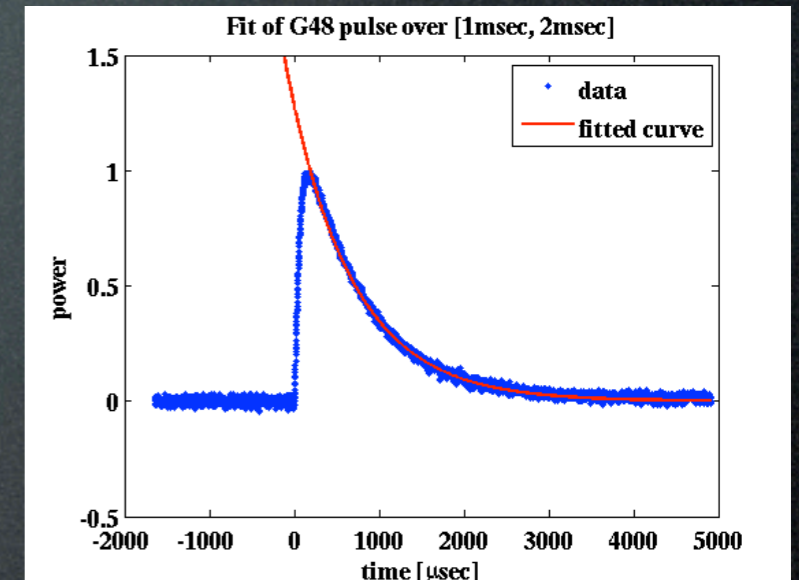
Energy Partitioning

- Phonon-aluminum interaction probability, QP-phonon downconversion

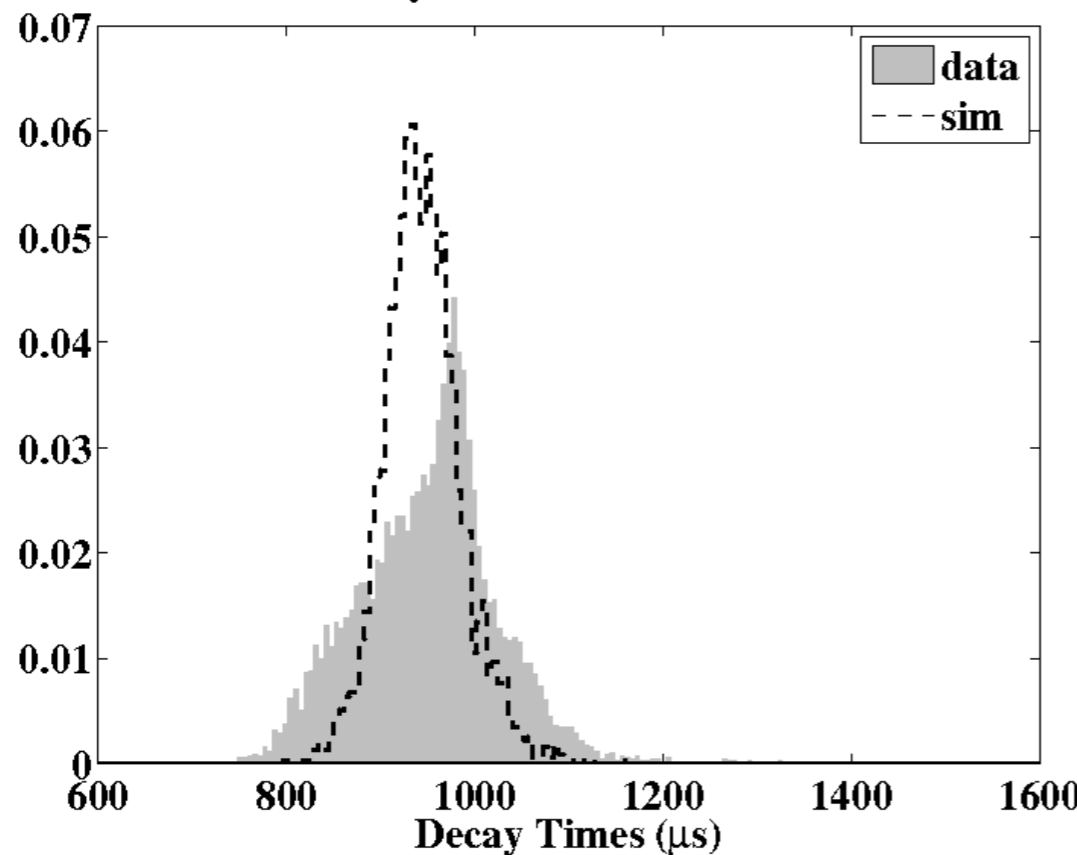


Decay Times

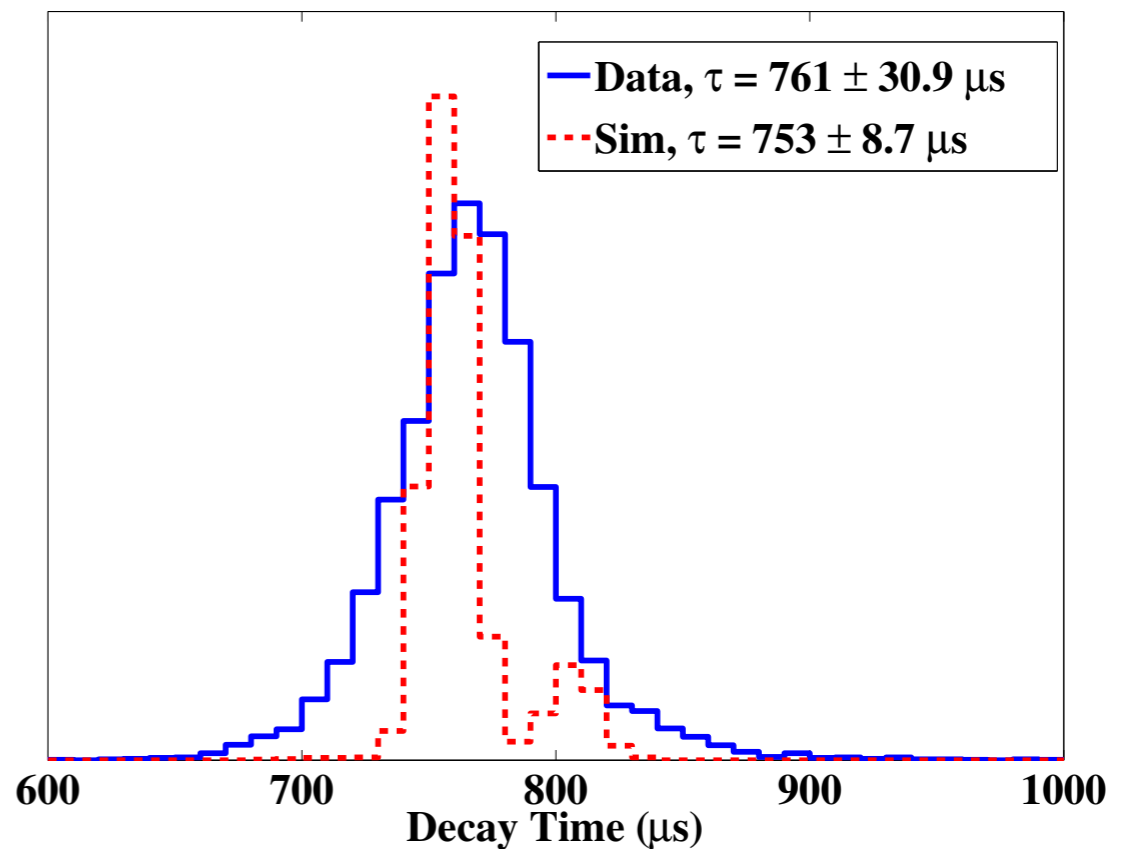
Phonon-aluminum
interaction probability,
QP-phonon
downconversion



Decay Times of all channels, iZIP3



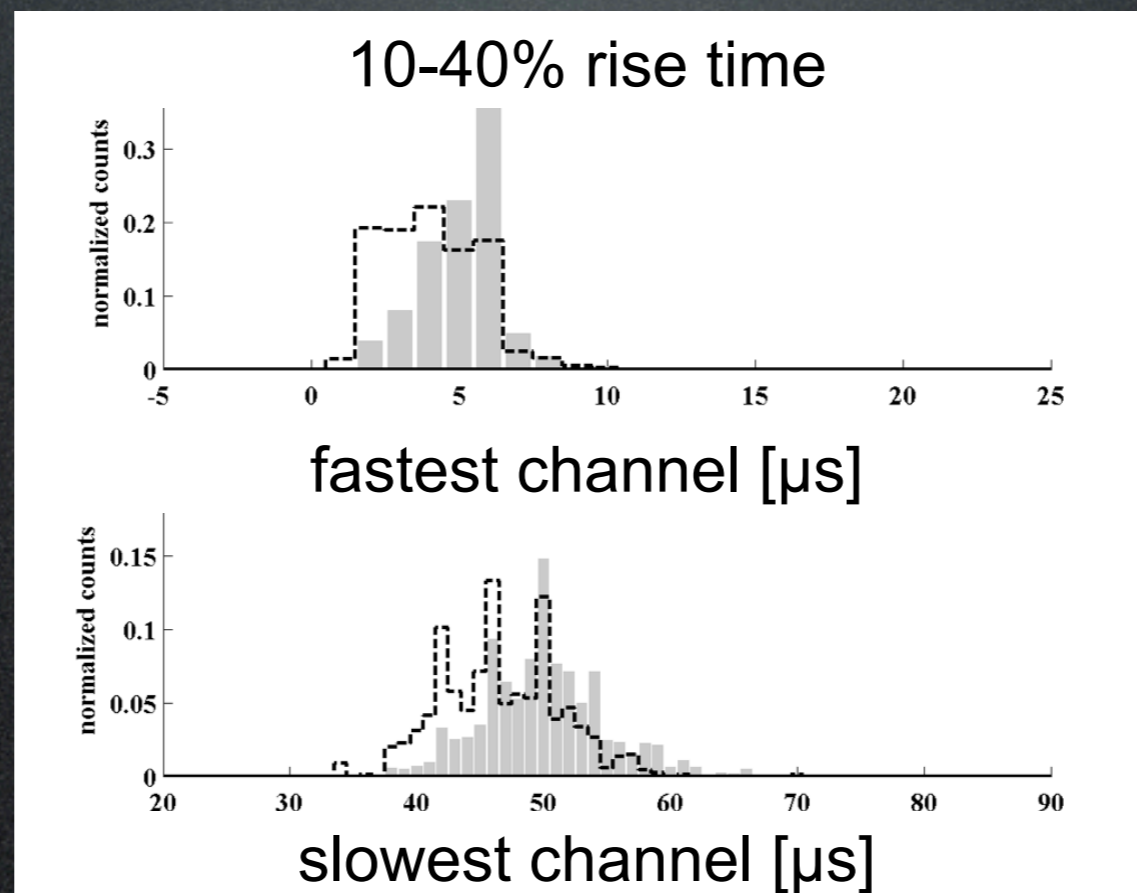
Decay Times of TES Pulses, iZIP4



iZIP3 Rise Times - G3D

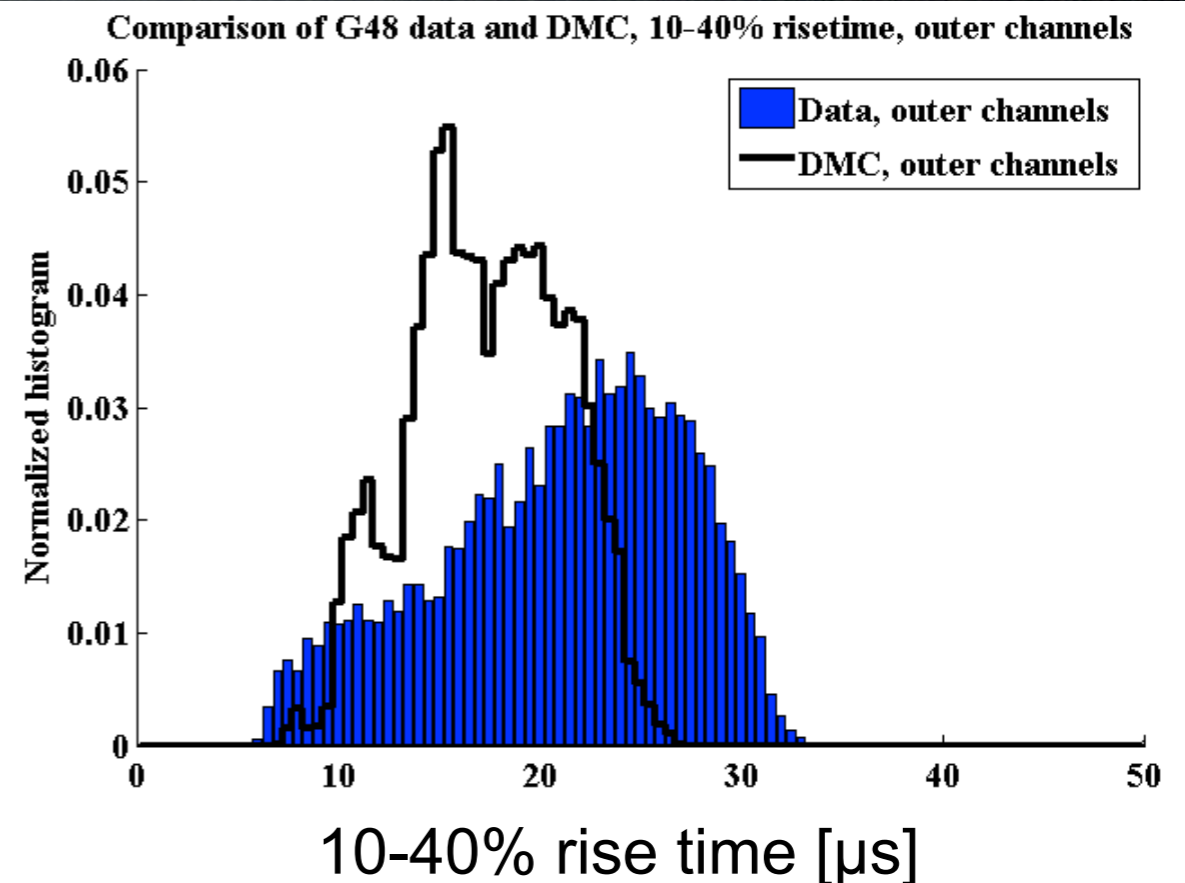
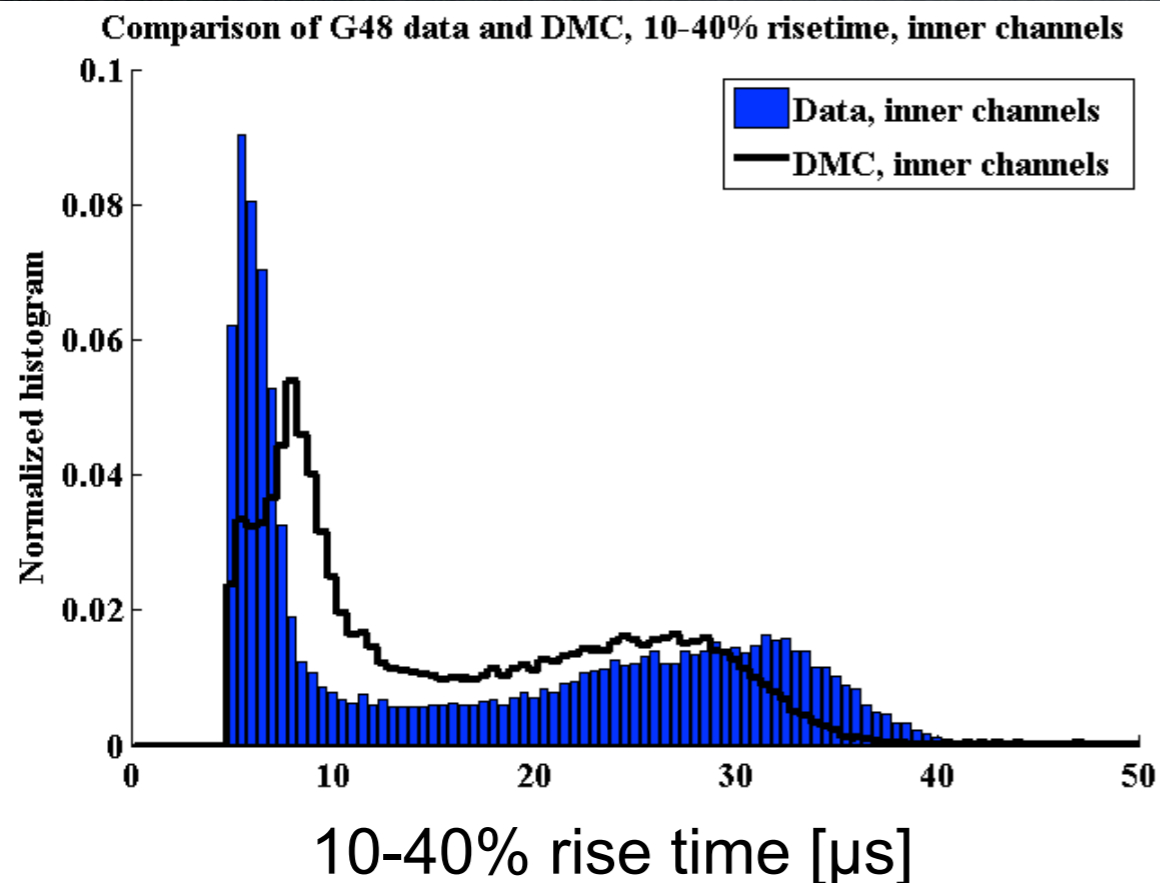
- Luke phonons, Phonon-aluminum interaction probability, QP-phonon downconversion and TES dynamics

Low T_c Side = 55 mK



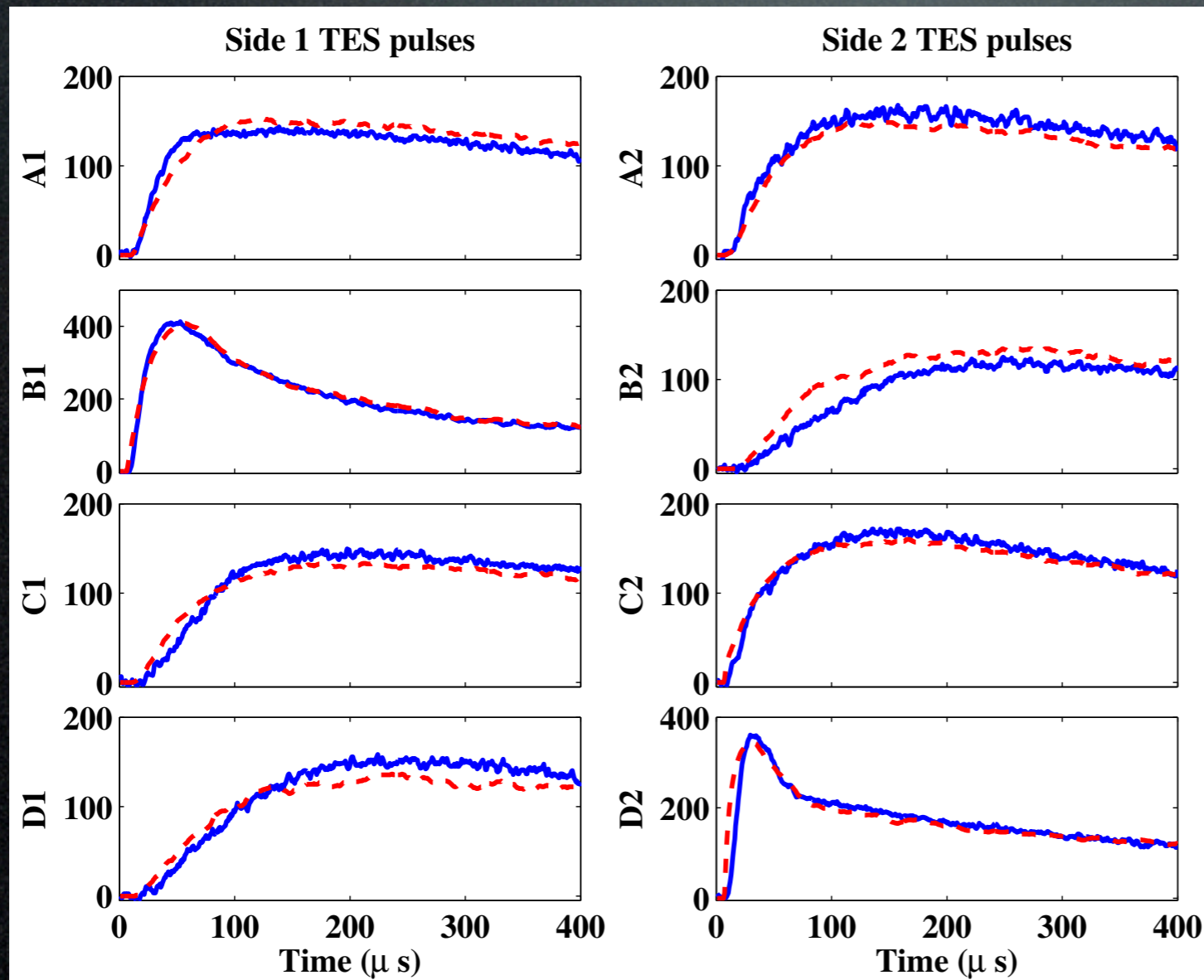
iZIP4 Rise Times - G48

- Luke phonons, Phonon-aluminum interaction probability, QP-phonon downconversion and TES dynamics
 - Need to improve detector physics or GEANT4 input?



TES Pulse Matching

- Direct comparison of TES pulses from data and MC (2 mm raster scan).

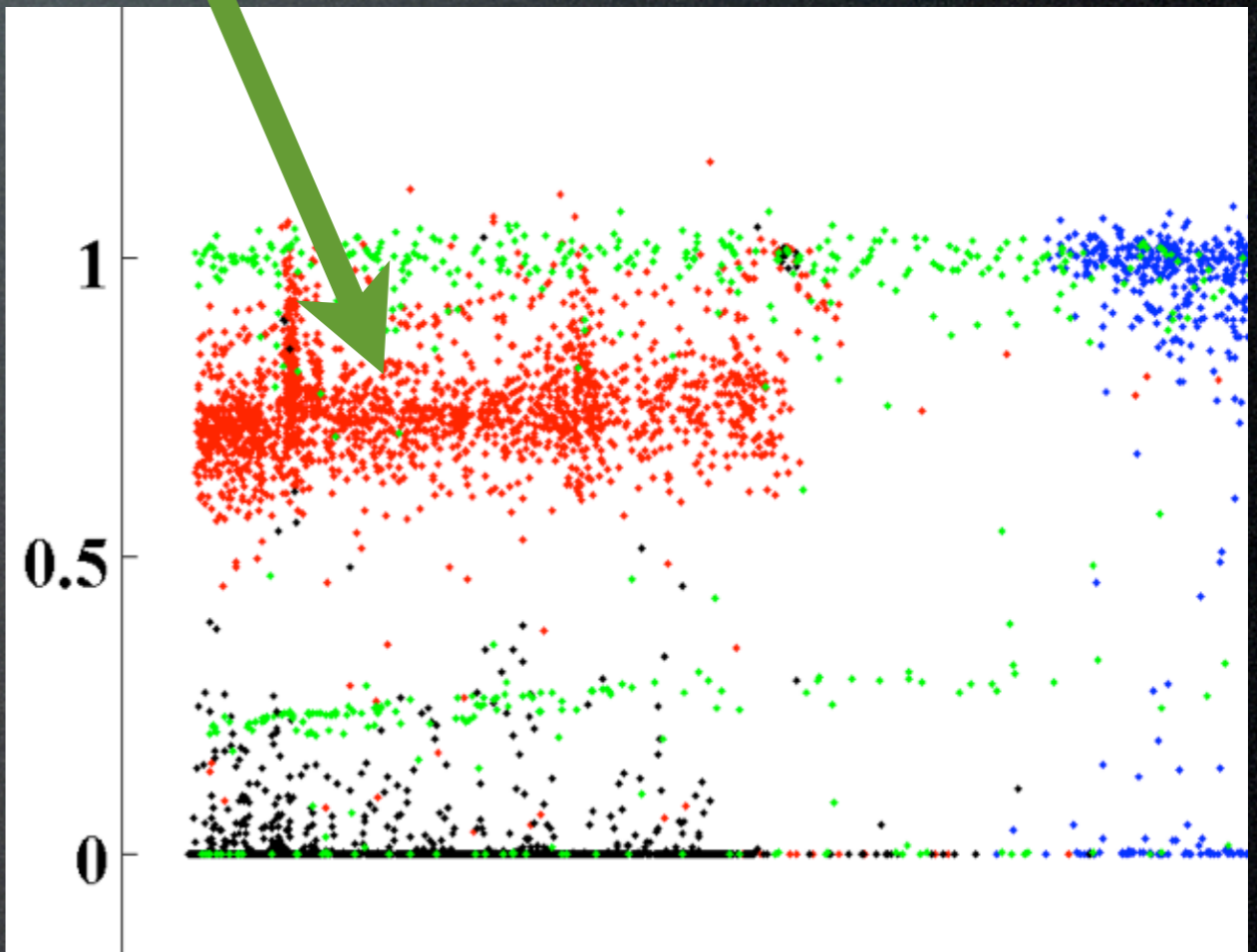
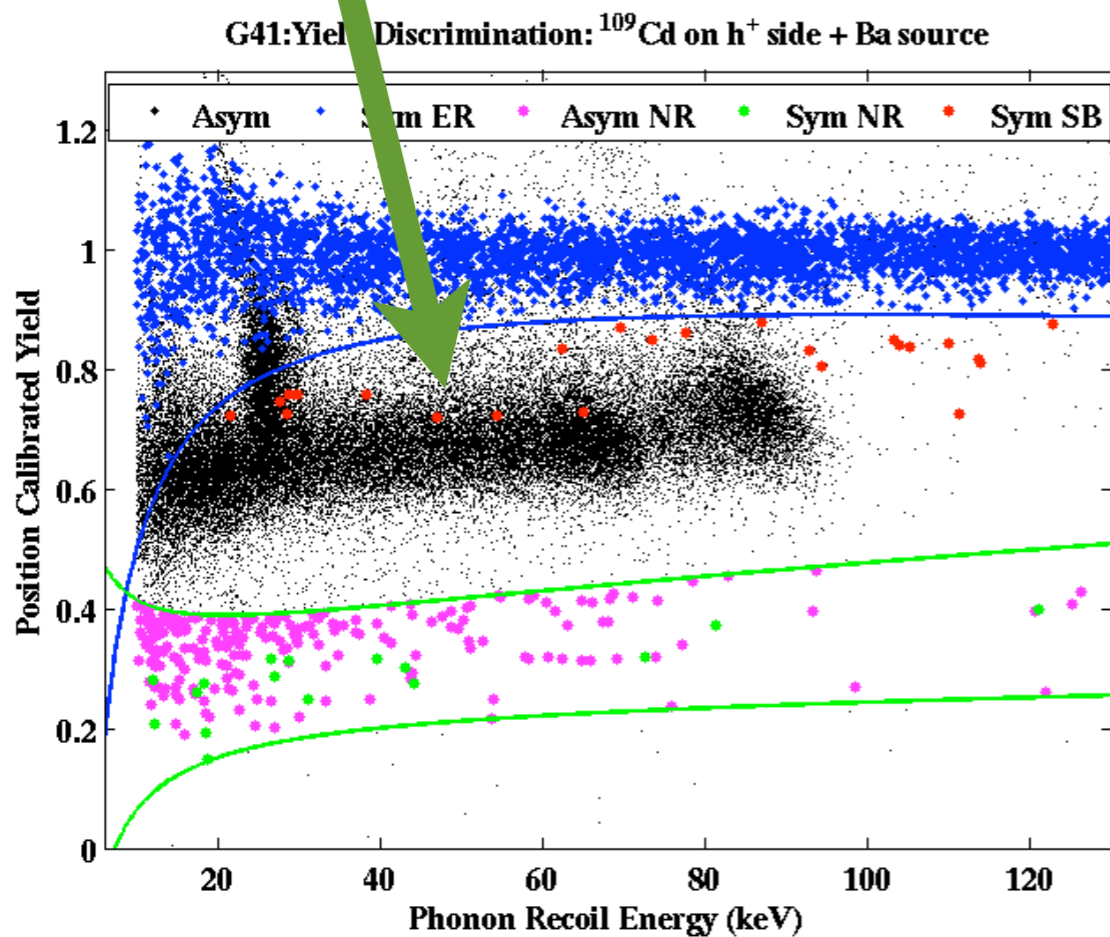


calibration data
MC

Surface Events

Reduced
ionization

MC tuning with charge carrier
momentum and surface
interaction dynamics



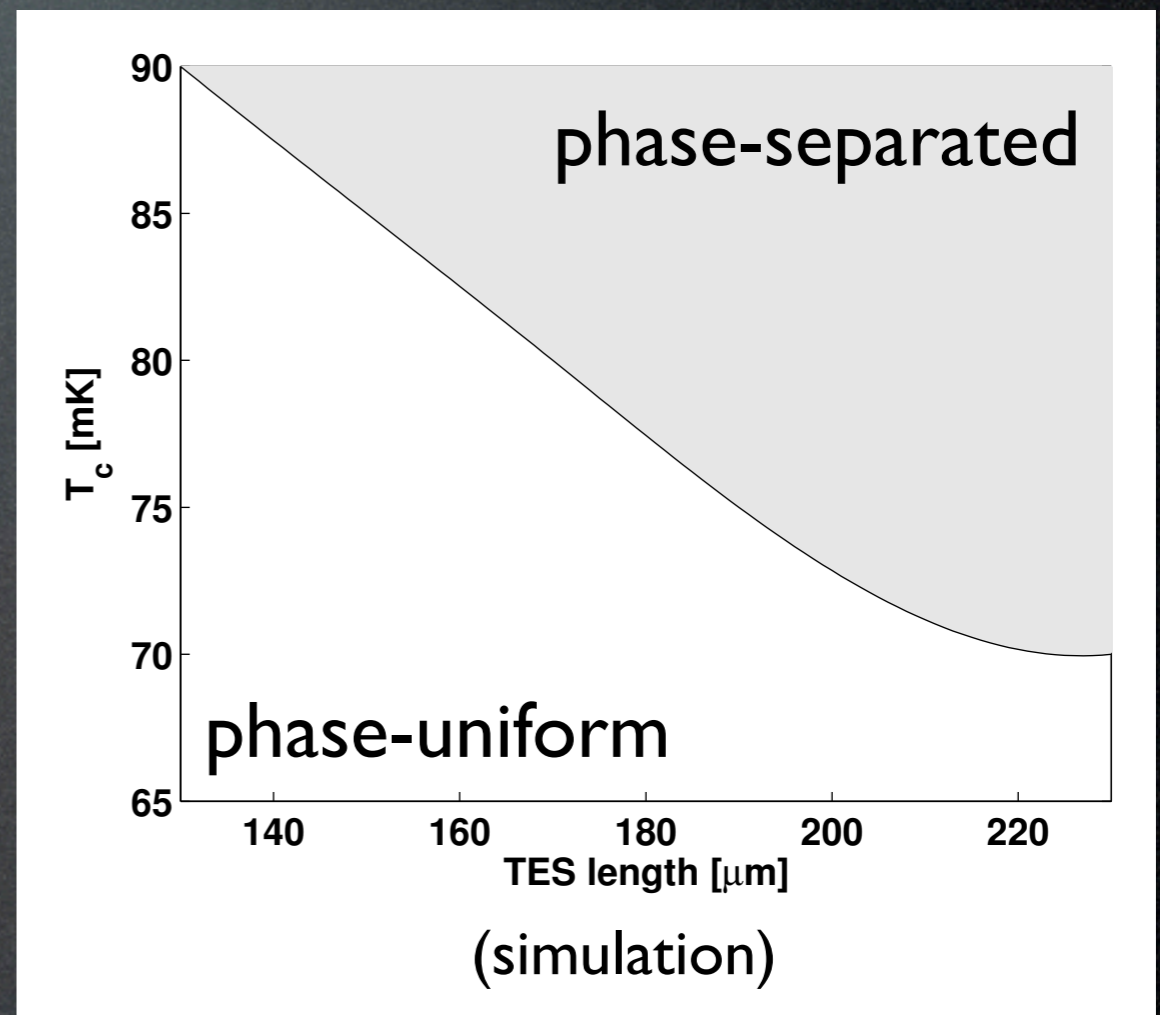
Implications for
Design, Operation and
Data Analysis

Optimize TES Length

Analytical, 1st order
Fourier expansion
of TES Joule power and
thermal diffusion
overestimates PS length

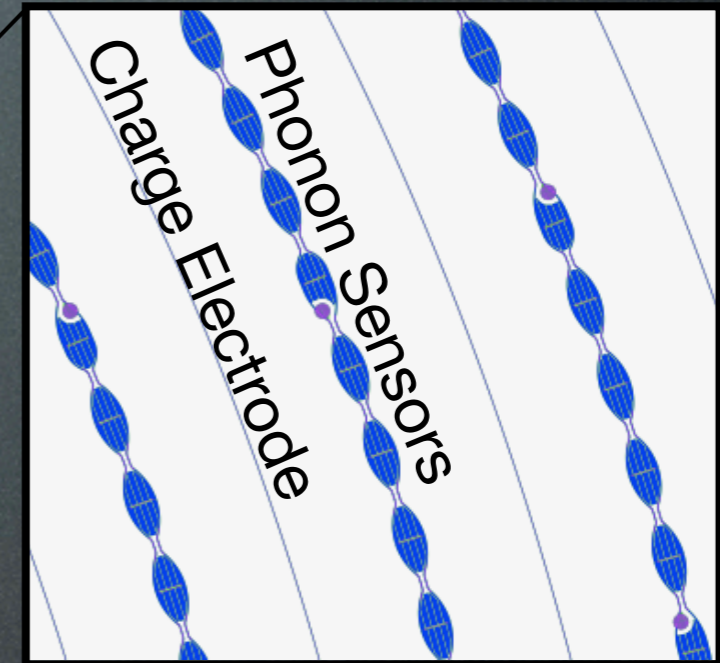
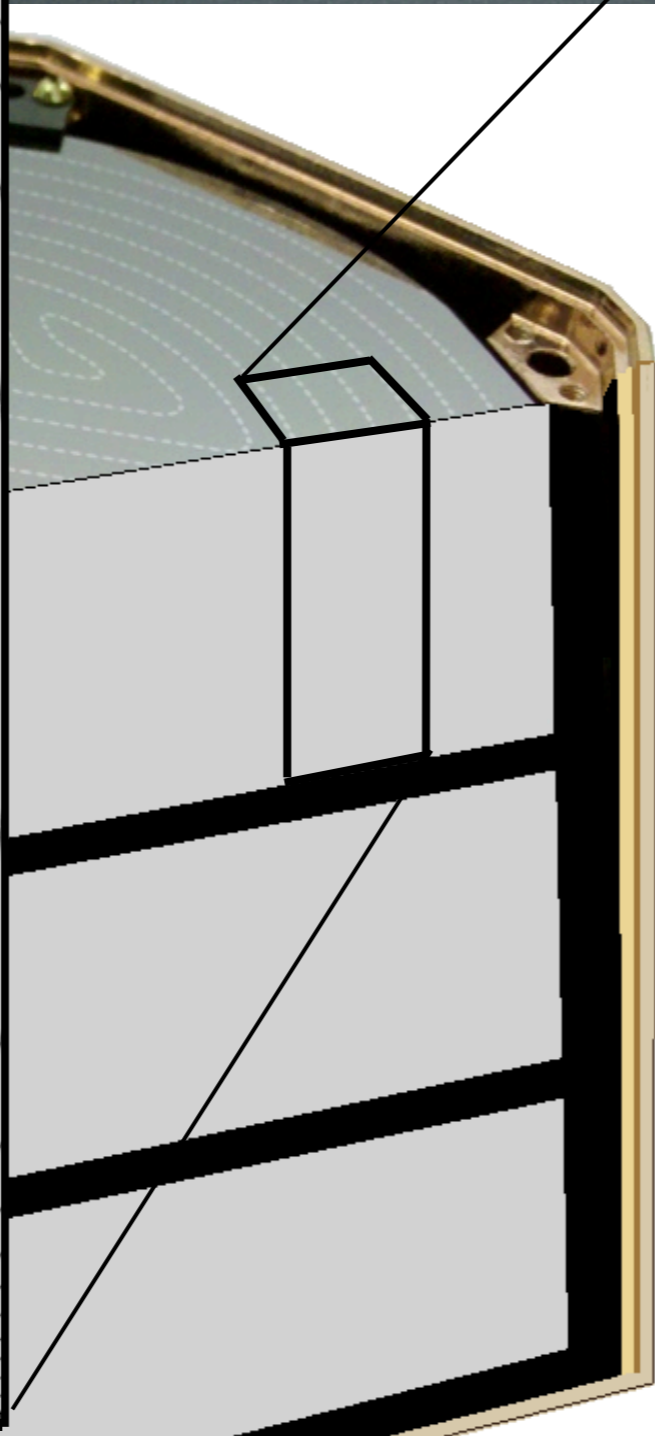
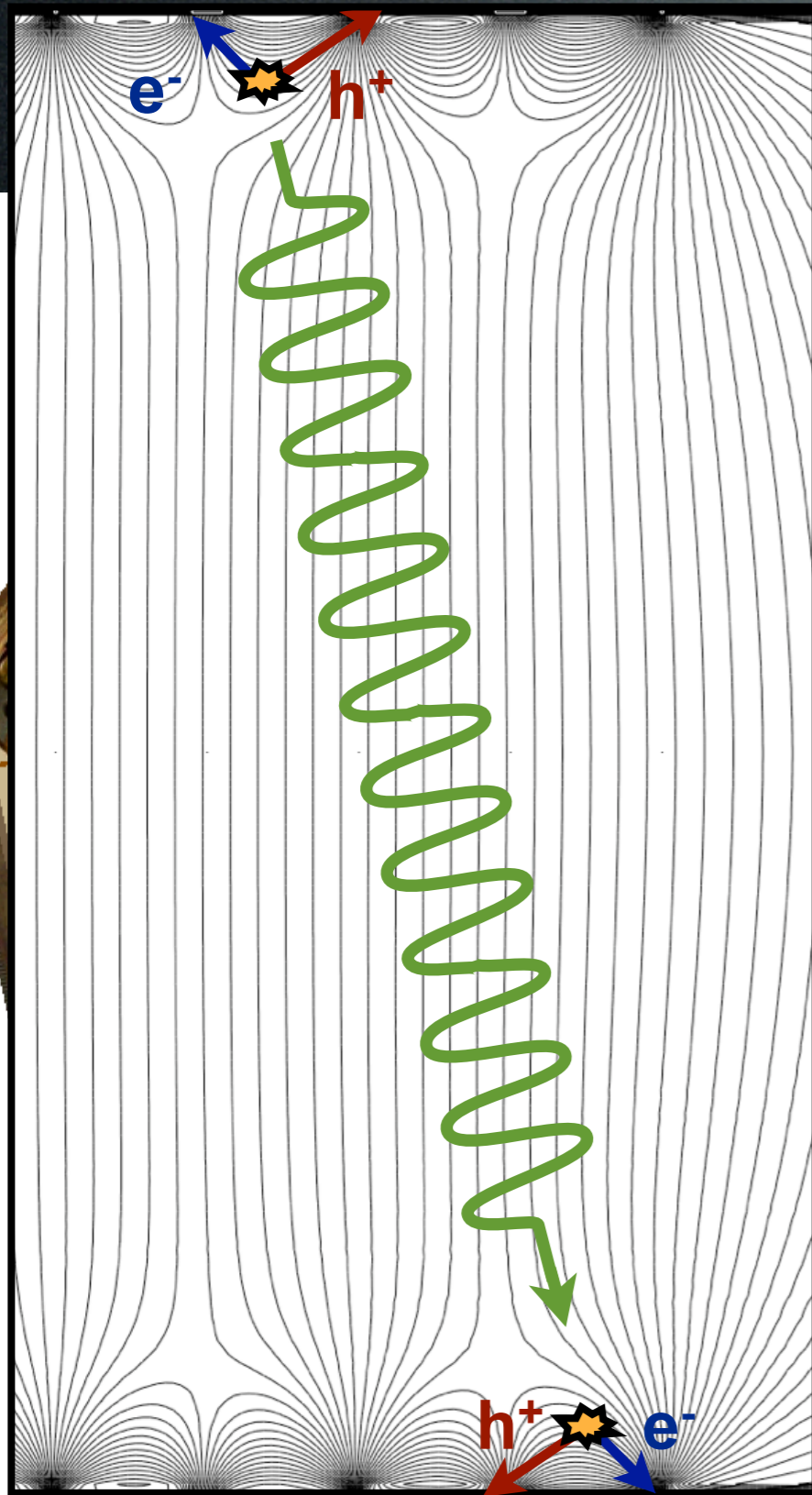
$$l_{\text{PS}} = \sqrt{\frac{\pi^2 L}{\alpha \Sigma T_c^3 \rho n}} \sim 250 \mu\text{m}$$

Numerical models more
accurate

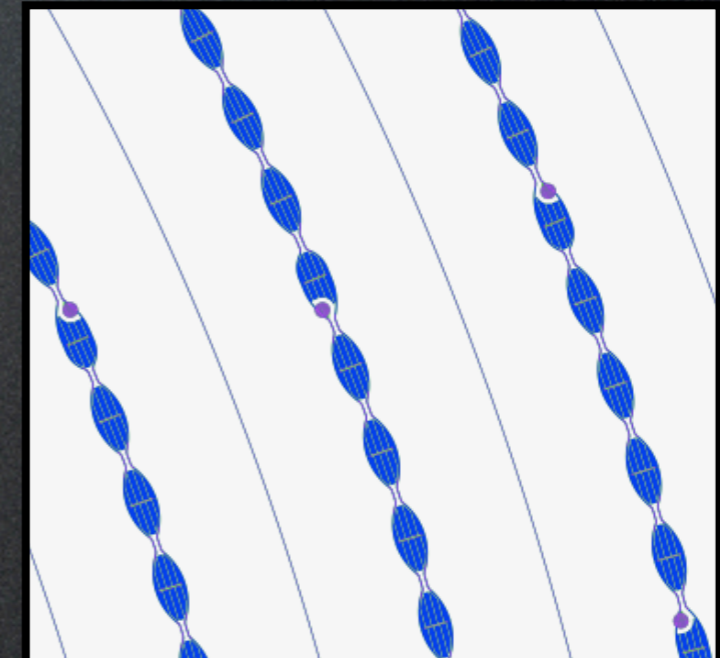




Multiple Surface Events

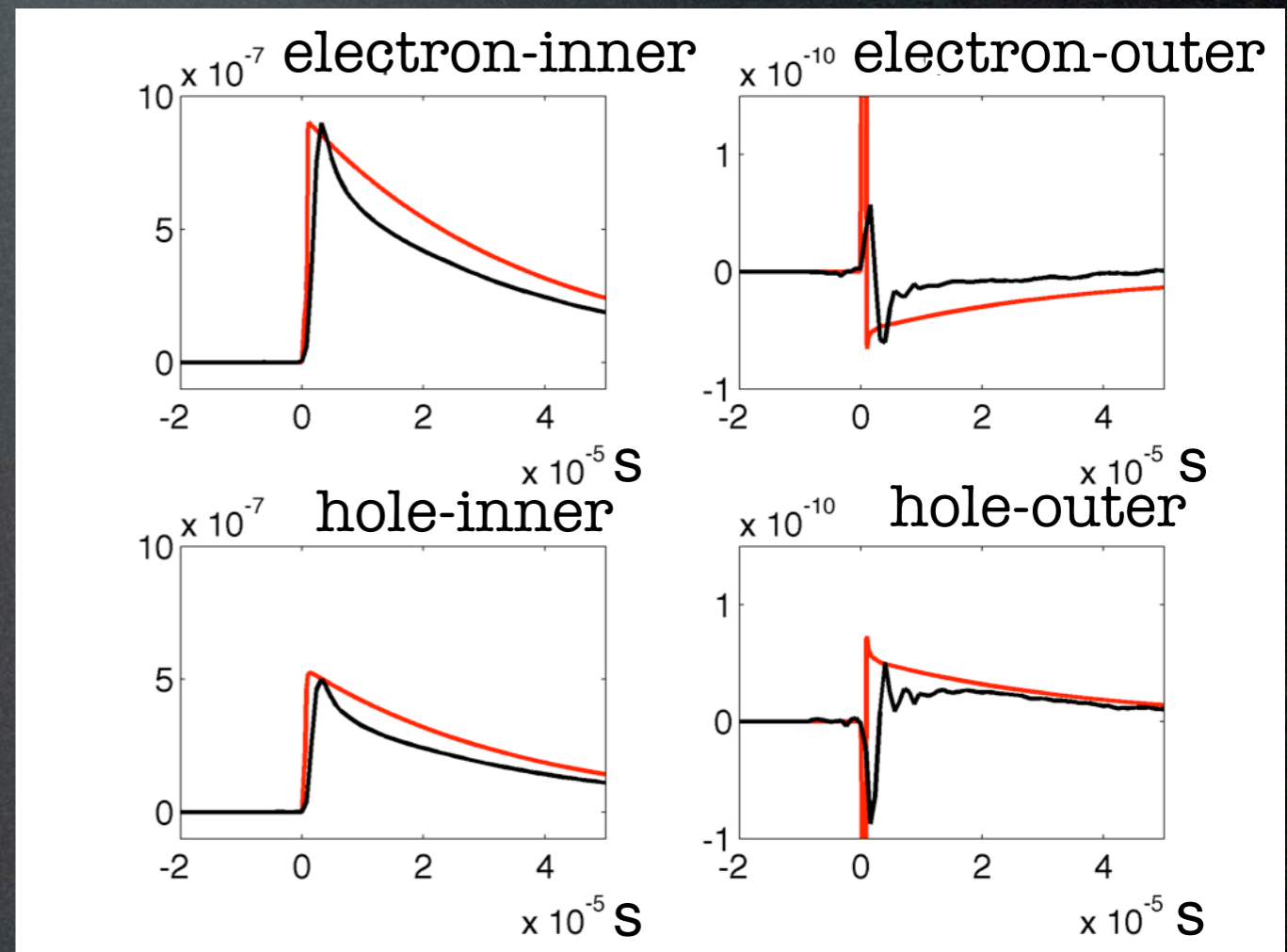


-2V 0V -2V 0V -2V 0V
2V 0V 2V 0V 2V 0V



Multiple Surface Events

- GEANT4 + MC indicate 6.8-13.6 Multiple Surface events $\text{ton}^{-1} \text{year}^{-1}$
- Phonon pulse shape rapid rise time for surface events
- Outer channel signals no signal for surface events!

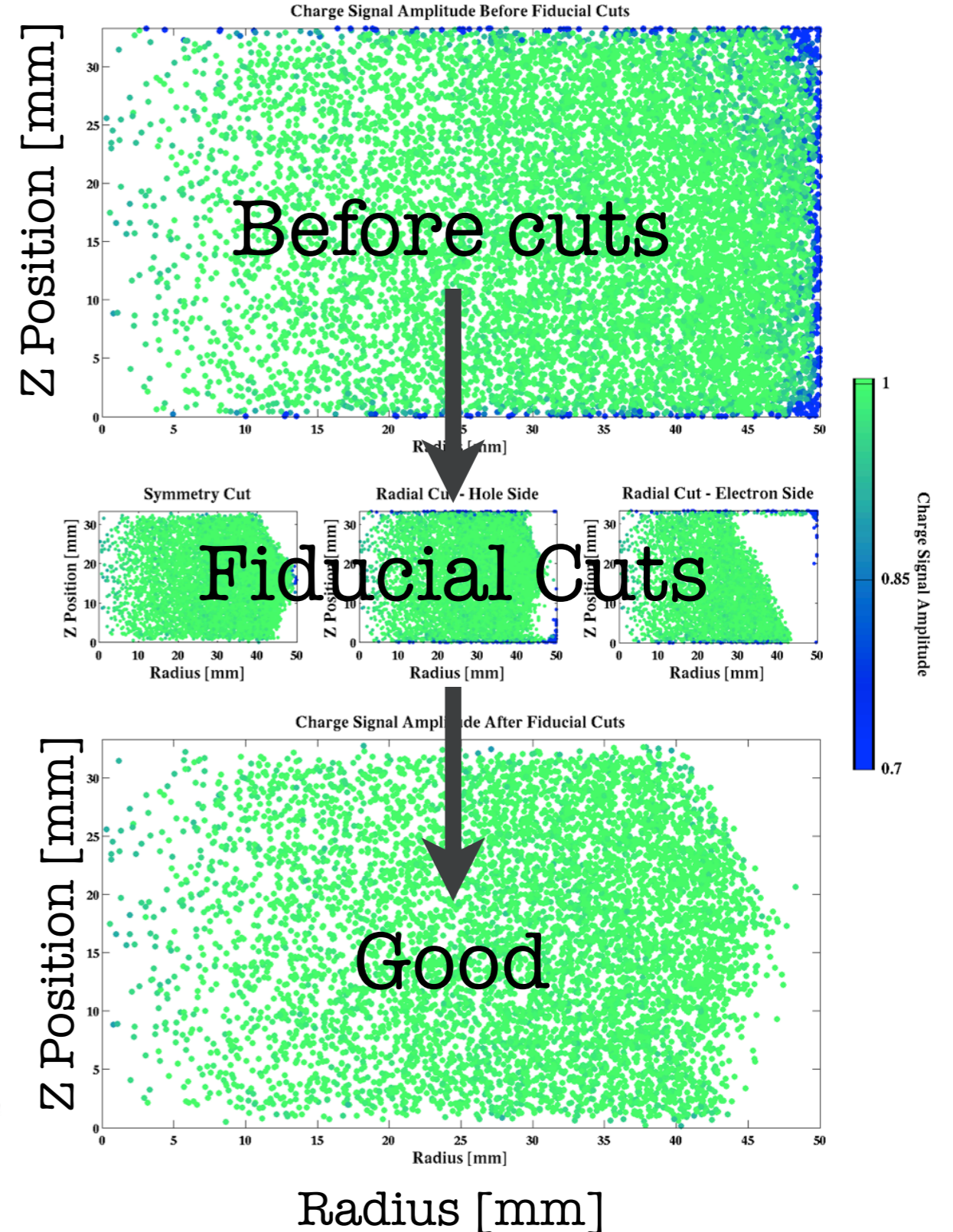


Reverse-MC Analysis

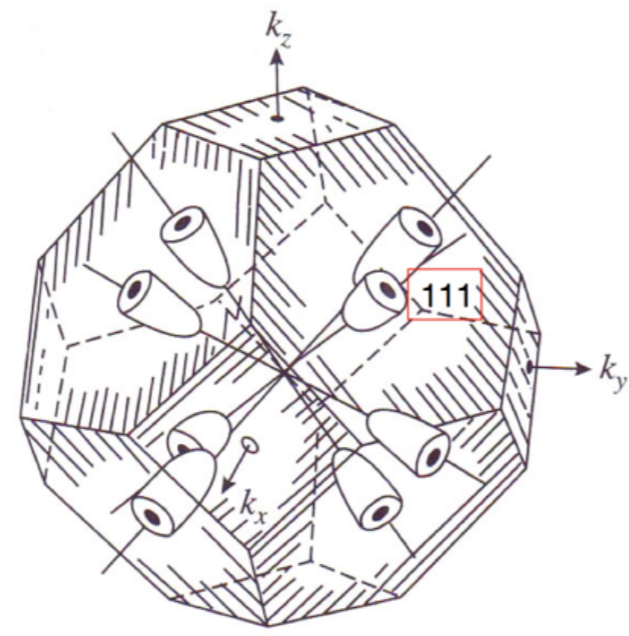
- Utilize all phonon pulse shape and charge information for
 - Event classification
 - Bulk / surface
 - Gamma / nuclear recoil
 - Single / multiple
 - Energy estimation

Charge Fiducial Volume

diameter × thickness [mm]	orientation	Cu can diameter [mm]	Ge-Cu space [mm]	fiducial volume [g]	fiducial volume [%]
76.2 × 25.4	100	80.2	2	400	64
76.2 × 25.4	100	84.2	4	380	61
76.2 × 25.4	100	92.2	8	360	58
100 × 25.4	100	104	2	720	67
100 × 25.4	100	108	4	700	66
100 × 25.4	100	116	8	700	65
100 × 33.33	100	104	2	980	70
100 × 33.33	100	108	4	950	68
100 × 33.33	100	116	8	920	66
76.2 × 25.4	111	80.2	2	380	61
76.2 × 25.4	111	84.2	4	380	61
76.2 × 25.4	111	92.2	8	370	59
100 × 25.4	111	104	2	700	66
100 × 25.4	111	108	4	700	66
100 × 25.4	111	116	8	700	65
100 × 33.33	111	104	2	950	68
100 × 33.33	111	108	4	950	68
100 × 33.33	111	116	8	940	67



Design work on electrode structure and tower design ongoing



Advanced detector MC of cryogenic, phonon and ionization detectors

Charge

- E-field models
- Electron mass tensor
- Electron inter-valley scattering
- Neganov-Luke phonons
- Ramo-Shockley potential signal

Phonon

- Phonon focusing
- Isotope scattering
- Anharmonic decay
- Quasiparticle / phonon
downconversion

Transition Edge Sensor

- Phase separation
- Internal fluctuation noise

Validation

- Electron inter-valley scattering
- Phonon pulse shape

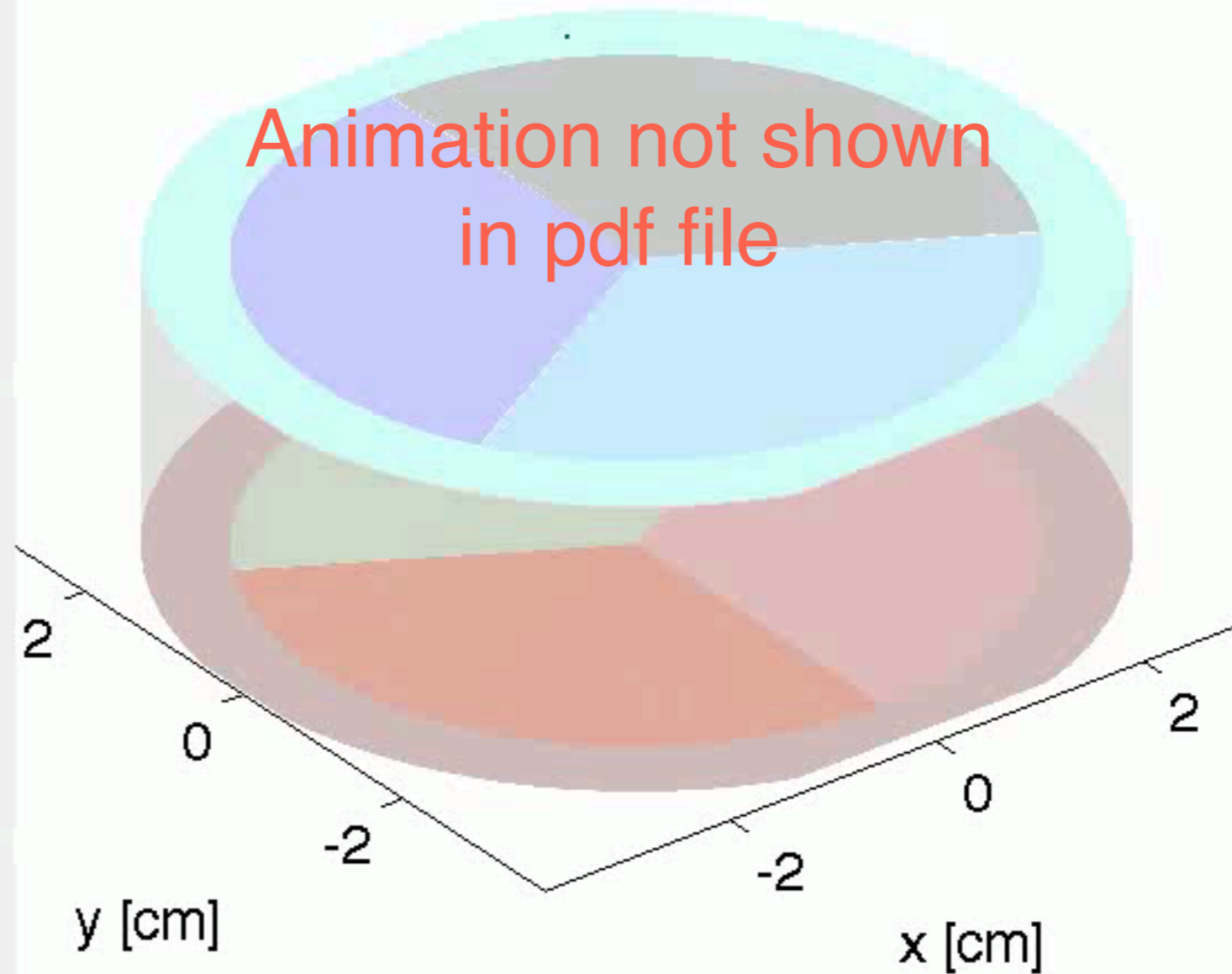
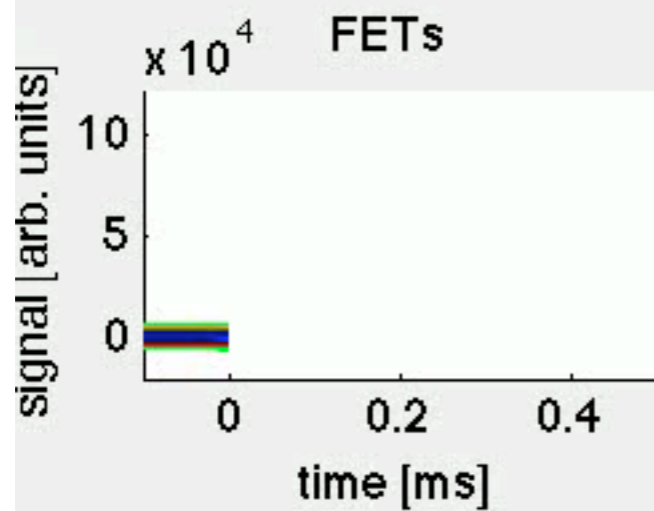
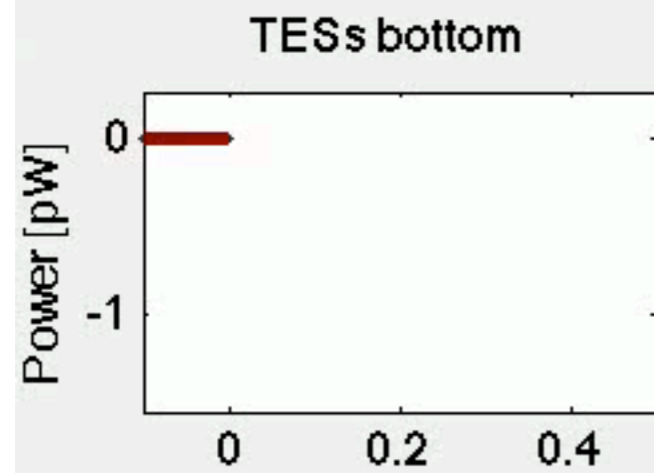
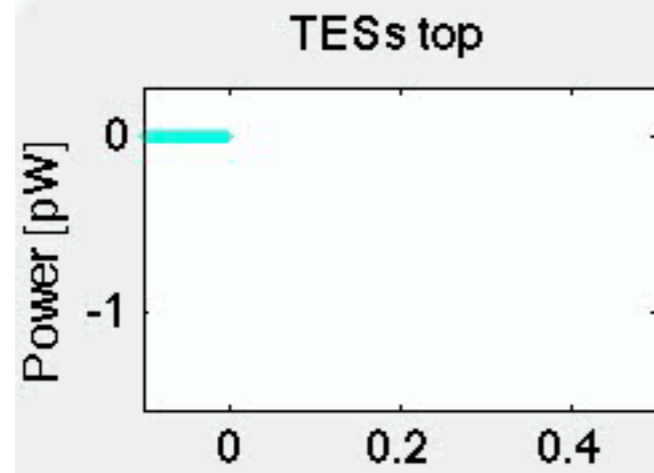
Usage

- Phonon channel layout
- Charge channel layout
- Crystal orientation
- TES phase separation length
- TES noise
- Background rejection
- Reverse-MC data analysis

Backup Slides

100-110 Crystal Orientation

Animation not shown
in pdf file

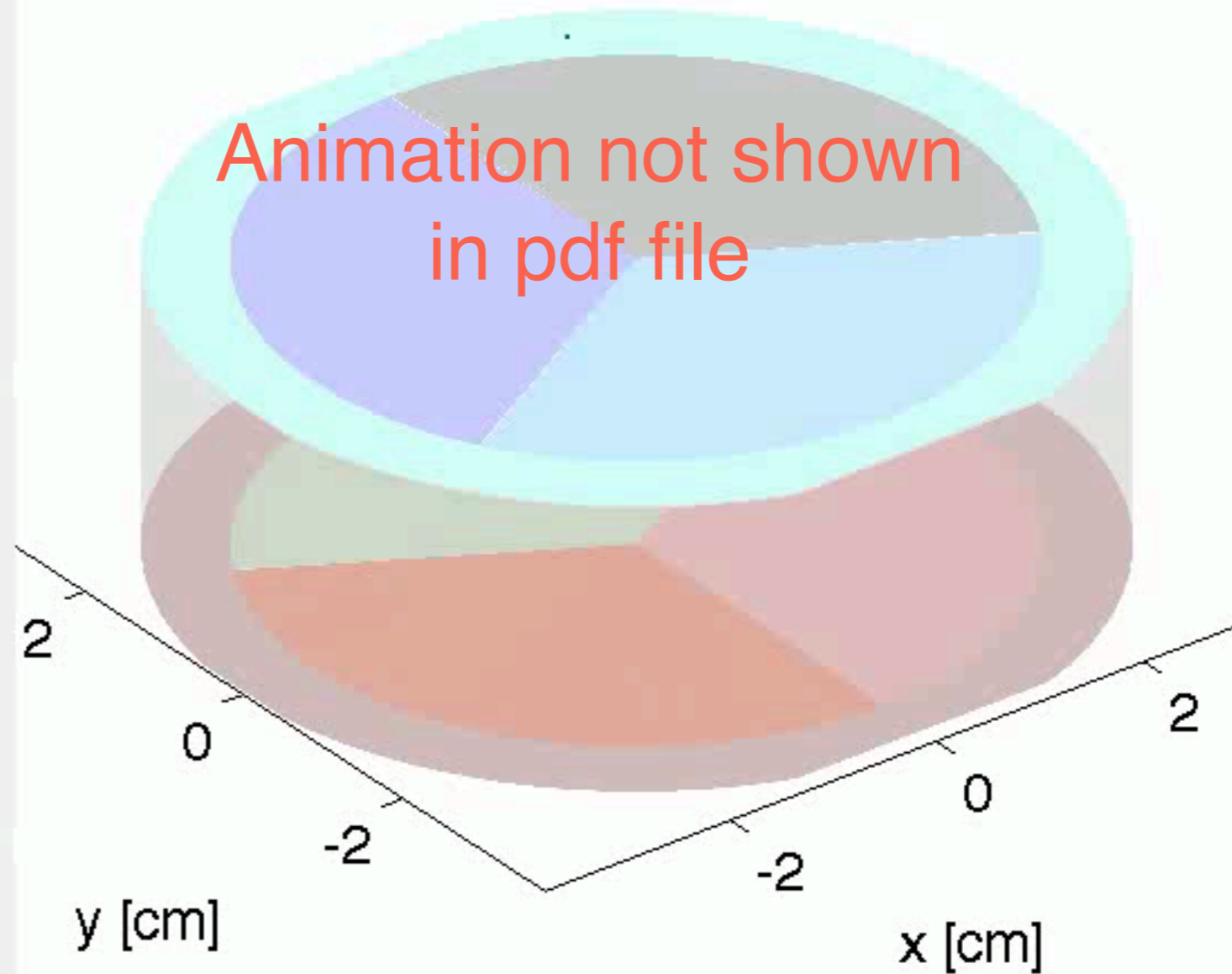
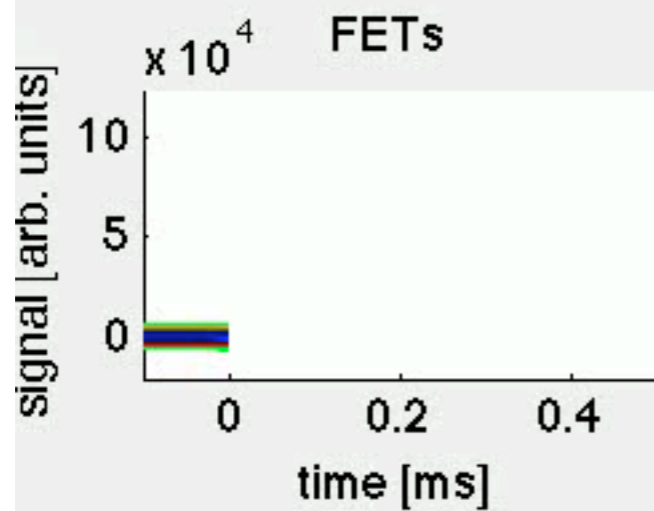
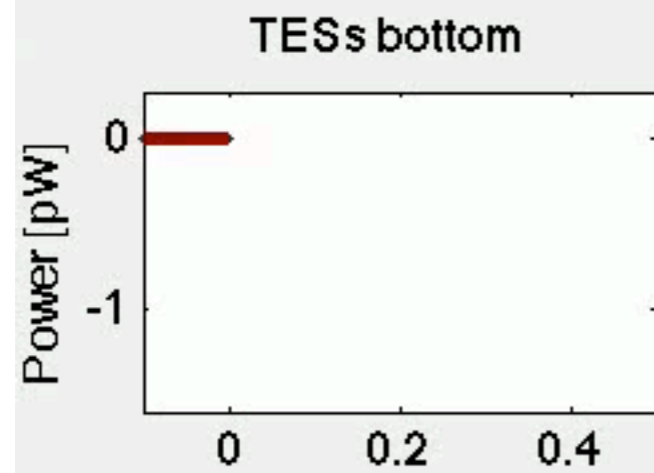
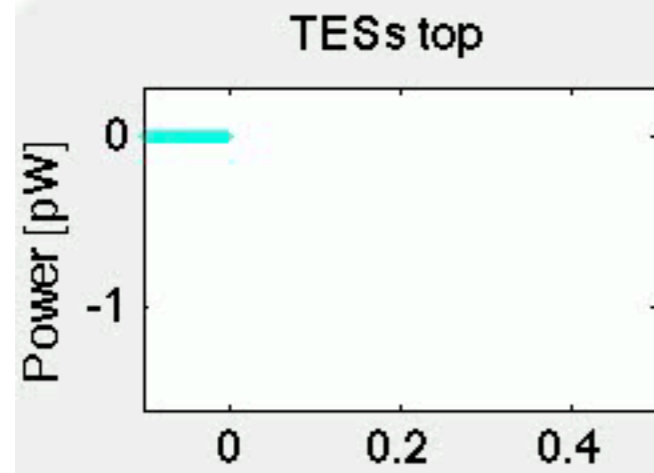


Q top, outer
Q top, inner
Q bottom, inner
Q bottom, outer

fast transverse
slow transverse
longitudinal
 $t = 1.7e-10$

111-122 Crystal Orientation

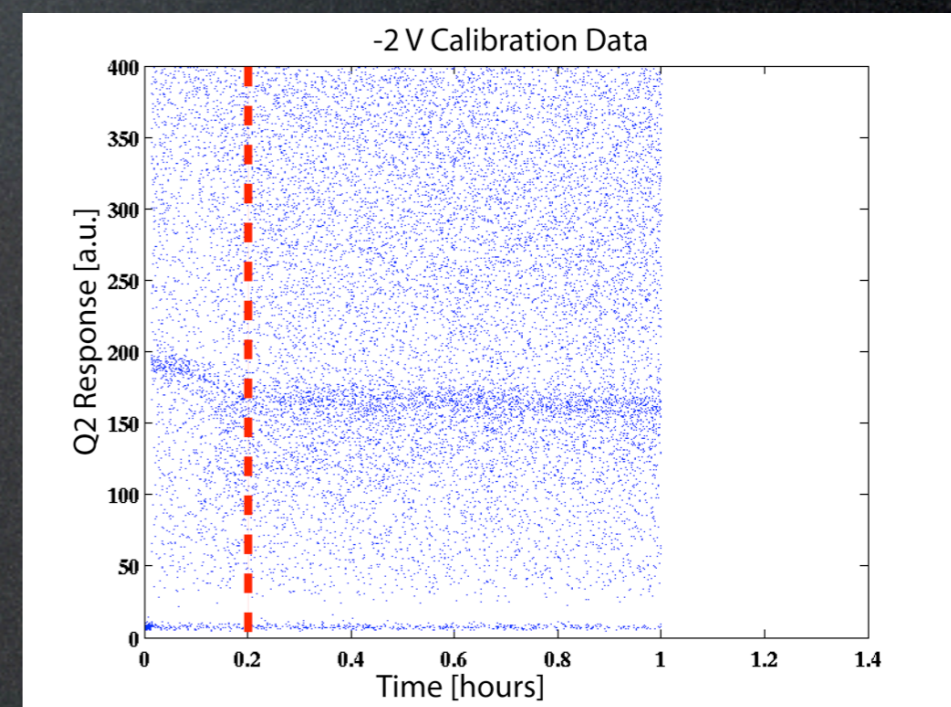
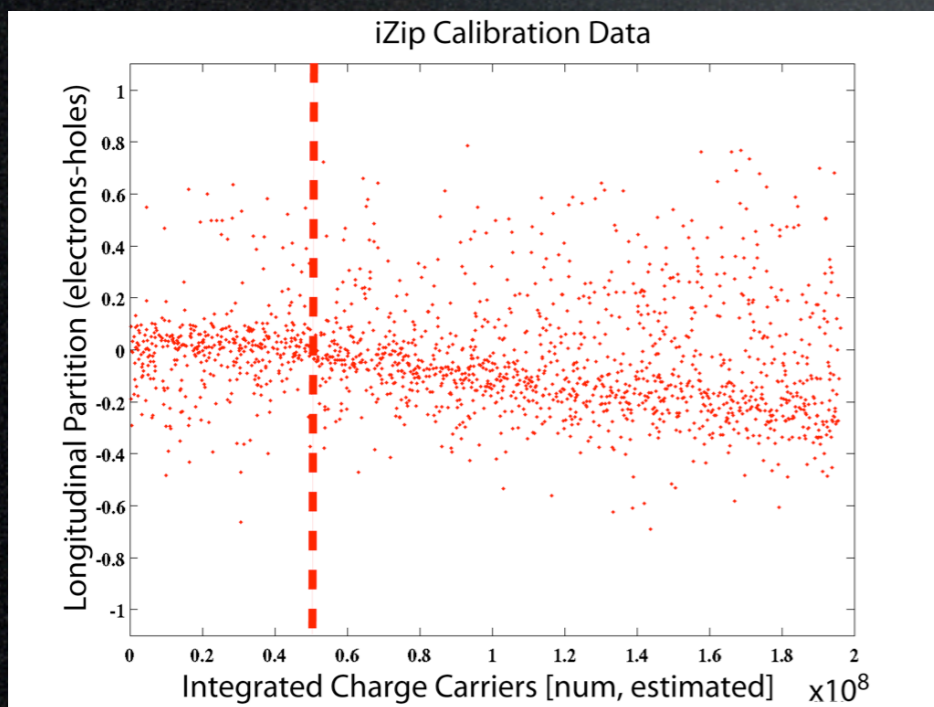
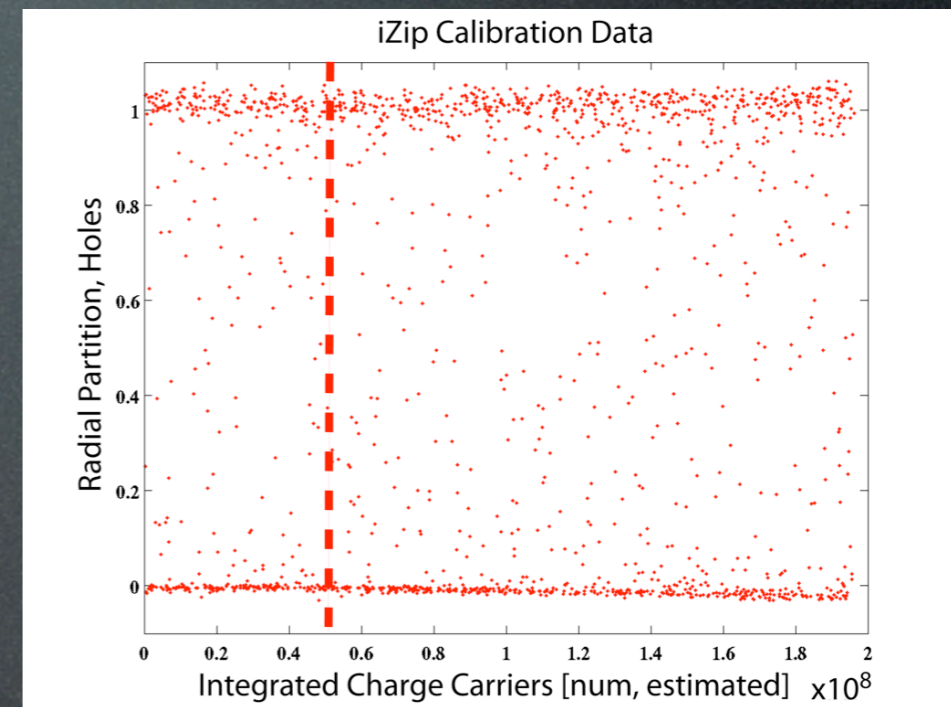
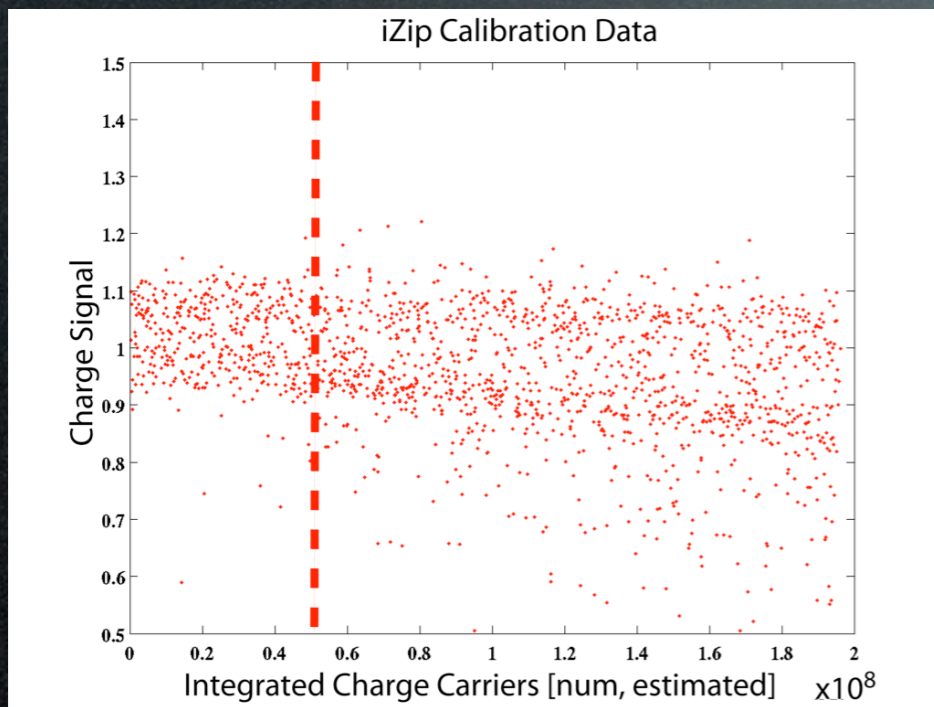
Animation not shown
in pdf file



Q top, outer
Q top, inner
Q bottom, inner
Q bottom, outer

fast transverse
slow transverse
longitudinal
 $t = 1.7e-10$

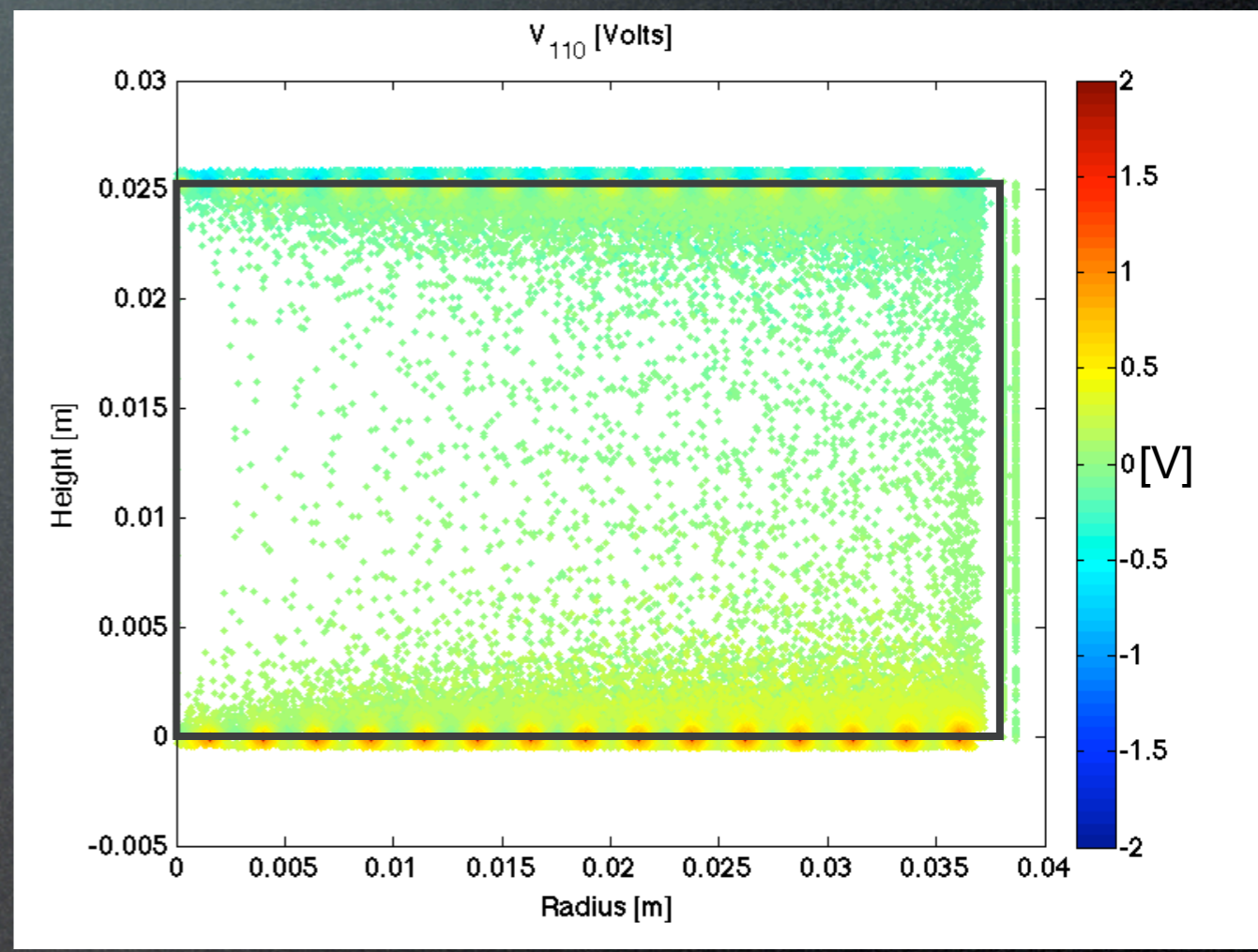
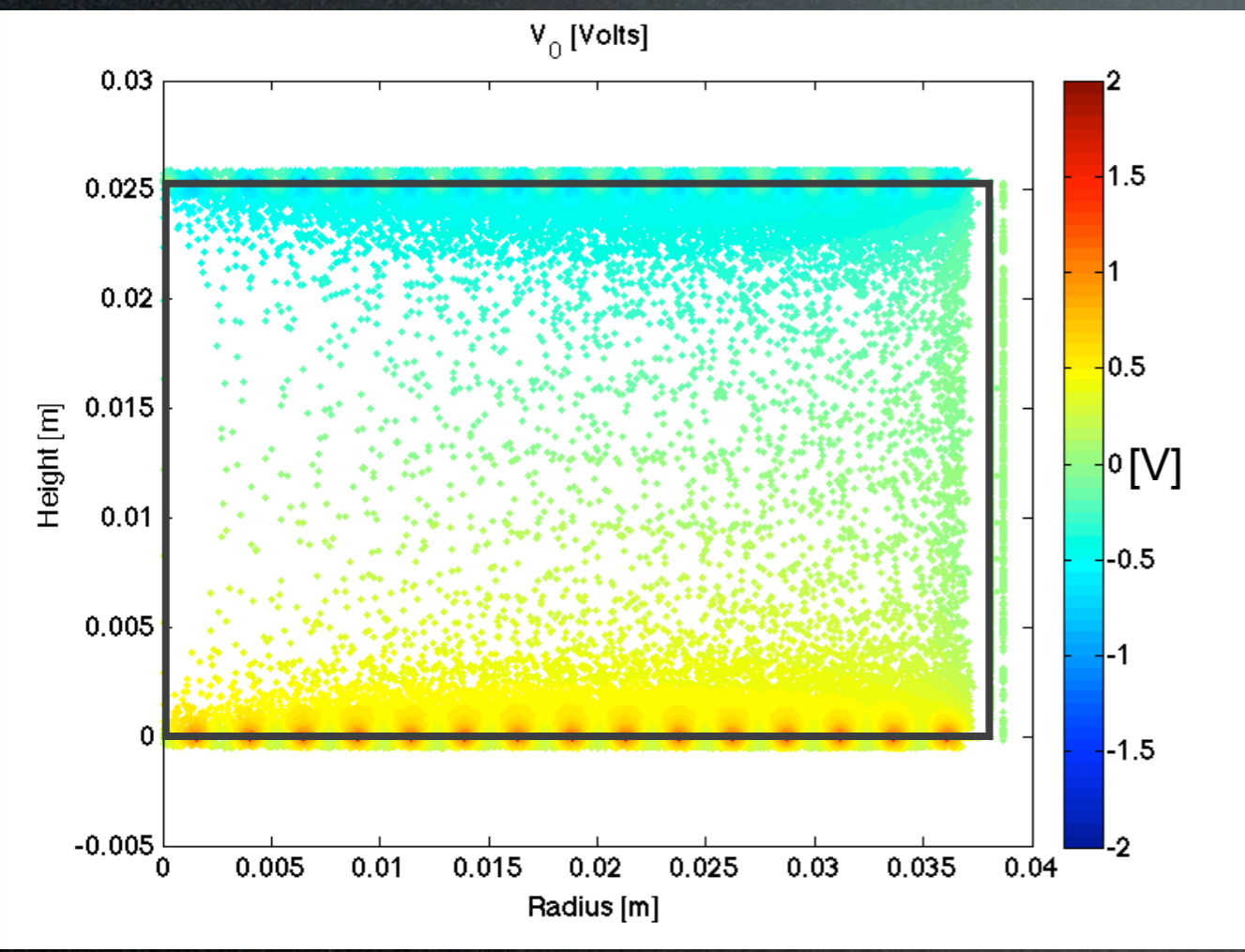
Charge Degradation



Event Induced Potential

Initial

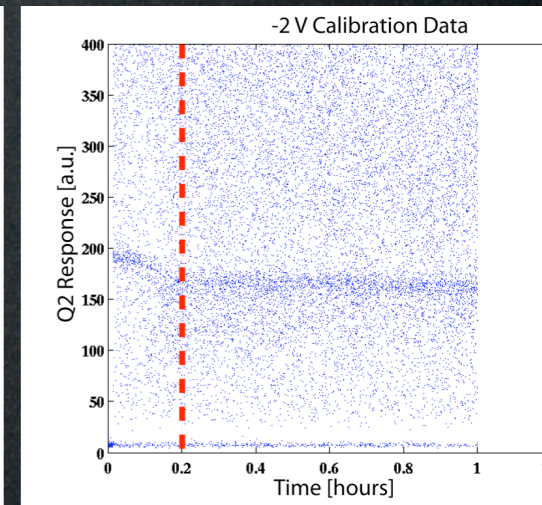
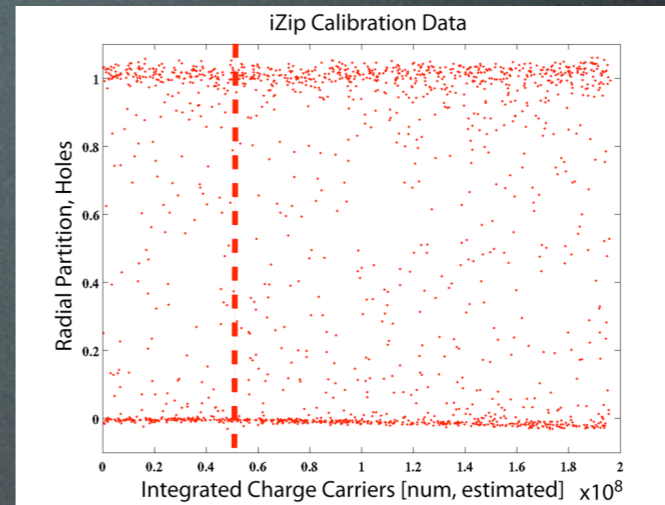
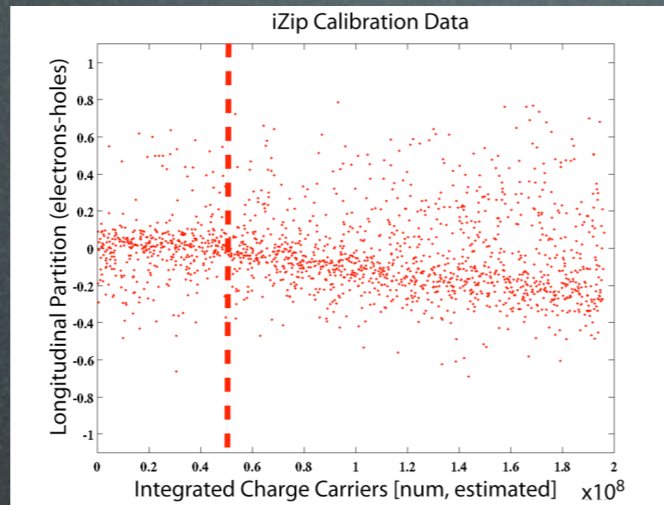
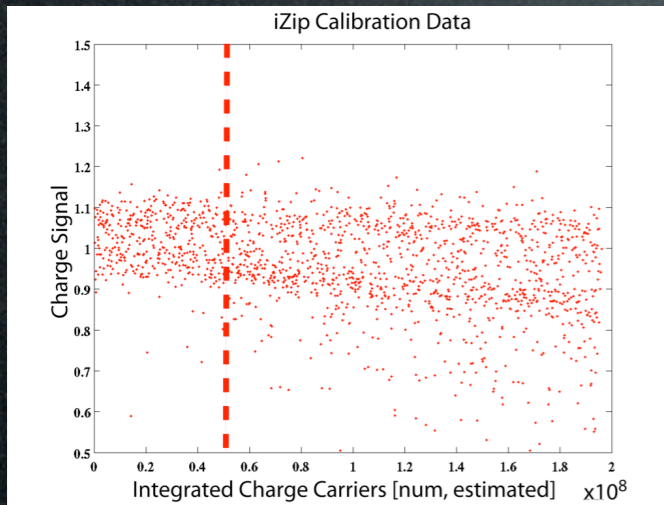
After gamma exposure



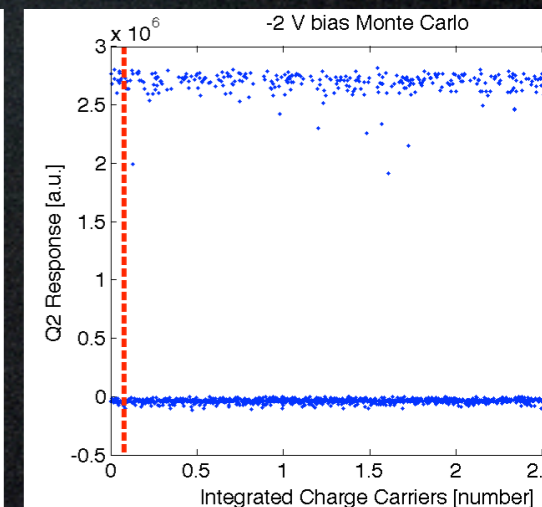
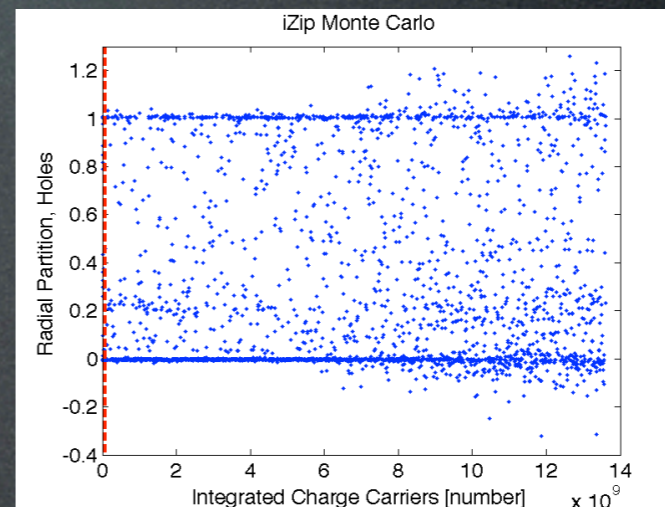
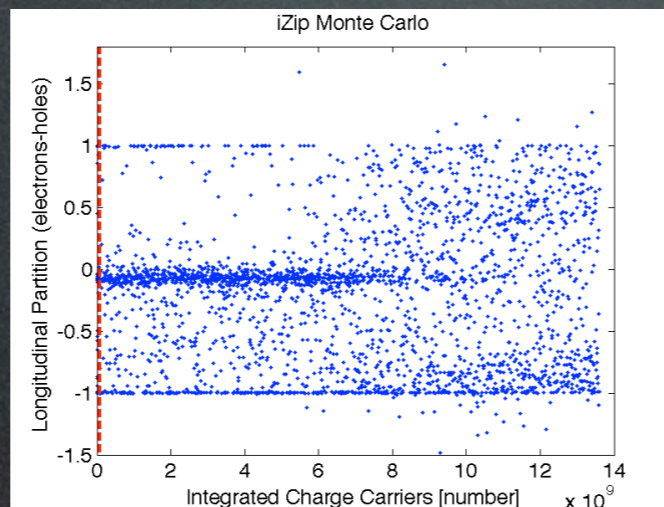
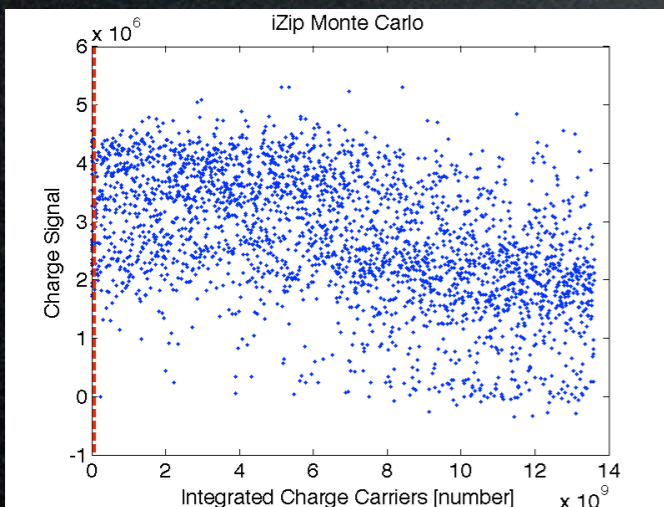
dots indicate mesh points

Data vs. MC

Data



MC



----- Period of comparable gamma exposure

- Not the right model! A red herring?

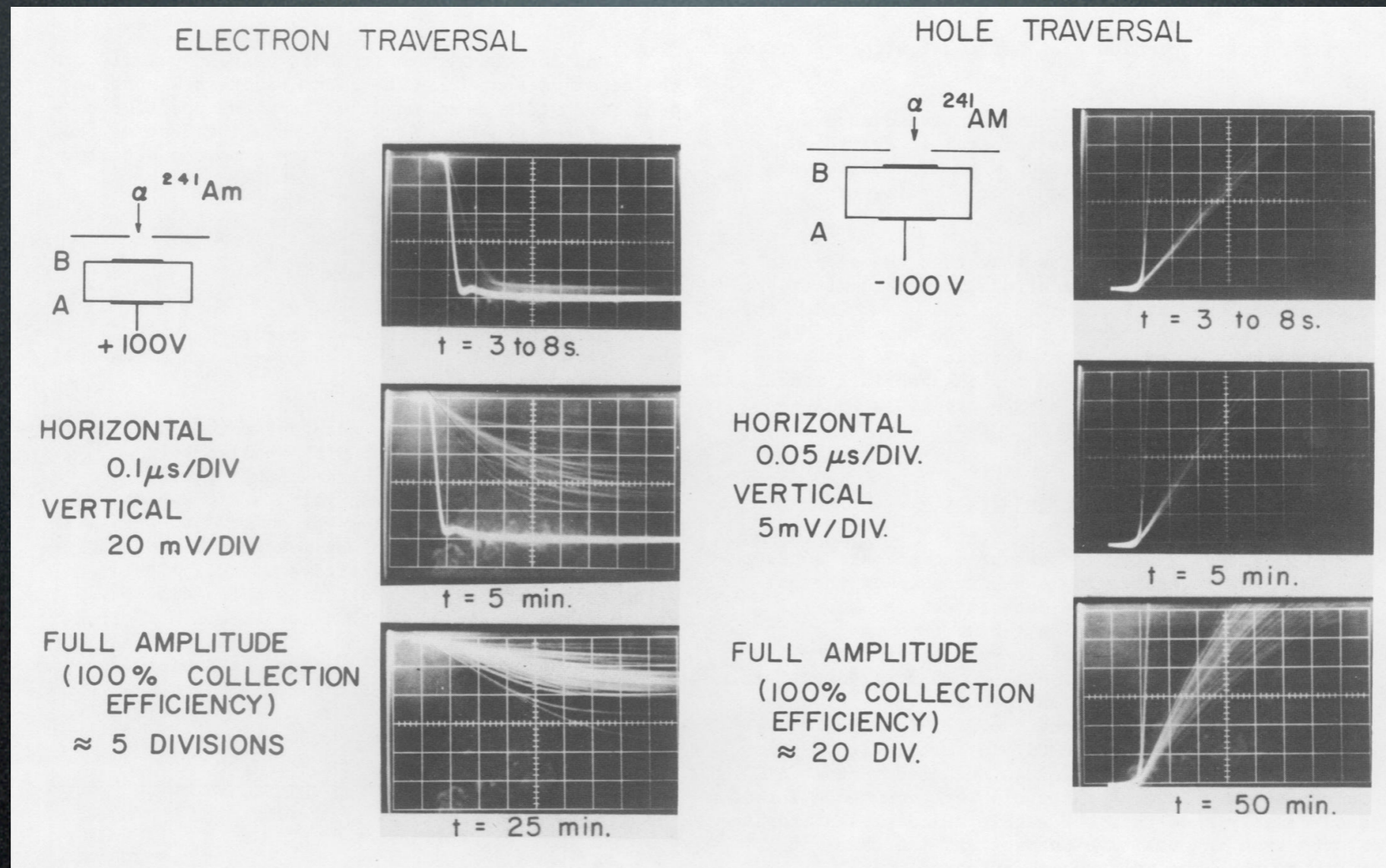
Polarization In CdTe

- Similar effect seen in CdTe
 - Independent of radiation rate
 - Depolarization faster than polarization
 - Consistent with negative space charge

CdTe Conclusion

- Ionization of deep acceptors
- Mitigation steps
 - Pulsing bias off
 - Different contact materials

Early Identification



- Possibly can be identified by slowing of electron transport times

Temperature Dependence

$$\tau_I = \frac{1}{N_0 \sigma \langle v \rangle} \exp(E/kT)$$

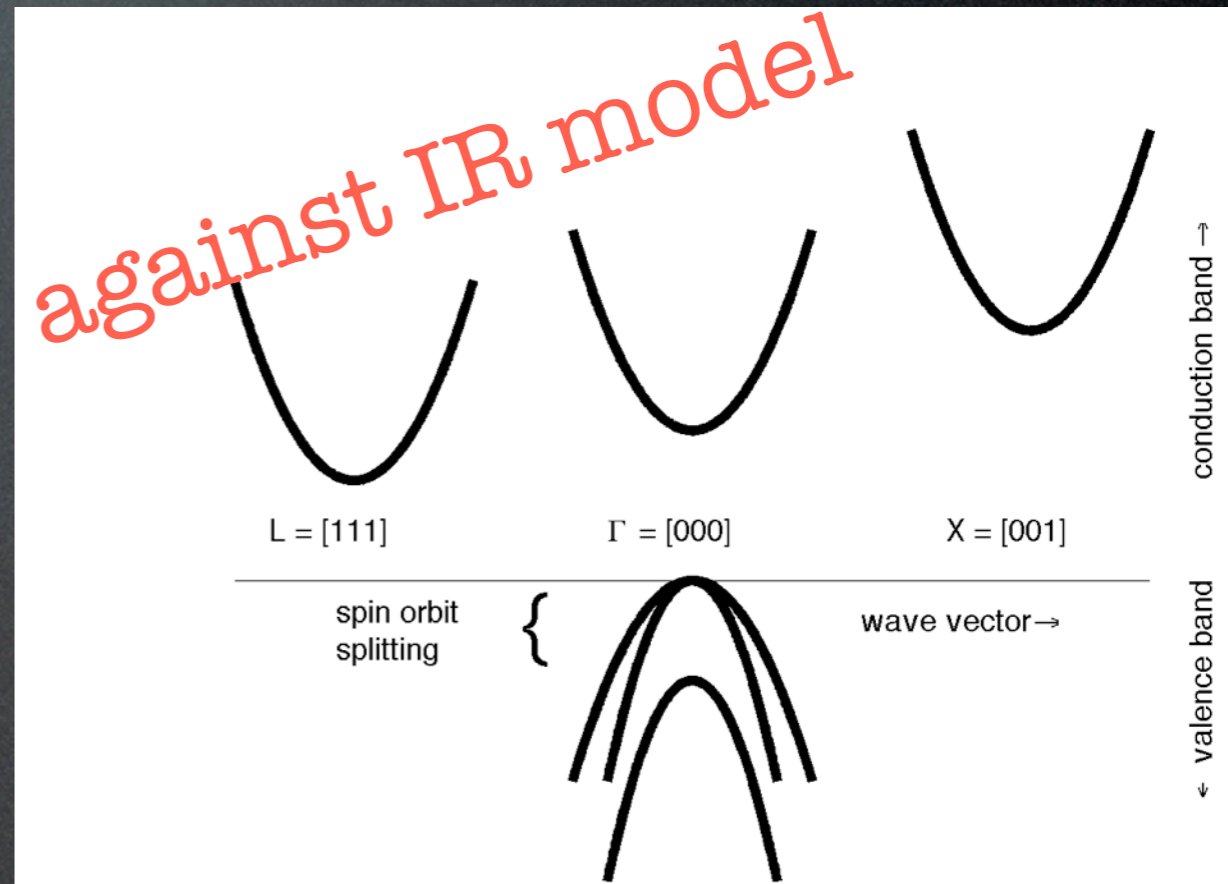
$$\tau_D = \frac{1}{N_v \sigma \langle v \rangle}$$

- But temperature dependence not observed in iZIP
- Are we seeing polarization similar to CdTe? Or is this a red herring?

Infrared Radiation?

- 0.7 eV bandgap is $>$ IR energy
- Ge is an indirect gap semiconductor, no phonons to mediate excitation at 50 mK

against IR model



Infrared Radiation?

Optical efficiency of far-infrared photoconductors

J.-Q. Wang, P. L. Richards, J. W. Beeman, N. M. Haegel, and E. E. Haller

We report an experimental and theoretical study to optimize the geometry of far-IR photoconductive detectors with diffraction-limited throughput. Factors considered in this optimization include internal optical path relative to measured absorption length, photoconductive gain, uniformity of illumination, cosmic ray cross section, and compatibility of the design with the requirements of 1- and 2-D arrays. A rod-shaped detector geometry with square cross section, electrodes on the lateral faces, and a beveled backface to trap the radiation by total internal reflection was found to have nearly equal responsivity to the best detectors in integrating cavities.

- Doped germanium detectors are used for IR detection!!!
- Gap reduced at dopants
- Not indirect gap at dopants

Evidence for IR

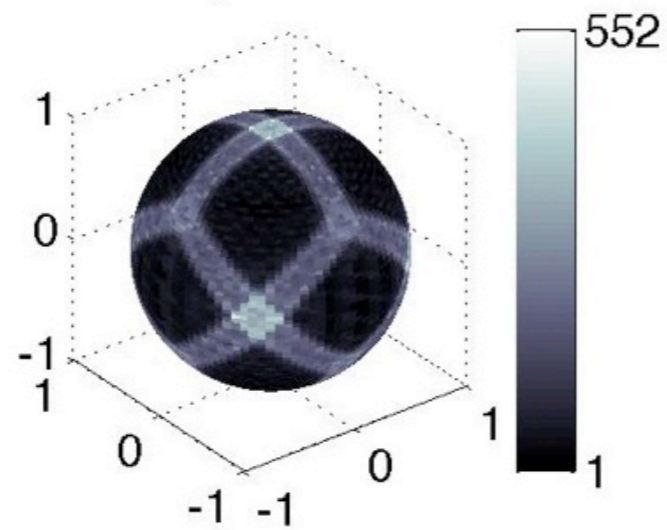
- Difference seen in Berkeley vs Soudan could be due to different IR environment.
- However attempts to reduce / increase IR at Berkeley show no change in degradation.
- Performance in present run much improved!

Fano Fluctuations

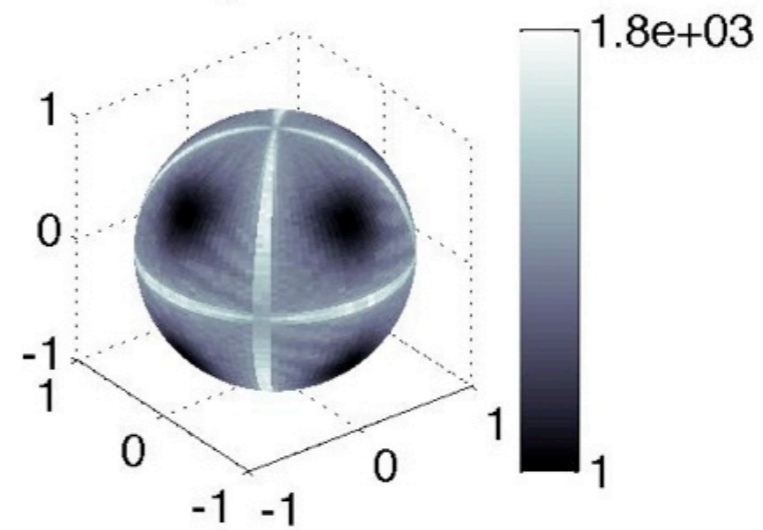
- $E_{\text{creation}} = 3 \text{ eV}$ to create charge carrier
- 0.75 eV bandgap
- Fluctuation in carriers
$$\sigma^2 = F * E_{\text{gamma}} / E_{\text{creation}}$$
$$F_{\text{Ge}} = 0.1$$

Phonon Group Velocity

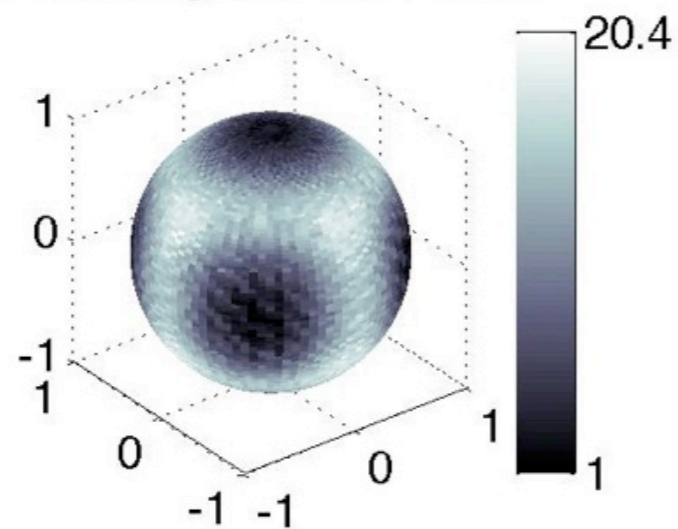
ST Intensity 3249 m/s 54%



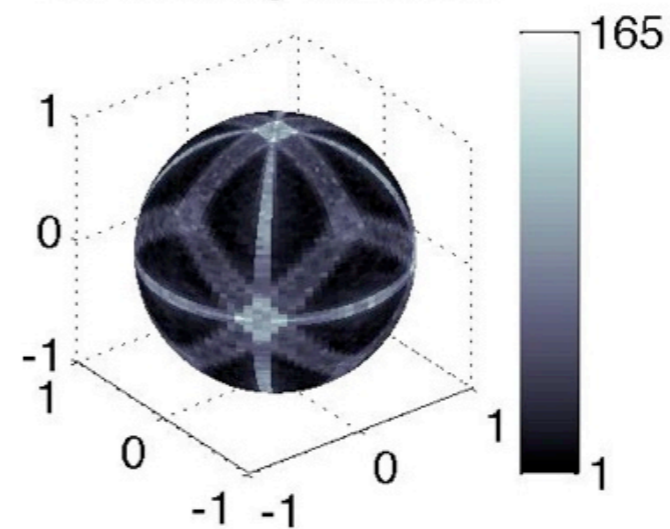
FT Intensity 3509 m/s 37%



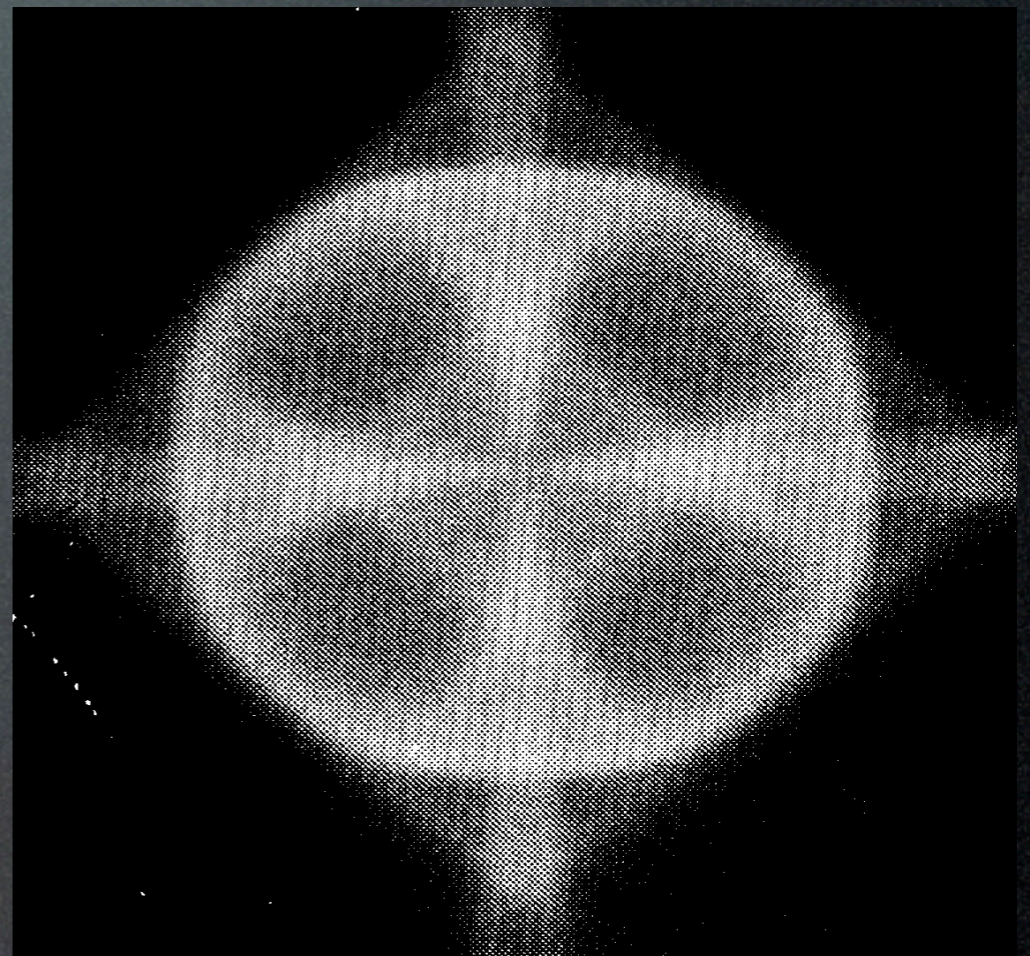
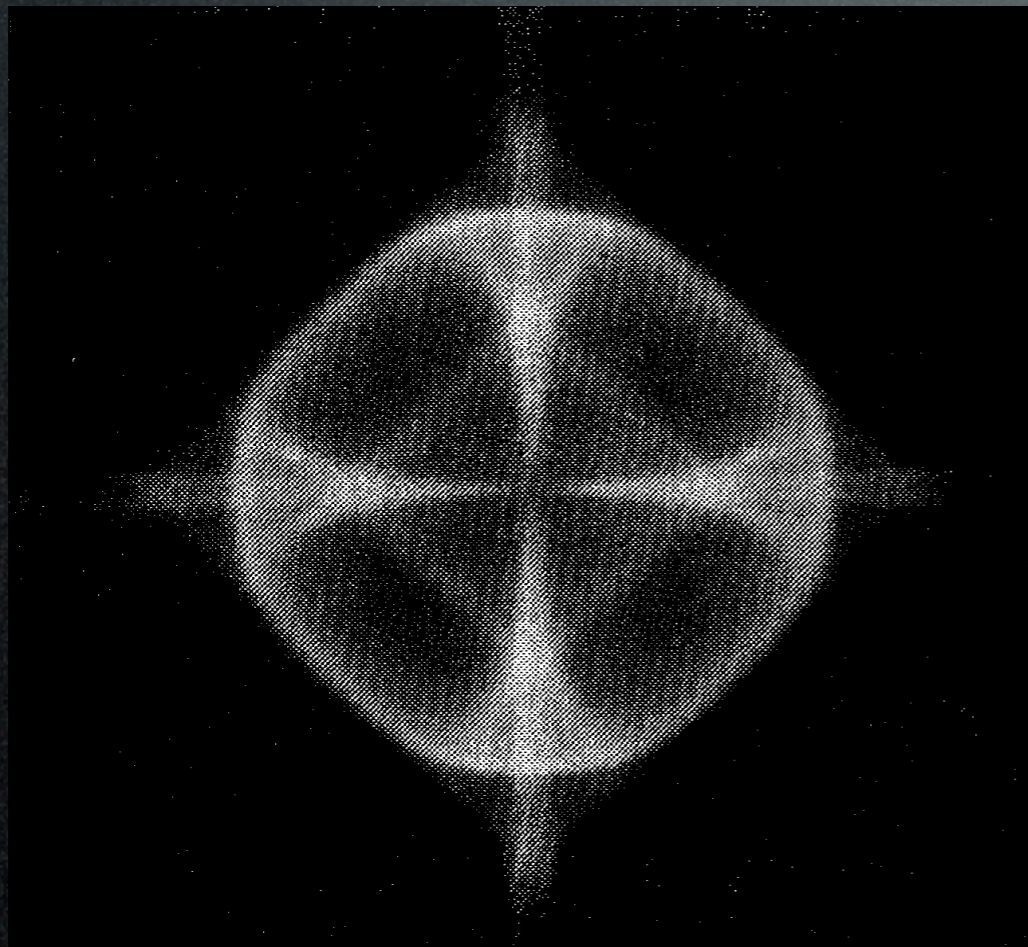
L Intensity 5324 m/s 9.8%



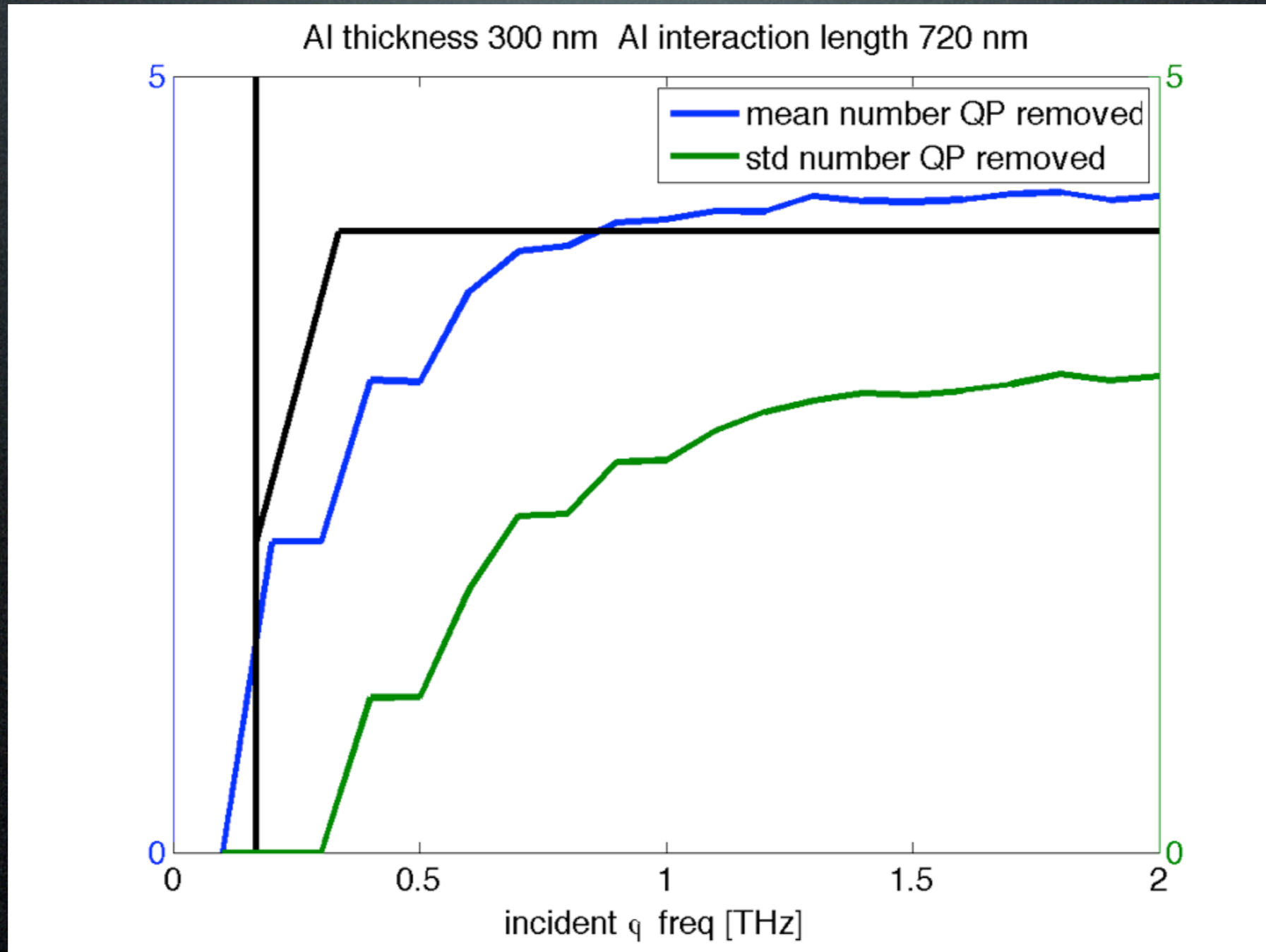
All Intensity 3548 m/s

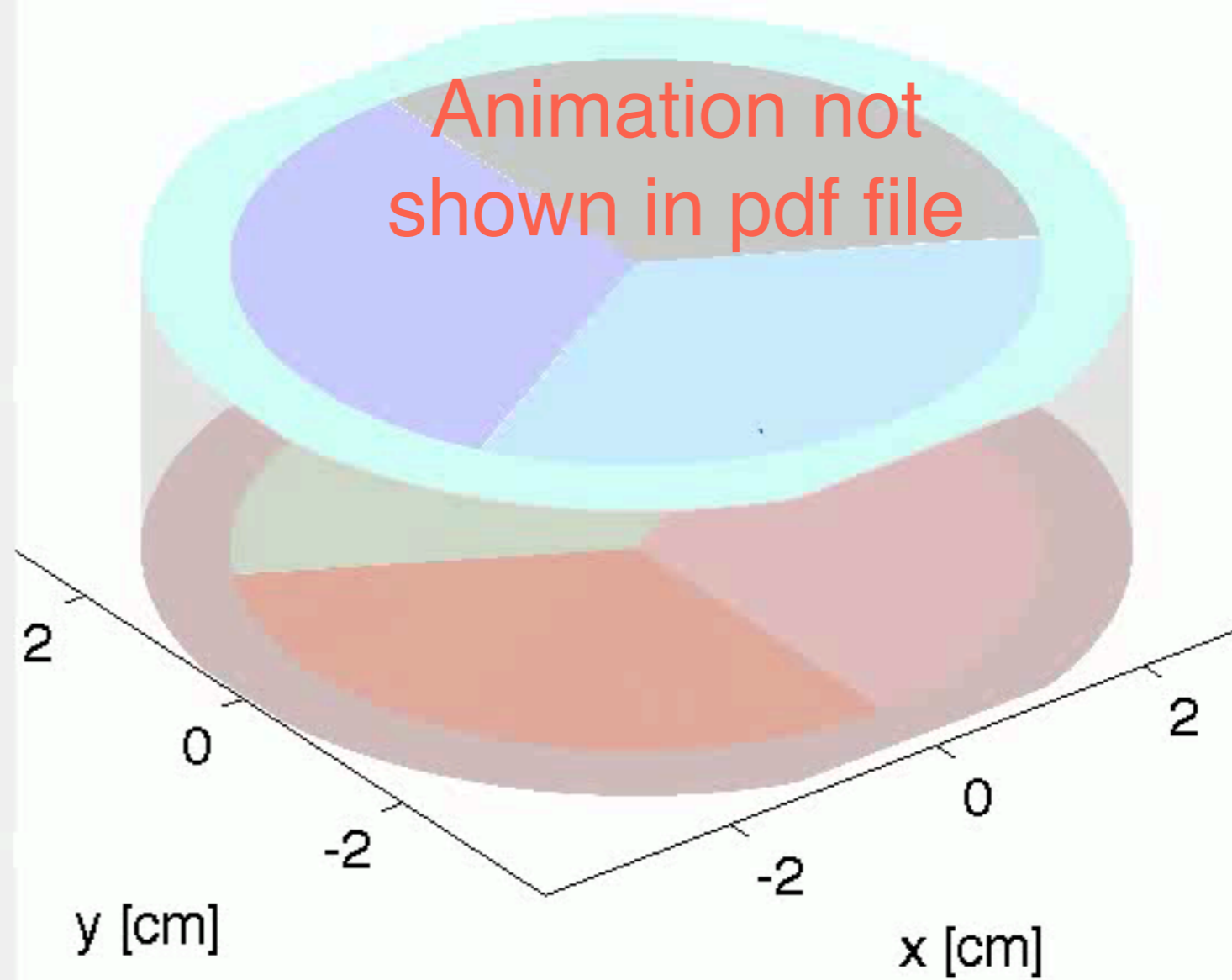
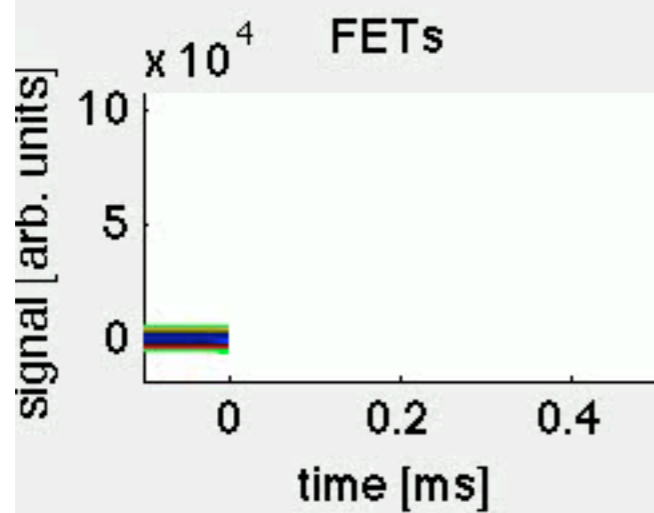
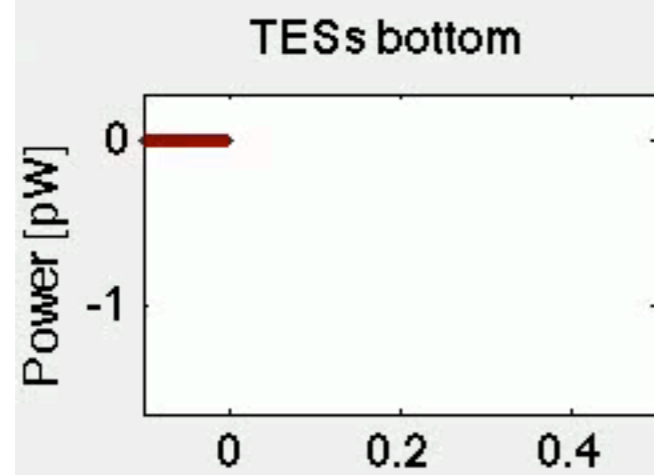
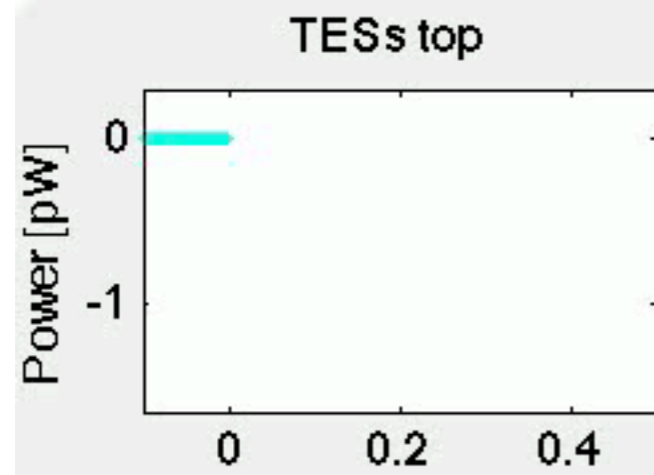


Phonon Focusing Images in $[100]$ Si



Quasiparticle / Phonon Downconversion





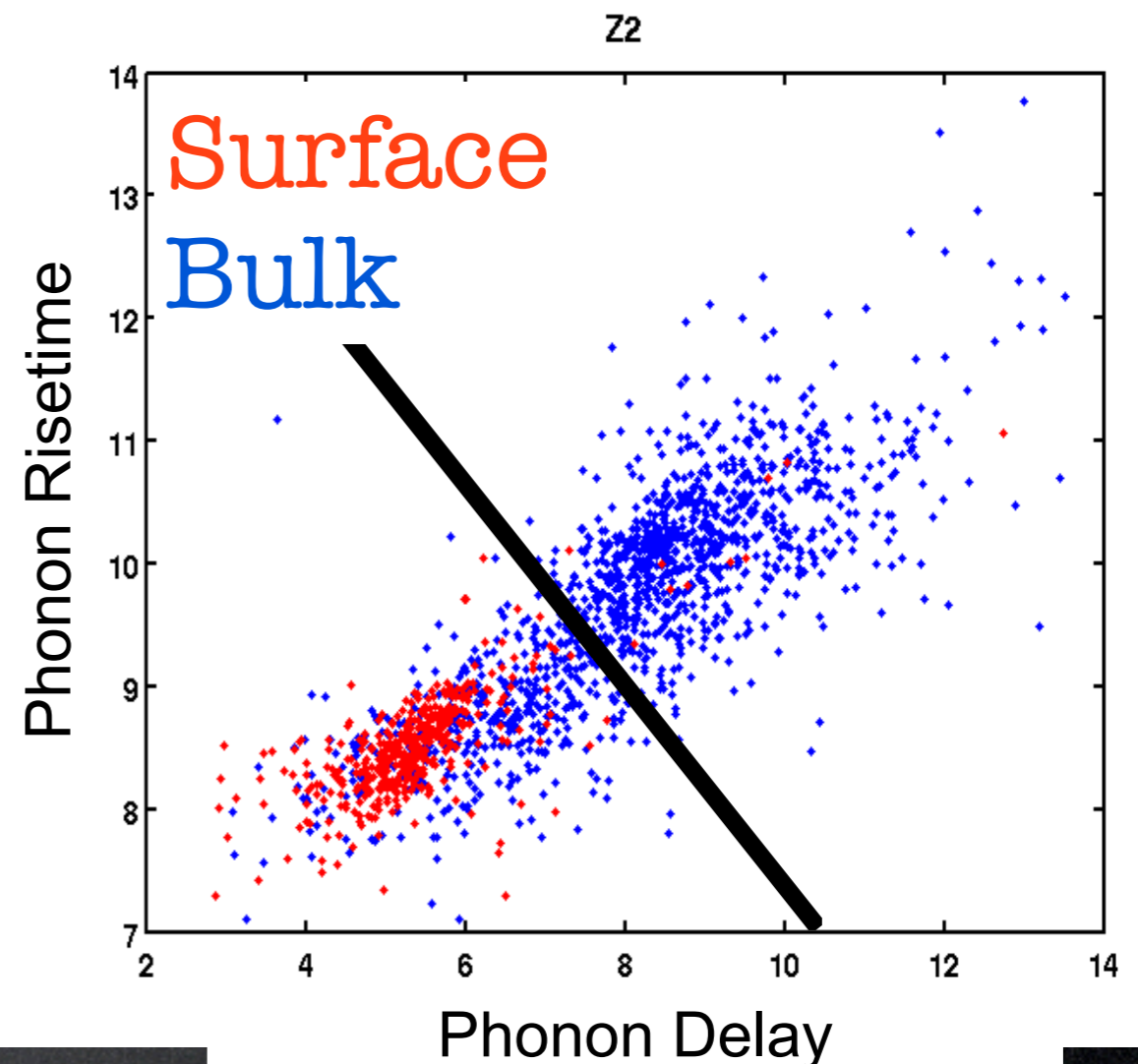
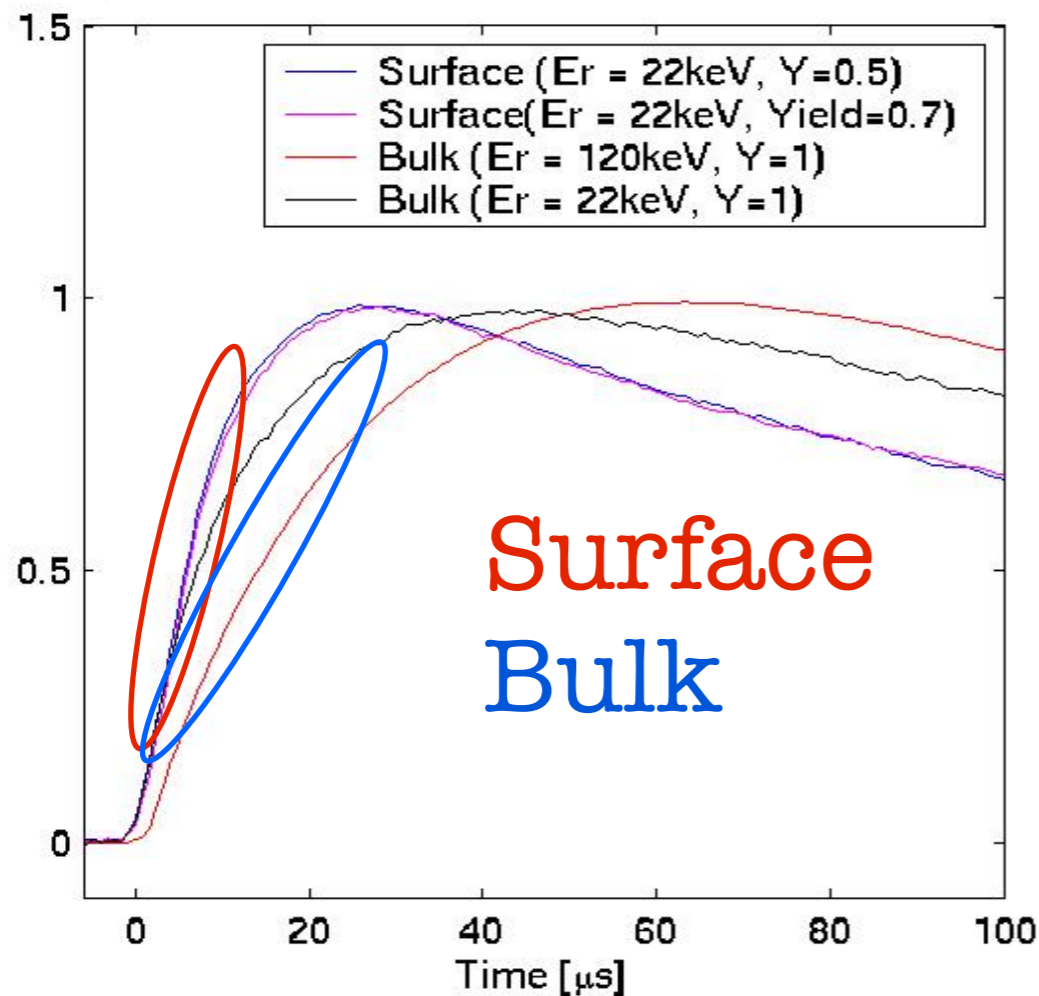
Q top, outer
 Q top, inner
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fast transverse
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 $t = 1.7e-10$

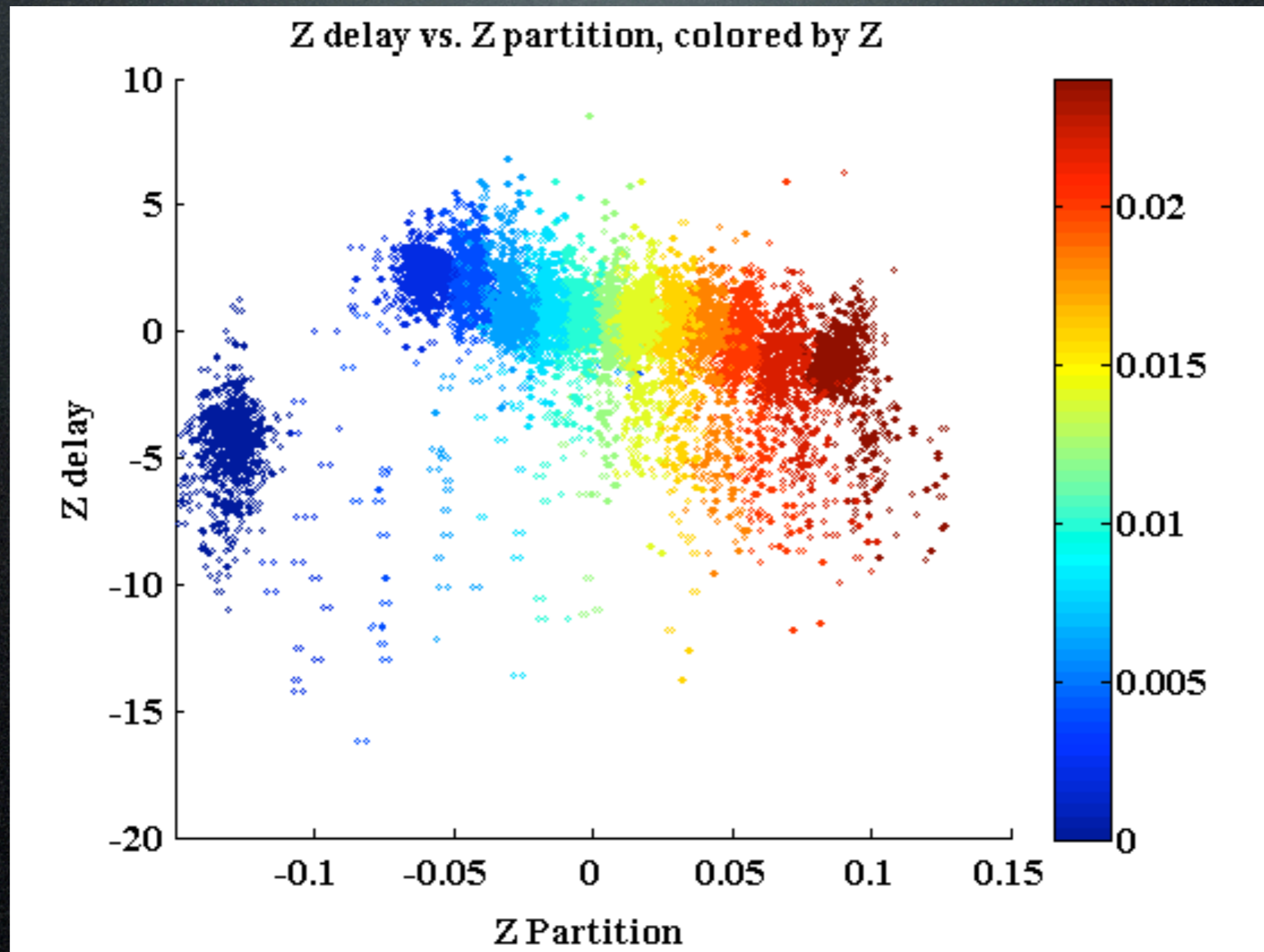
Phonon Timing

Timing Cut, expected 0.5 surface event leakage into nuclear recoil band

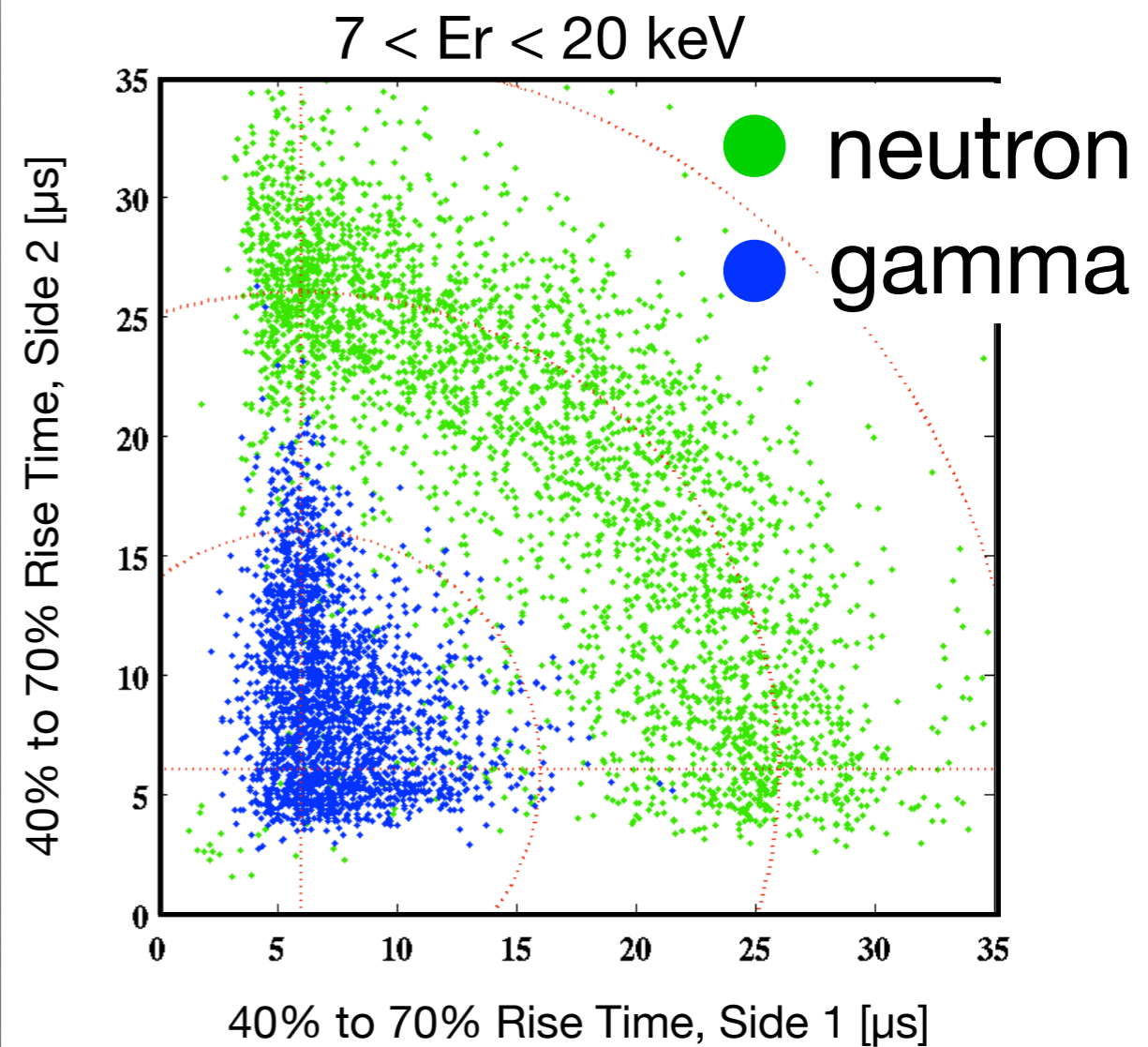
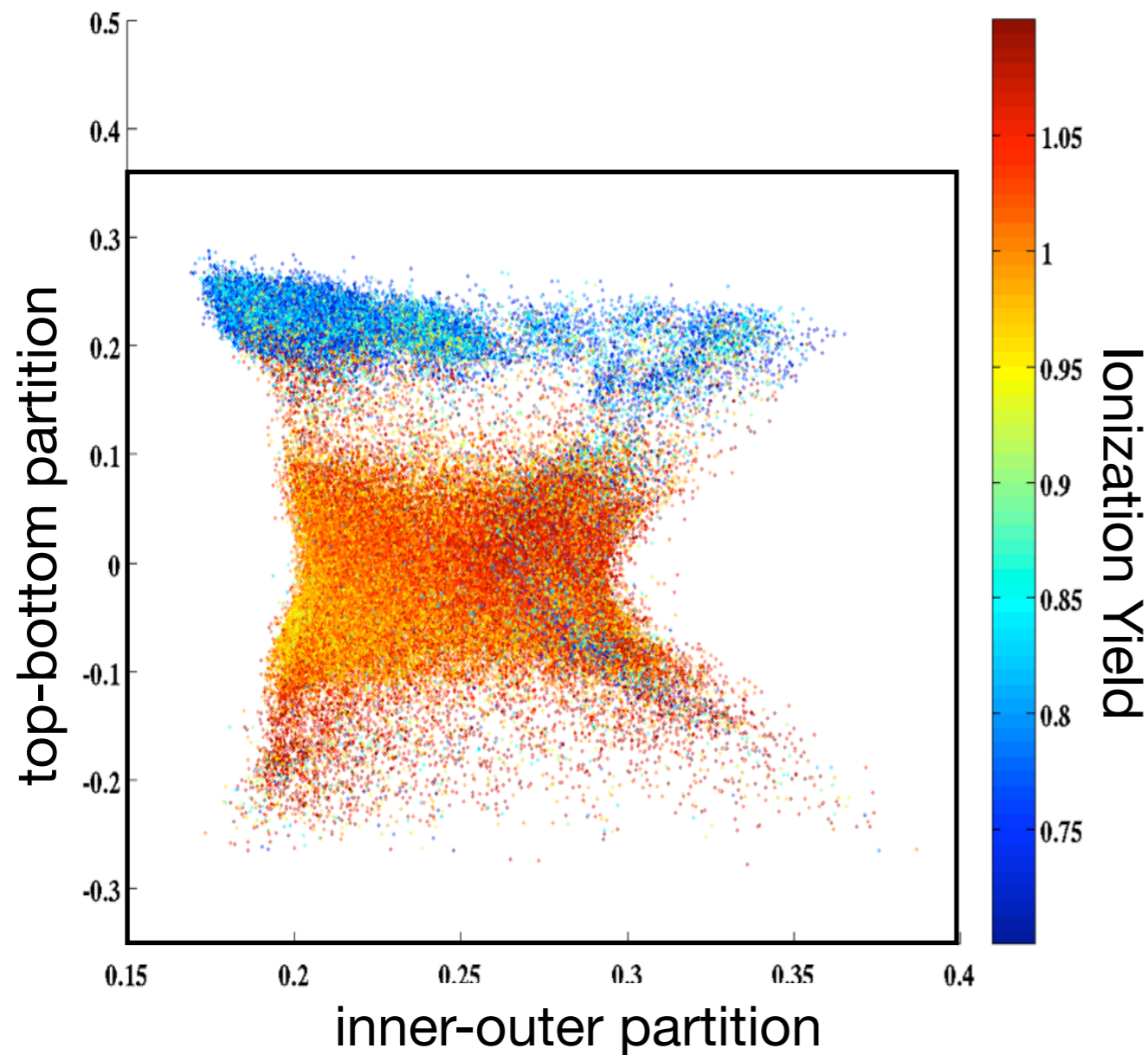
Phonon Sensor



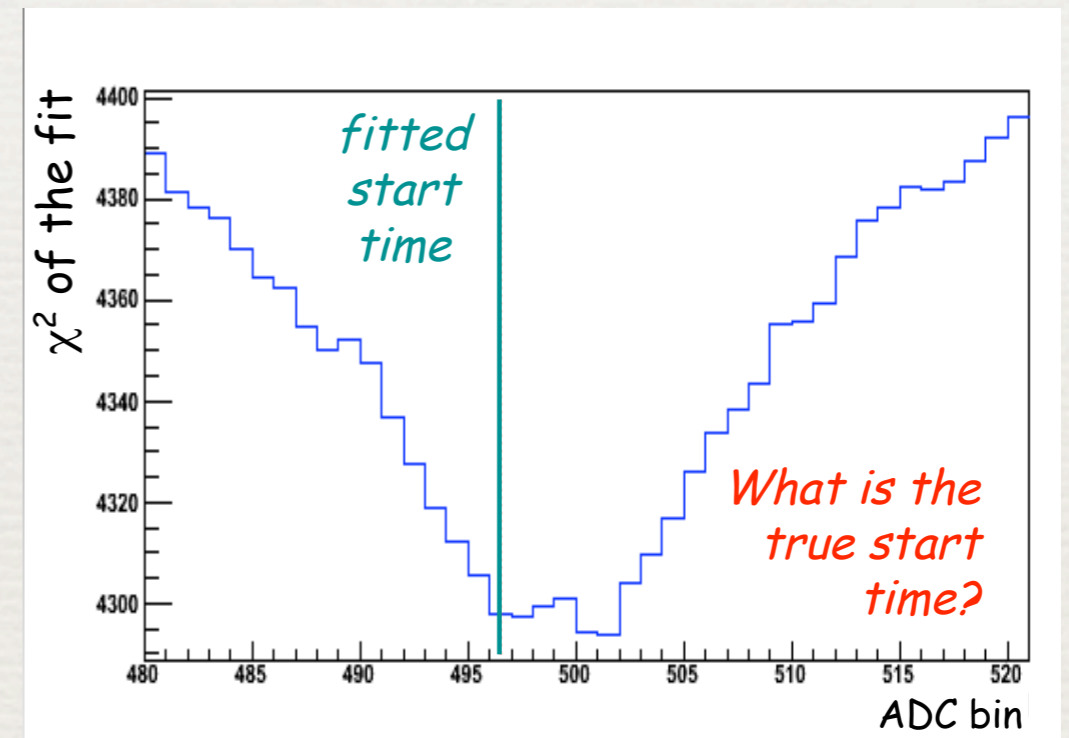
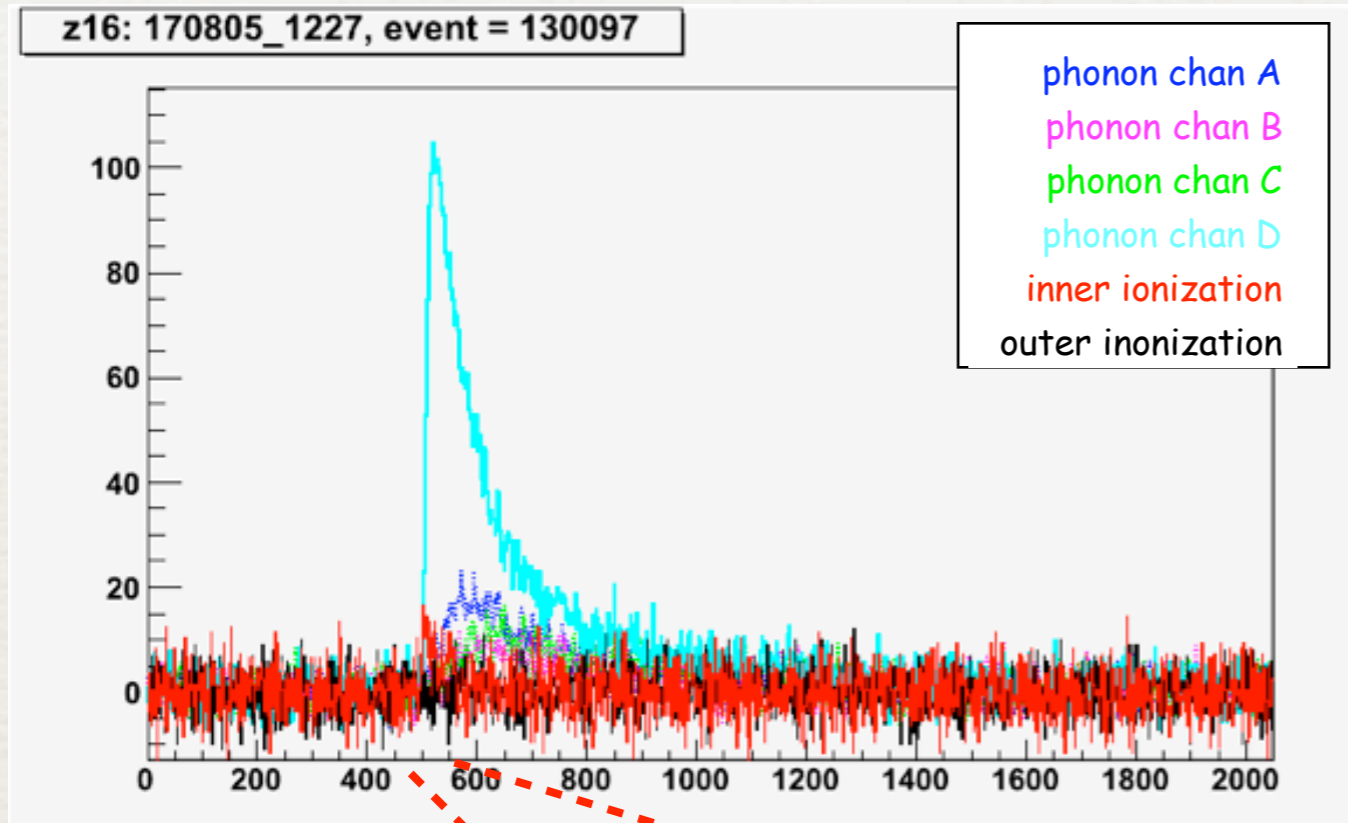
Z-Position in iZIP



Phonon-only Discriminators



T3Z4-Candidate Timing



This effects some events with ionization energy $< \sim 6$ keV.

It does not effect candidate event on T1Z5.

Unfiltered

